

The IEEE Magnetics Society is proud to present

2011 Distinguished Lecture series

**Growth-control and microstructure characterization
of magnetic thin films,**

application to high density perpendicular magnetic recording media

Masaaki Futamoto

Chuo University, Tokyo

Contents

1. Introduction

- * Brief history of PMR research & development

2. Control and characterization of PMR media

- * Crystallographic and compositional microstructure
- * Magnetization microstructure

3. Recent high-density PMR media

- * Nano-structure, nano-magnetization structure

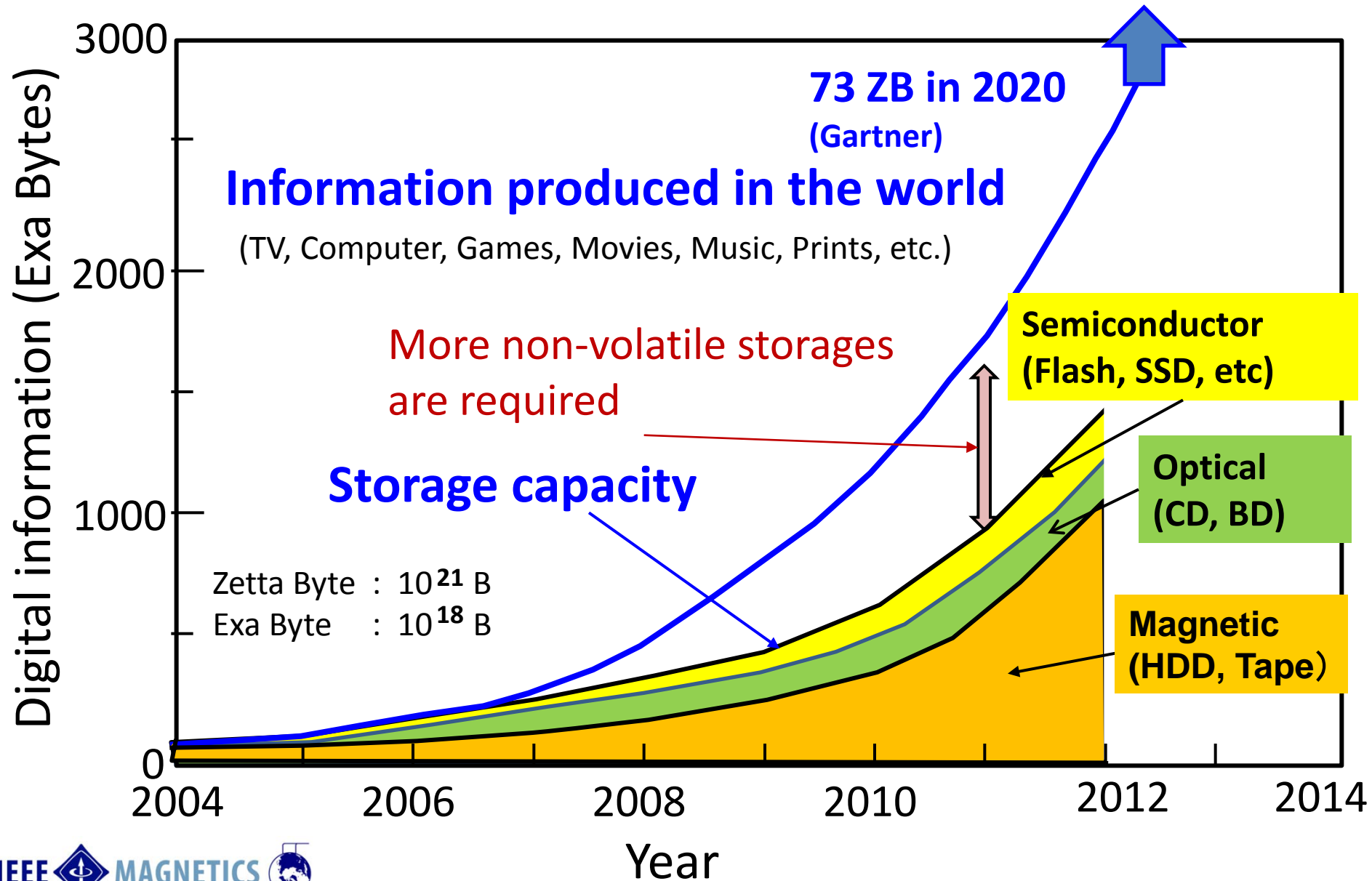
4. Future possibilities of PMR

5. Basic technology: Epitaxial film growth

- * Control of crystal structure & orientation

6. Summary

Digital information in the world



Technology Developments

1900

1950

2000

First Magnetic Recording System
(V. Poulsen) 1898

Wire recording Tape recording Video Tape Recorder

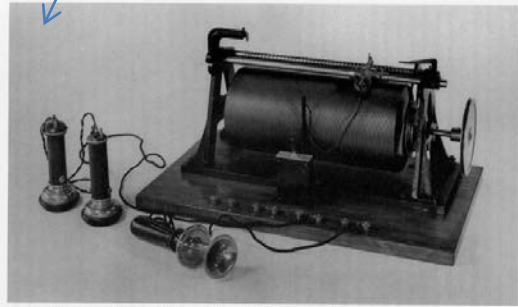
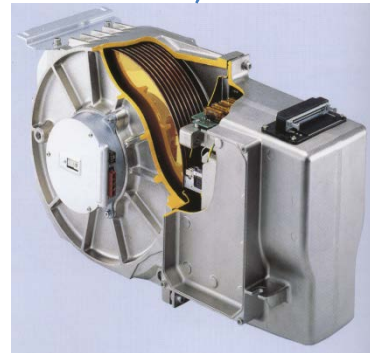


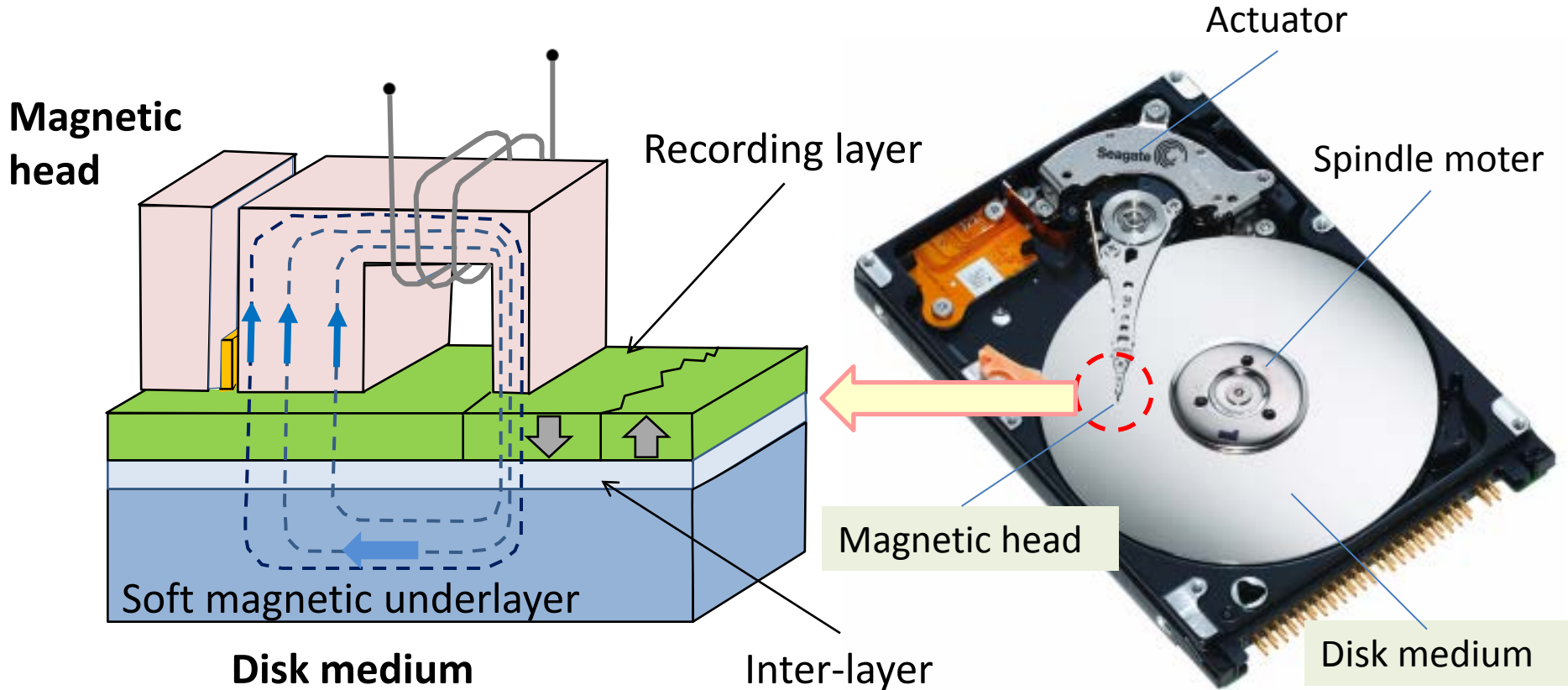
Figure 3. Cylinder telegraph from 1898 (Courtesy: Denmark's Technical Museum, Elanor).

Hard Disk Drive
IBM, 1956



Floppy disk

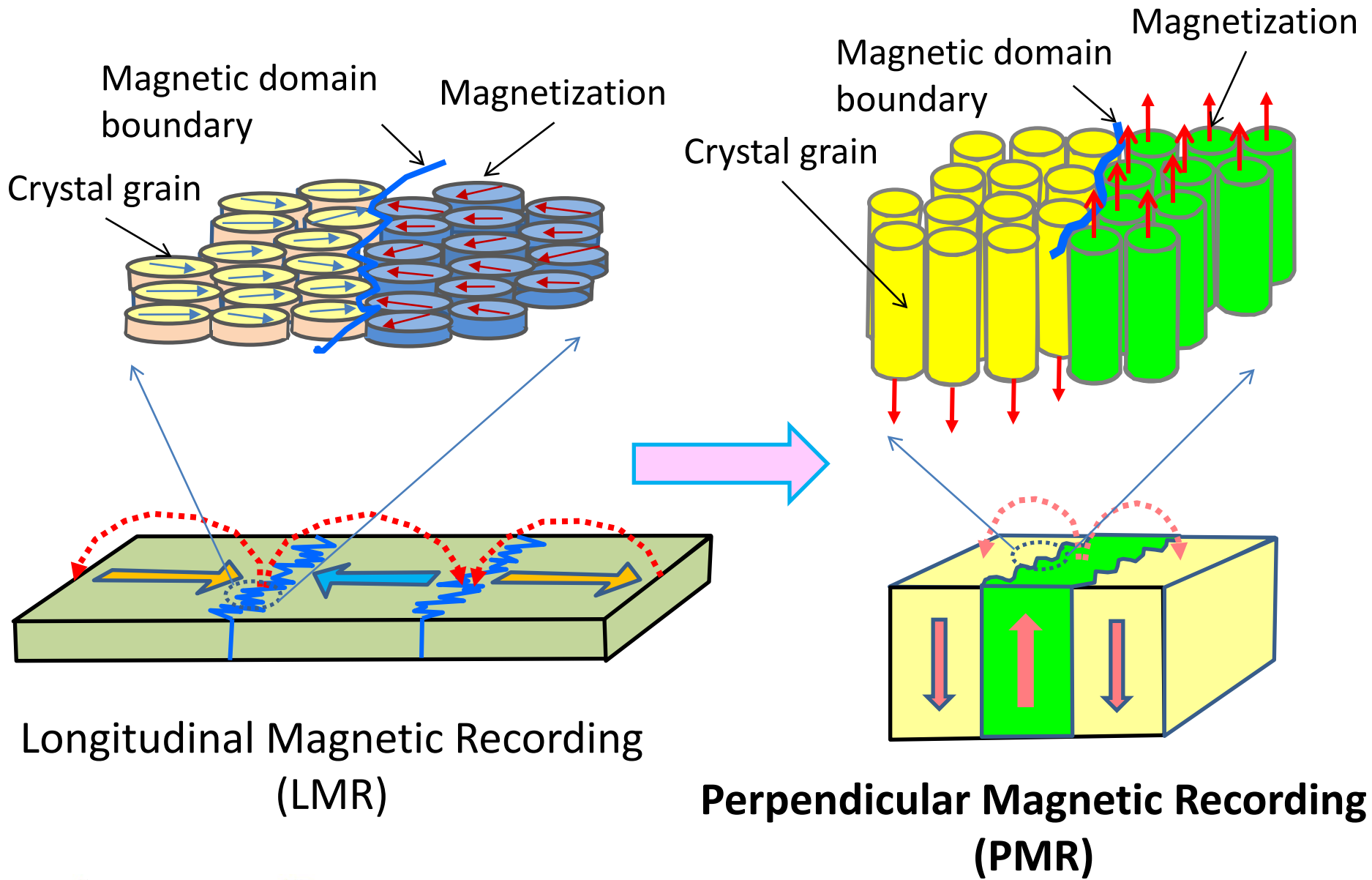
Structure of Recent Hard Disk Drive



(Perpendicular magnetic recording)

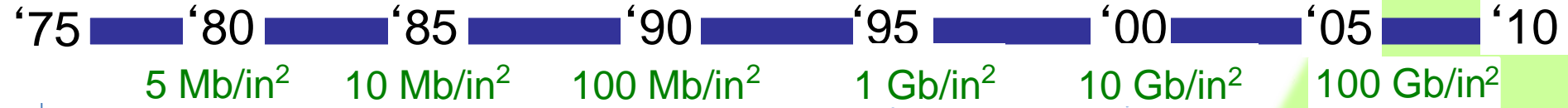
Hard Disk Drive (HDD)

Shift from LMR to PMR



R&D History of Perpendicular Recording Media

Year



● **CoCr-alloy media ('78)** Tohoku U.

● **Underlayer effect ('84-85)**
Hitachi

● **SUL noise observation ('84-85)**

● **Cross-sectional TEM ('84-85)
by ion-thinning**

● **Magnetization structure observation
E-holography ('86 - '87),** Hitachi

● **MFM ('92-'93)**

● **Improved underlayers (96-'97)**

Hitachi

● **Media noise reduction, Hitachi
High H_c, High Mr/Ms media ('97-'98)**

● **CoCrPtO high Mr/Ms media
('00-'01) Toshiba**

● **Improved SUL ('00-'02)
Hitachi & Many companies**

● **52.5Gb/in² demonstration
with PMR ('00) , Hitachi**

● **Compositional segregation
by EELS & EDX TEM ('96-'97), Hitachi**

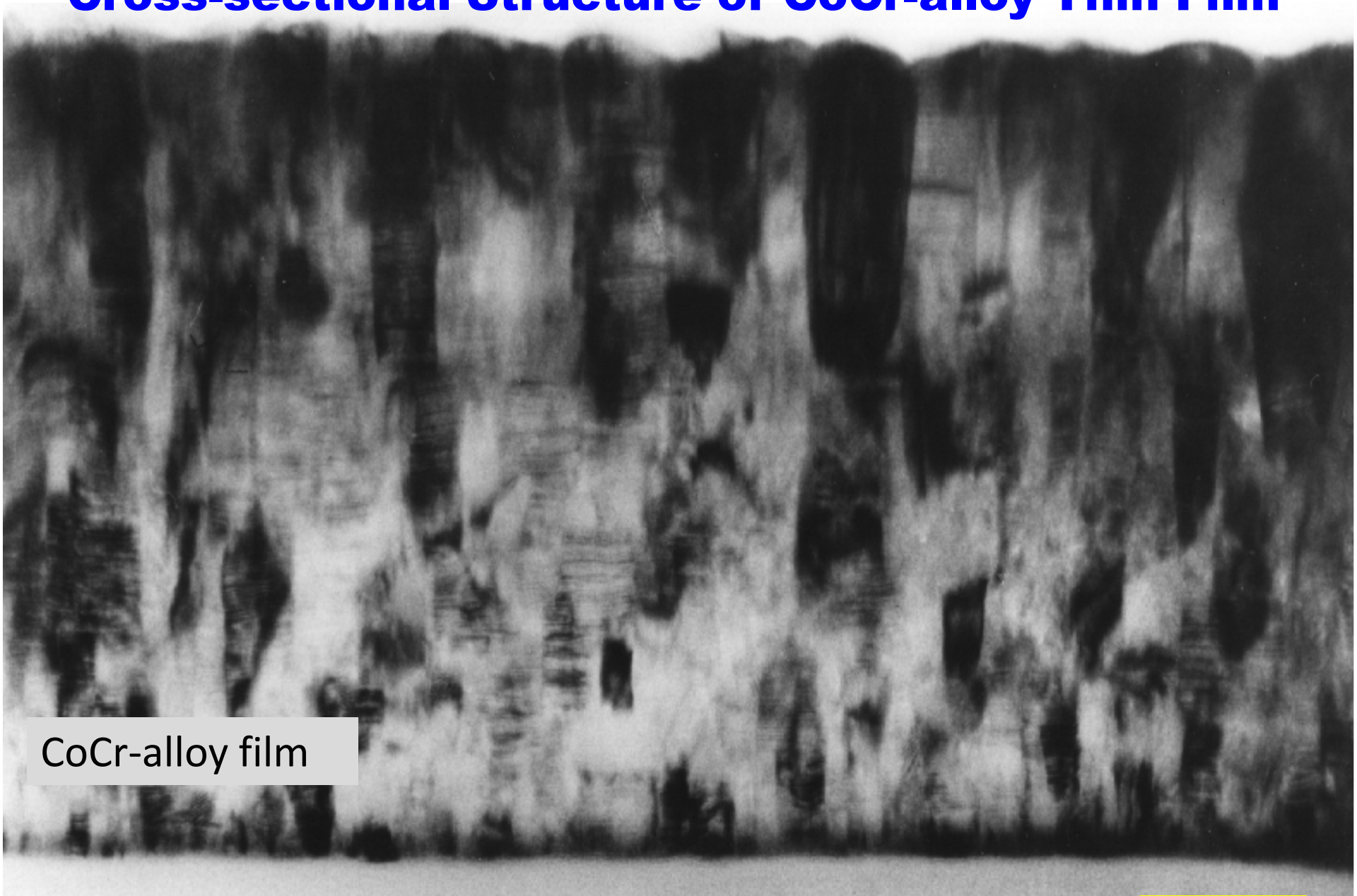
● **Co-alloy basic properties, Ku, α
('96-'97), Hitachi, Tohoku U.**



**Invention of PMR
by Prof. Iwasaki ('76) Tohoku U.**

Key technologies: Media

Cross-sectional Structure of CoCr-alloy Thin Film



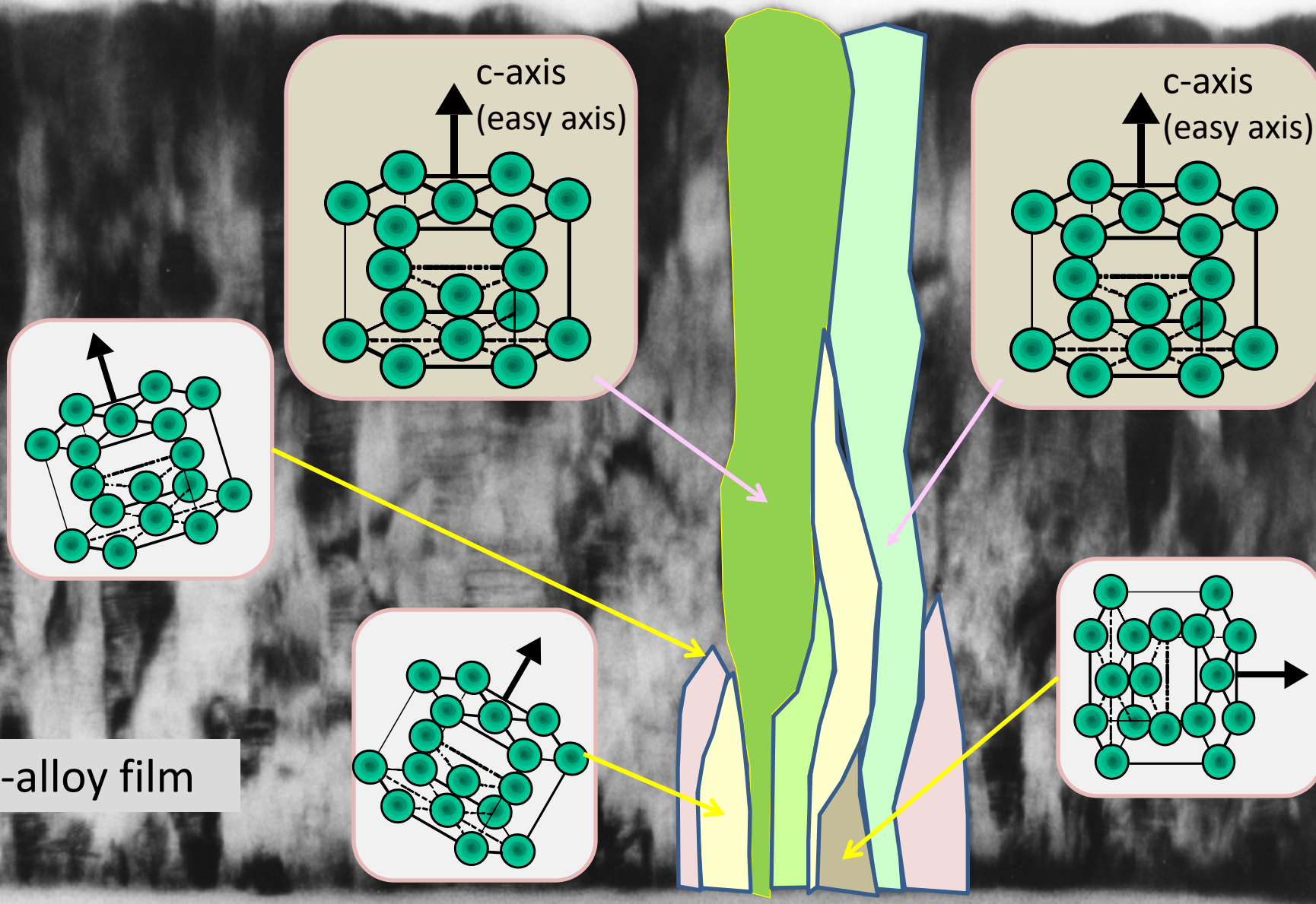
CoCr-alloy film

Substrate

M. Futamoto et al.,
Japan. J. Appl. Phys., 24, L460(1985).

50 nm

Cross-sectional Structure of CoCr-alloy Thin Film

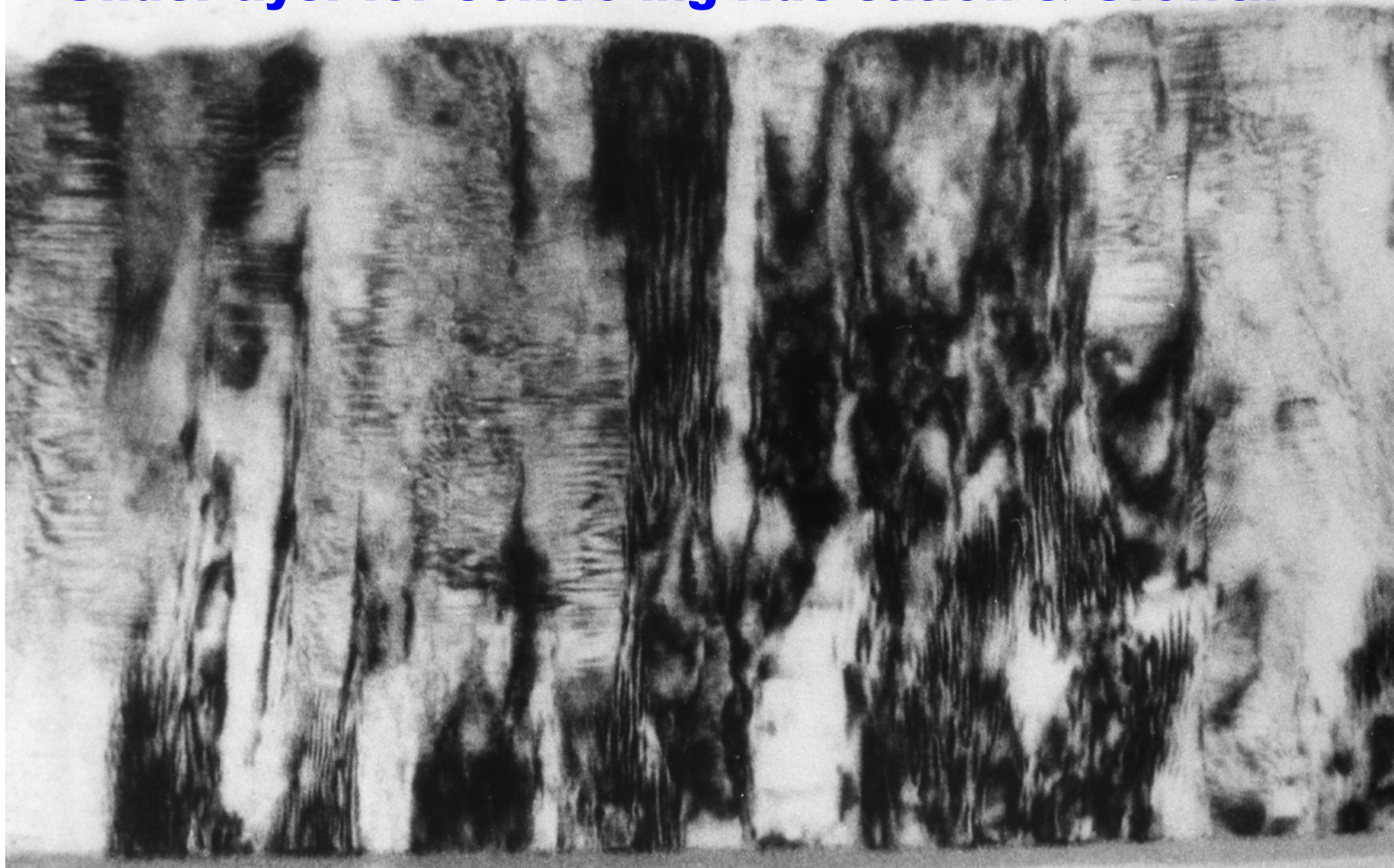


CoCr-alloy film

Substrate

50 nm

Underlayer for Controlling Nucleation & Growth



Amorphous underlayer

Substrate

M. Futamoto et al.,
IEEE Trans. MAG-21, 1426(1985).

50 nm

2nd Underlayer for Controlling Grain Diameter



2nd underlayer (Ti)



1st underlayer (Ge)

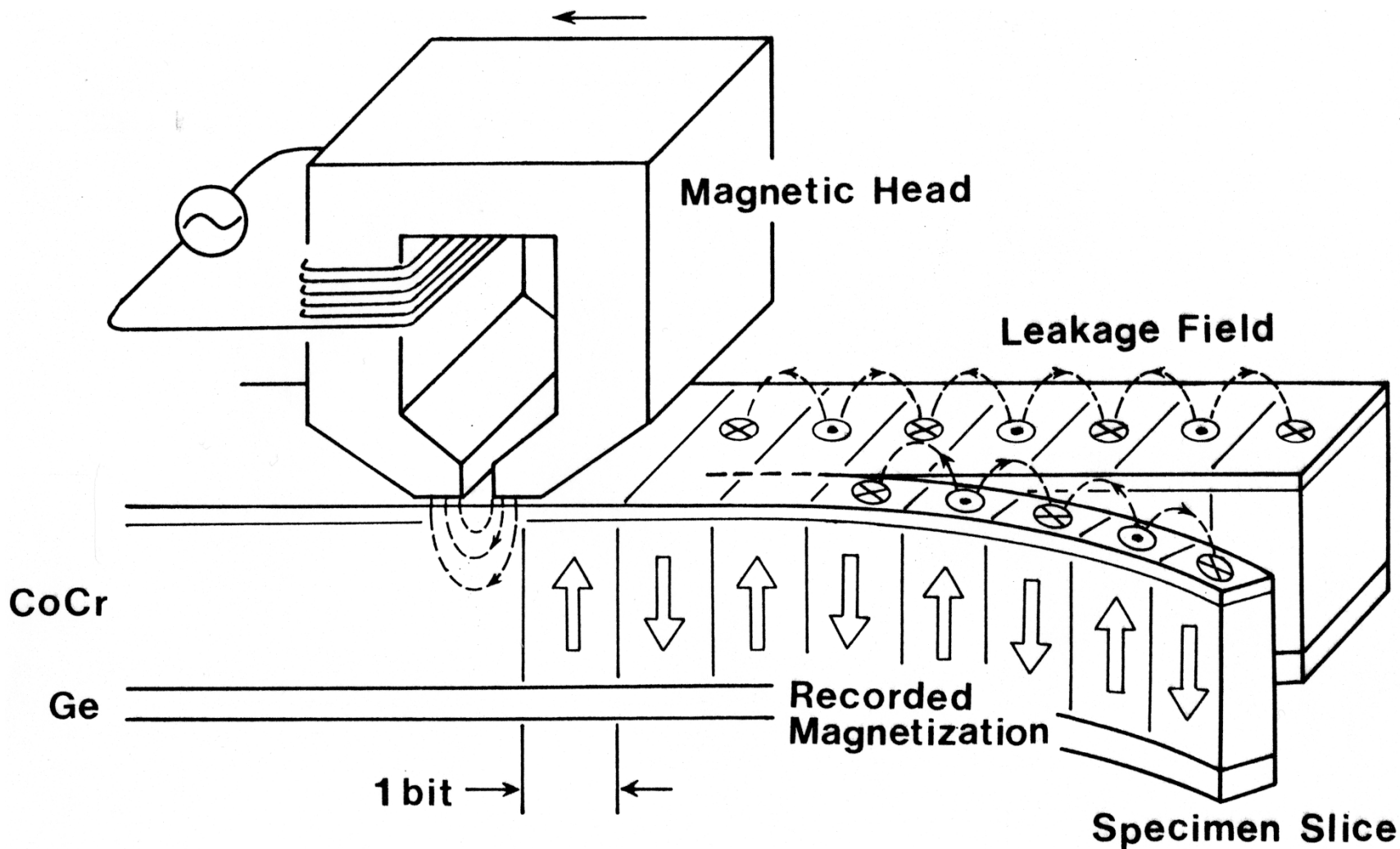


Substrate

M. Futamoto et al.,
J. de Phys., Coloq. C8, 1979(1988).

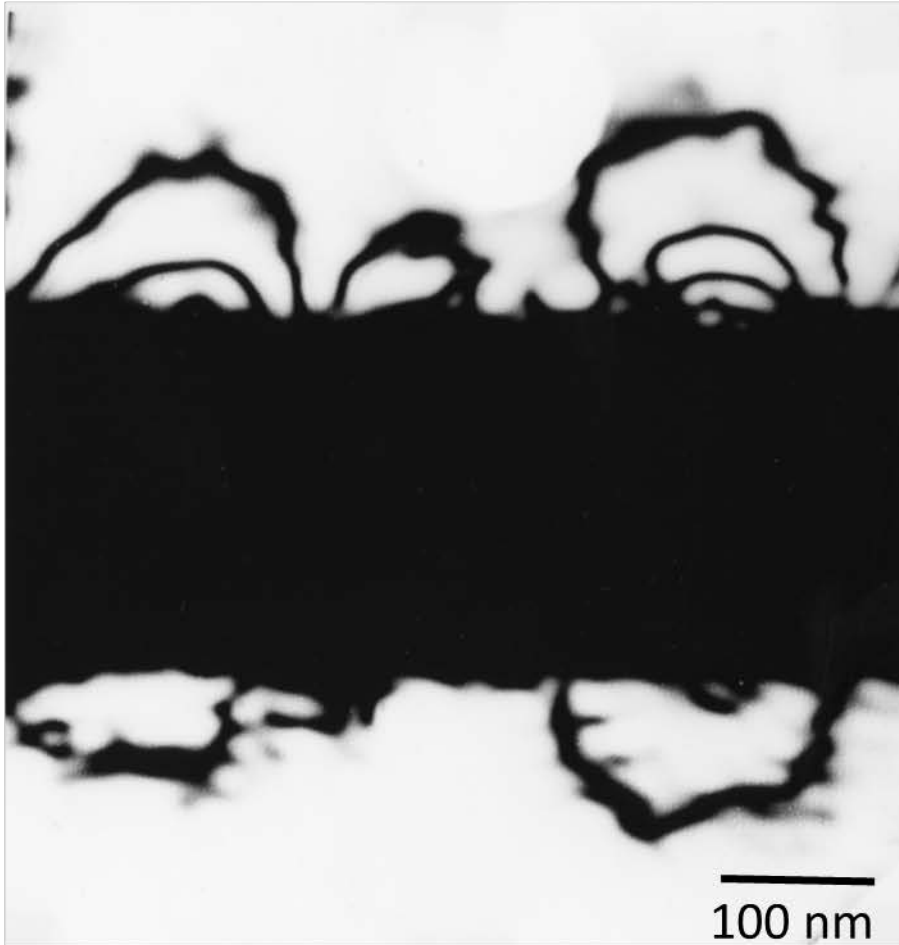
50 nm

Sample Preparation for Electron Holography

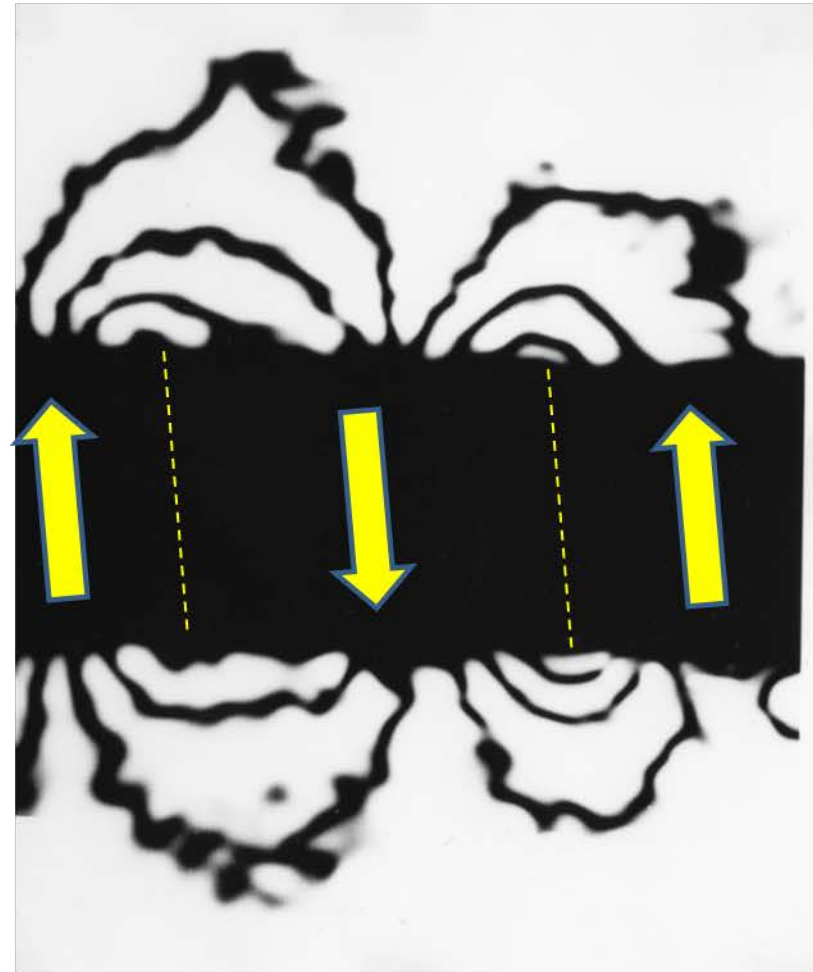


Y. Honda et al.,
J. de Phys., Coloq. C8, 1969(1988).

Effect of Film Orientation on Interference Micrograph of Leakage Magnetic Flux from Top and Rear Surfaces



Poorly c-axis oriented
(CoCr with no underlayer)



Highly c-axis oriented
(CoCr with Ge underlayer)

PMR Media Technology Development

1980

1990

2000

2010

Material

CoCr

CoCrTa

CoCrPt

CoCrPtTa

CoCrPt-Oxide

Commercial Application

LMR

PMR

Research

PMR

LMR

PMR

Microscopy

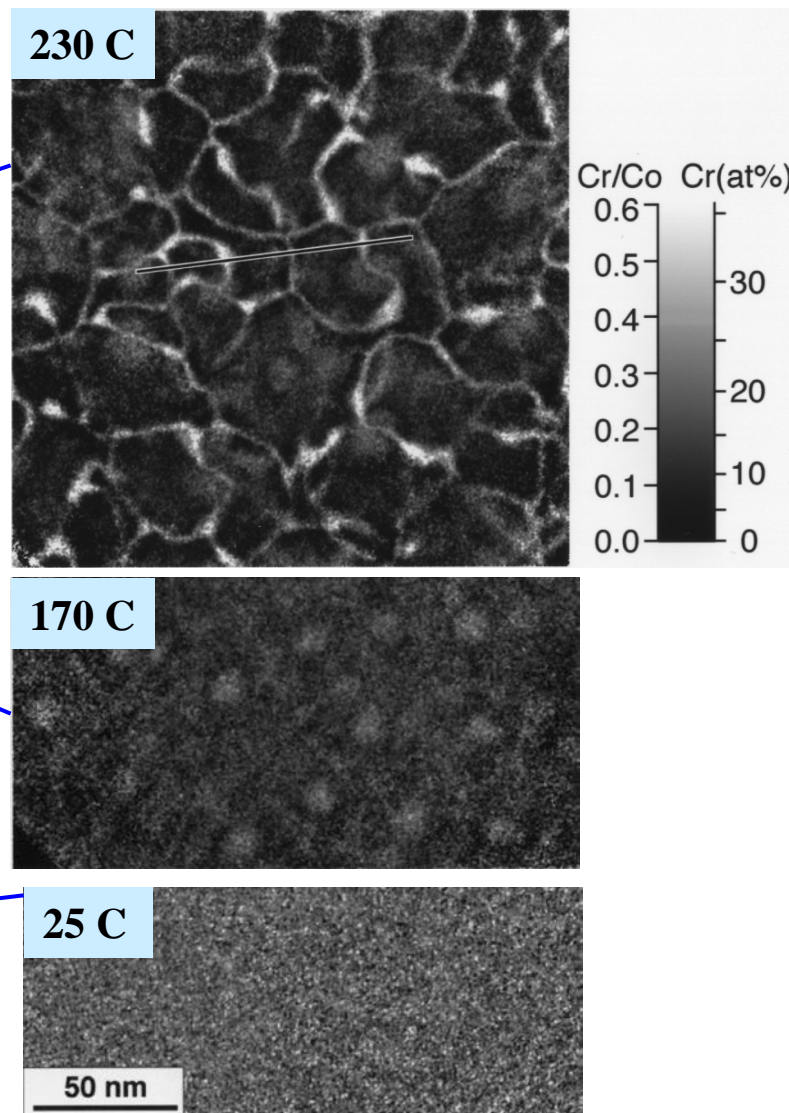
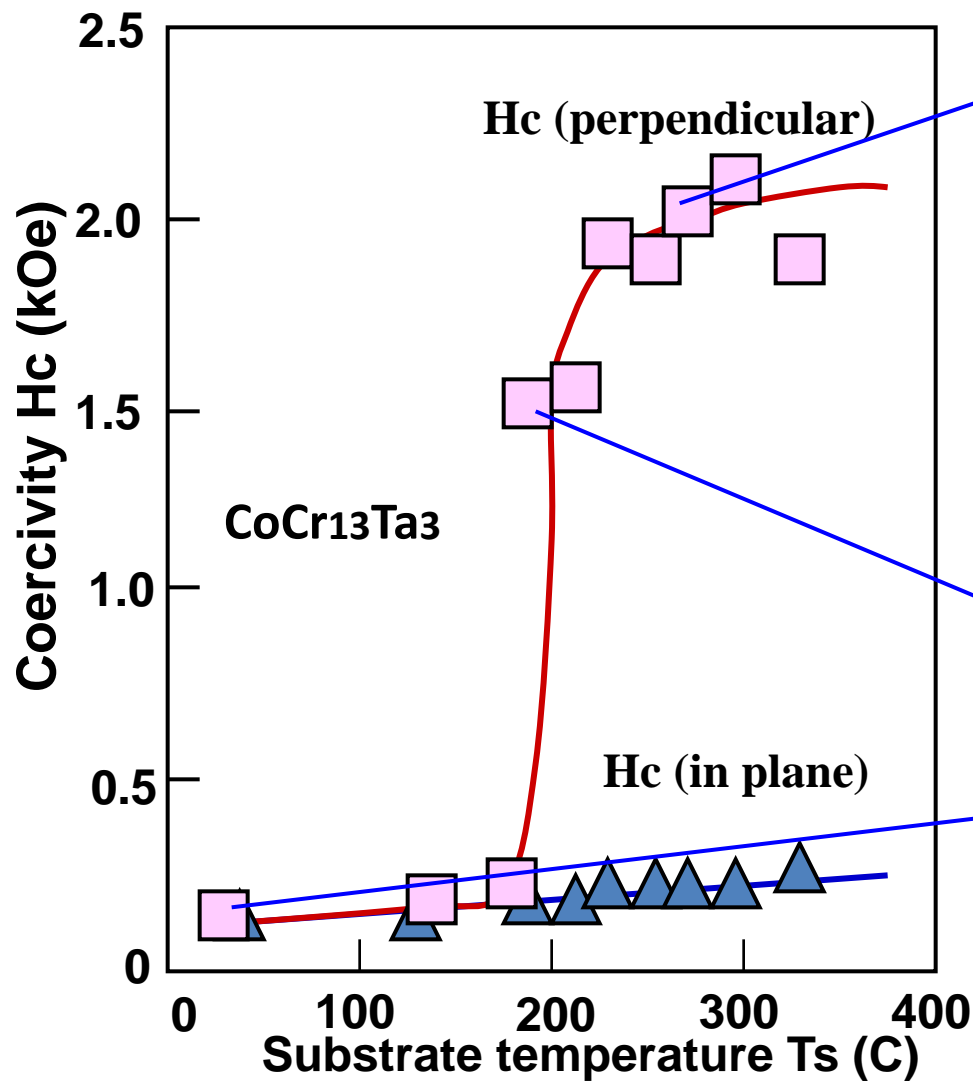
SEM

TEM with EDX, EELS

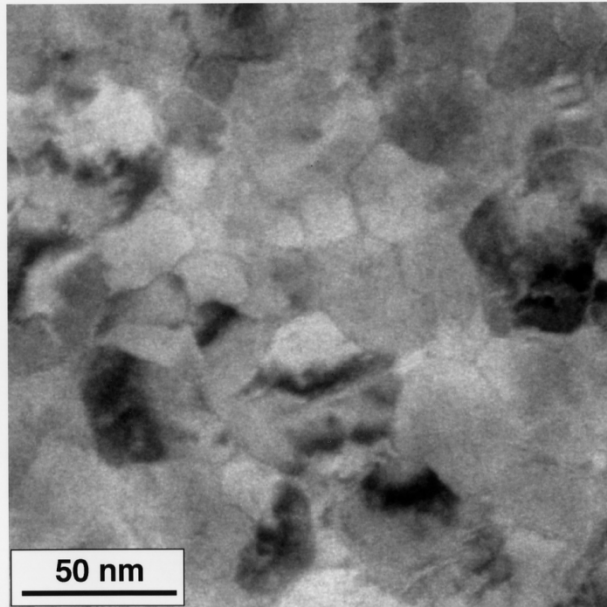
Plan-view TEM

Cross-sectional TEM

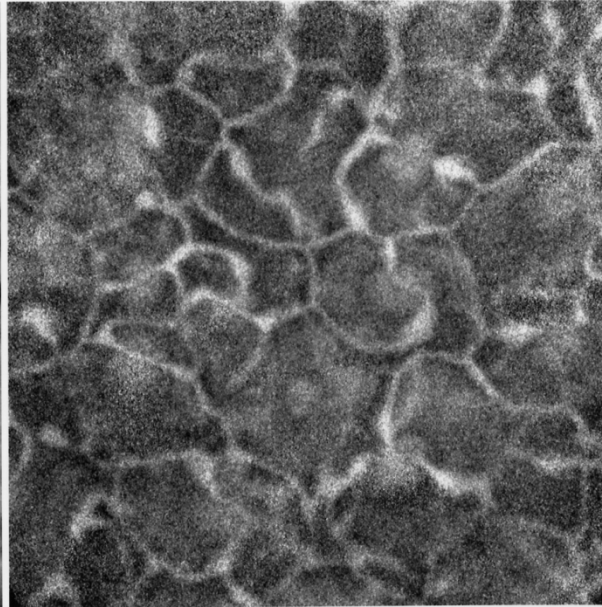
Cr Segregation at Grain Boundaries and Magnetic Properties



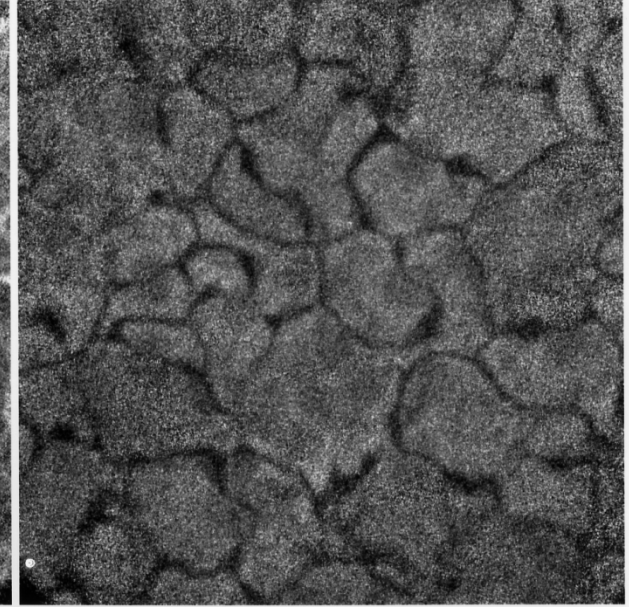
Plan-view TEM and Elemental Distribution Maps of CoCrTa PMR Medium



Zero loss image



Cr ratio map



Co ratio map

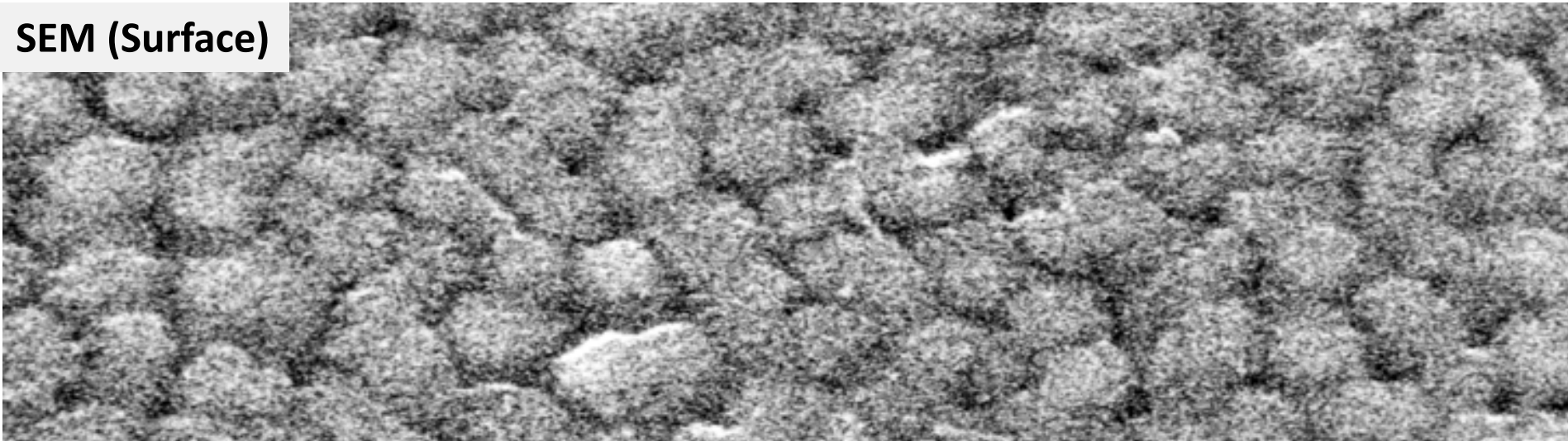
Co-13at%Cr-3at%Ta
PMR Medium

$T_s=230\text{ C}$

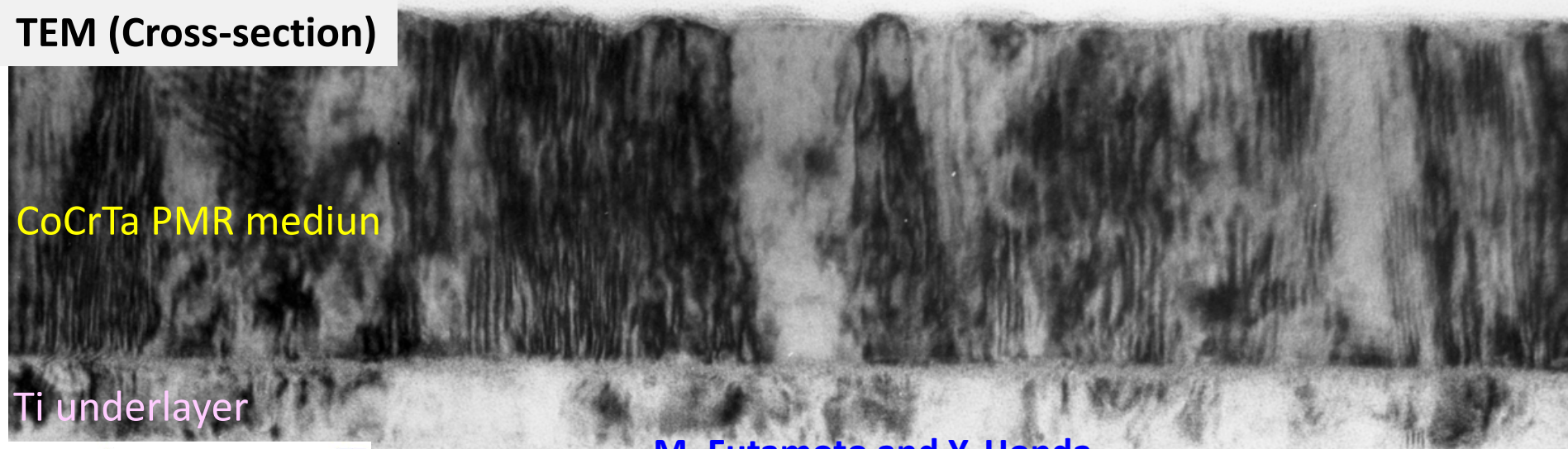
K. Kimoto, et al.
J. Mag. Mag. Mater.159,
401(1996).

Structure of CoCrTa Perpendicular Media

SEM (Surface)



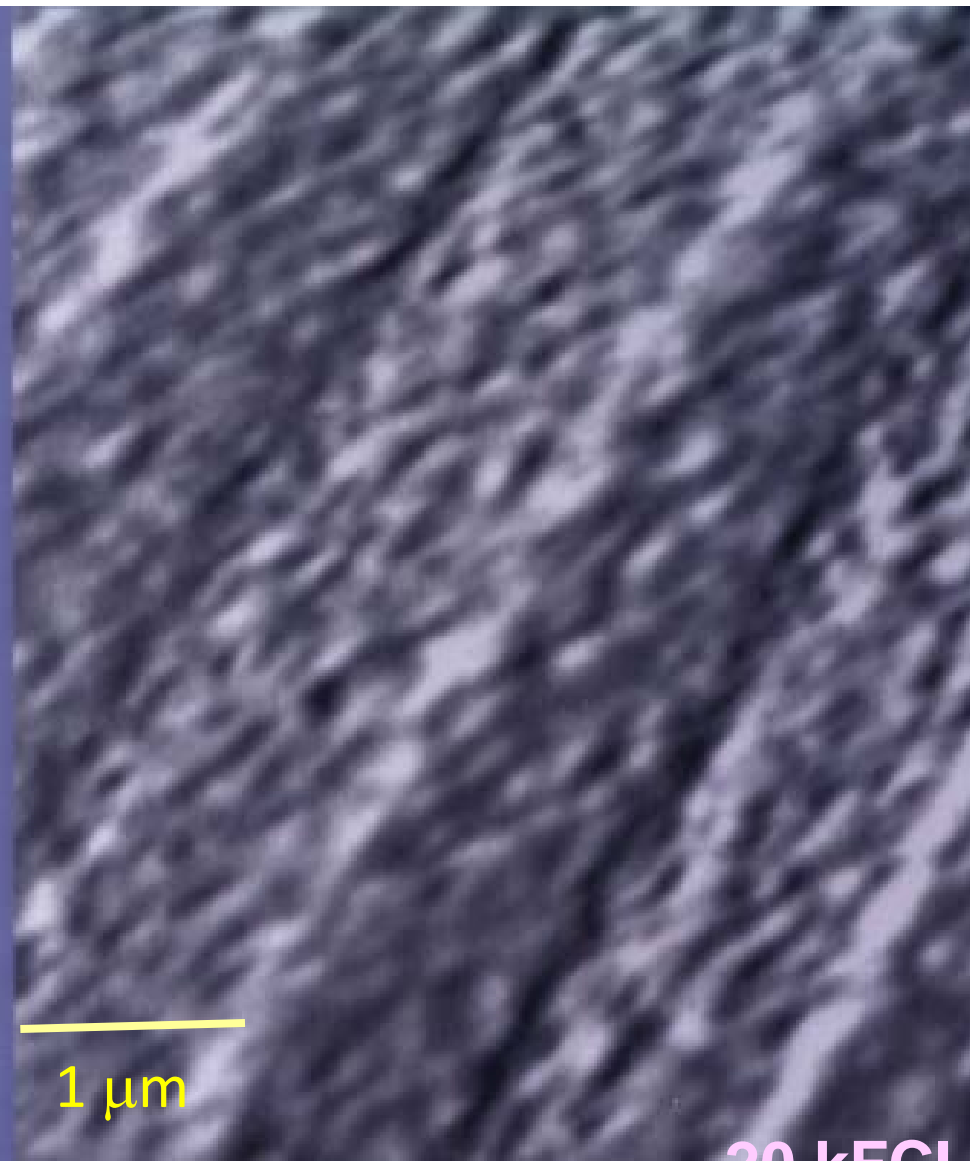
TEM (Cross-section)



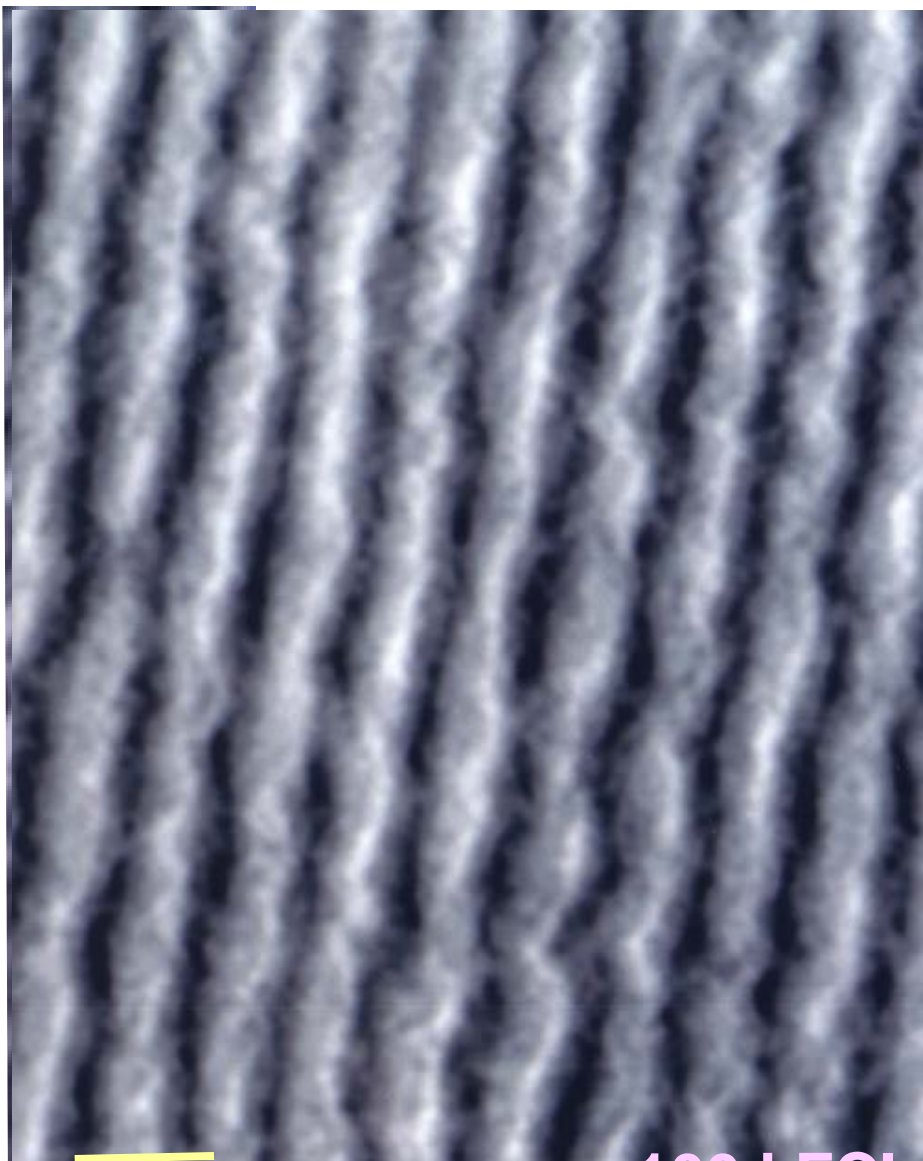
CoCrTa PMR medium

Ti underlayer

Magnetization Structure of CoCrTa Medium

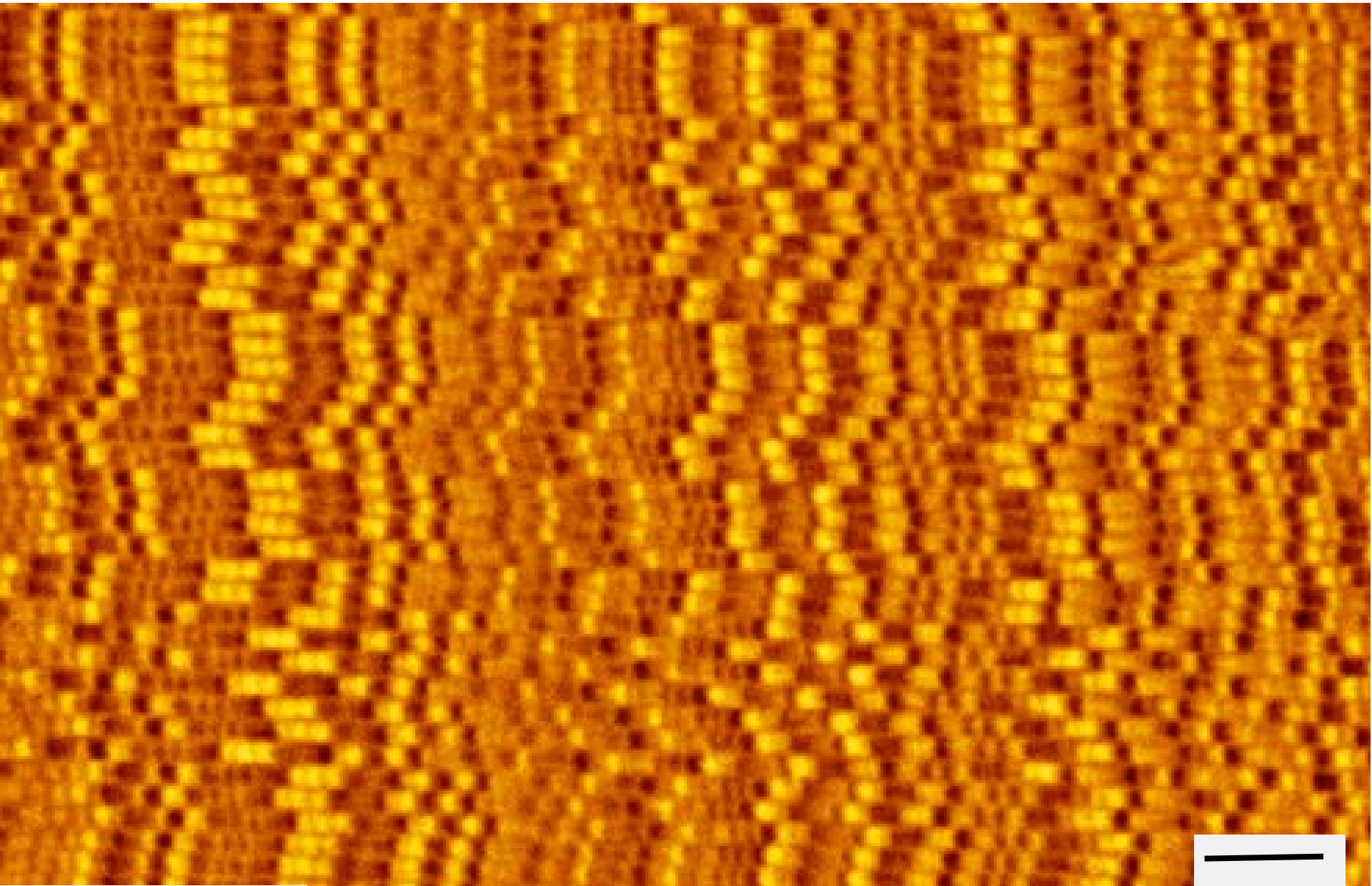


20 kFCI



100 kFCI

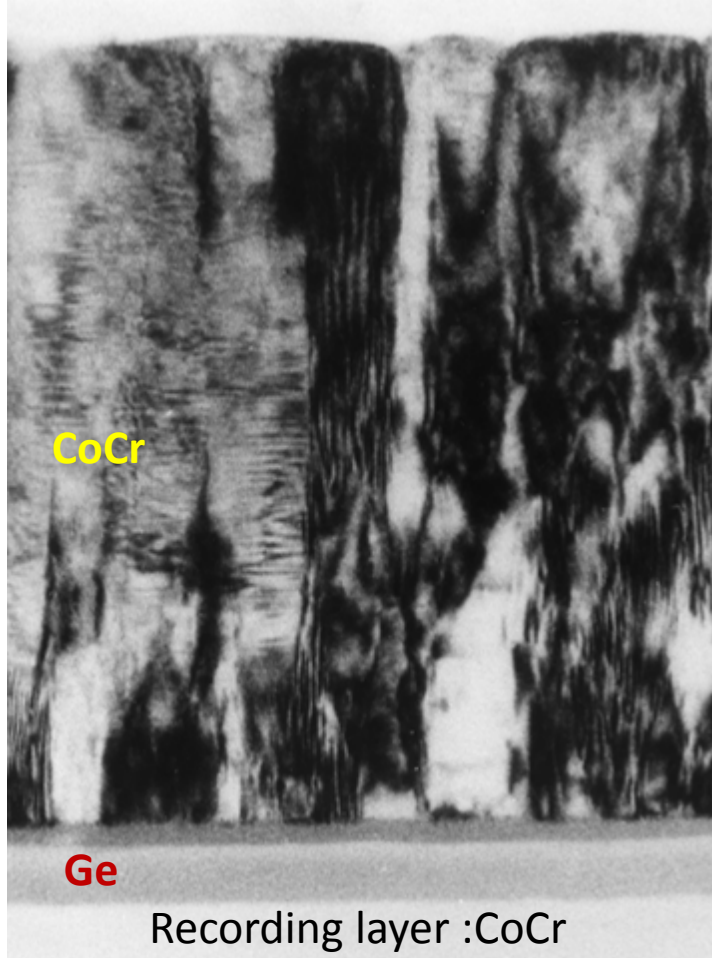
Magnetization Structure of CoCrPt+Oxides Medium



1 μm

Scaling Down of Media Microstructure in 1/4 Century

Year :1985

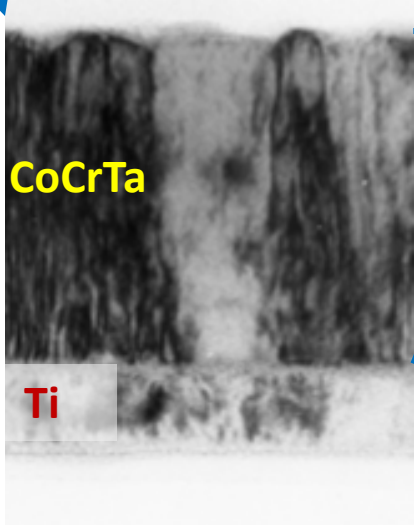


CoCr

Ge

Recording layer :CoCr
h=300 nm, d=30-50 nm
Hc=0.85 kOe

Year :1995

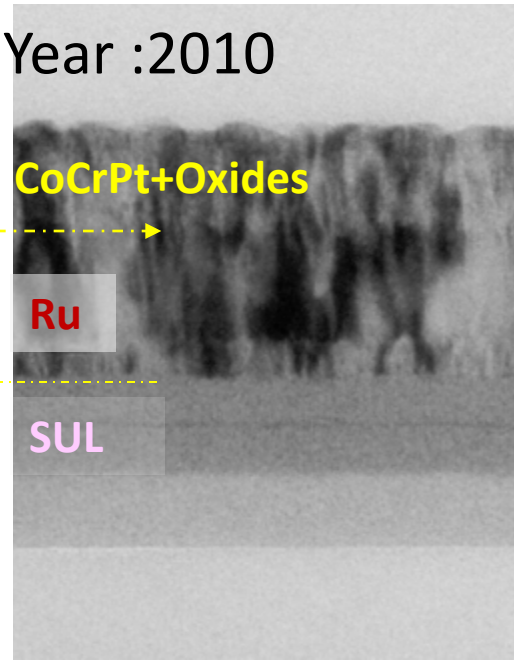


CoCrTa

Ti

Recording layer :CoCrTa
h=100 nm, d=15-20 nm
Hc=2.2 kOe

Year :2010



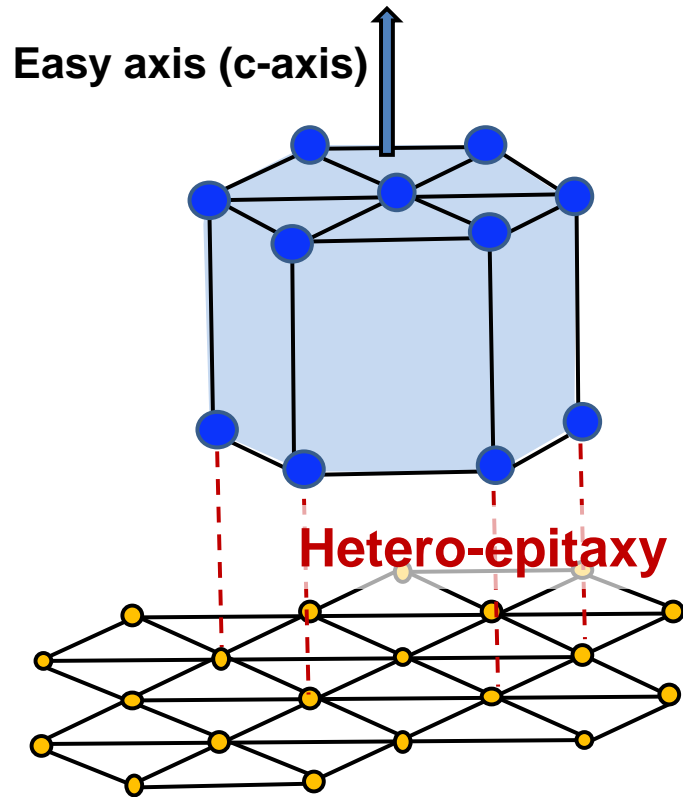
CoCrPt+Oxides

Ru

SUL

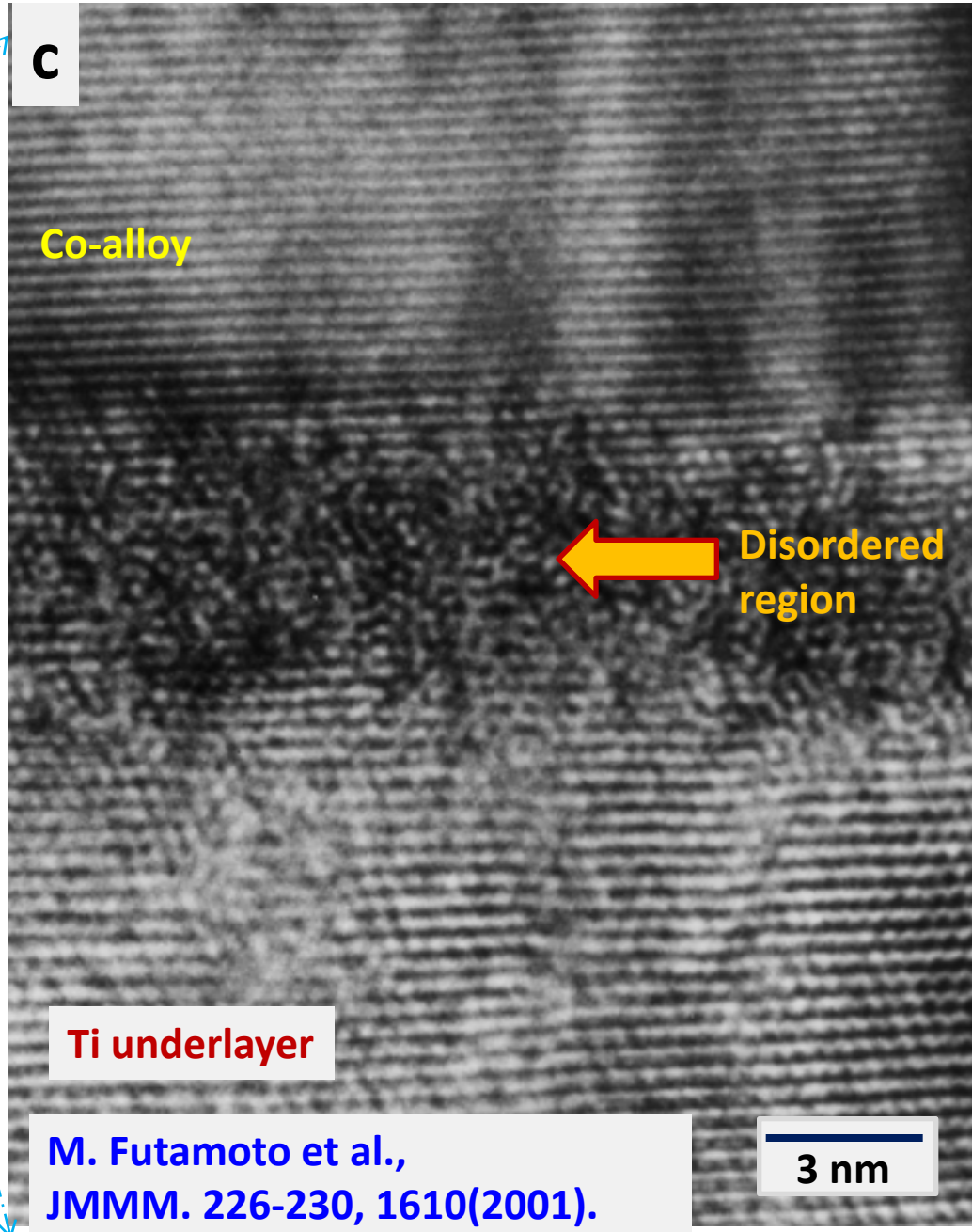
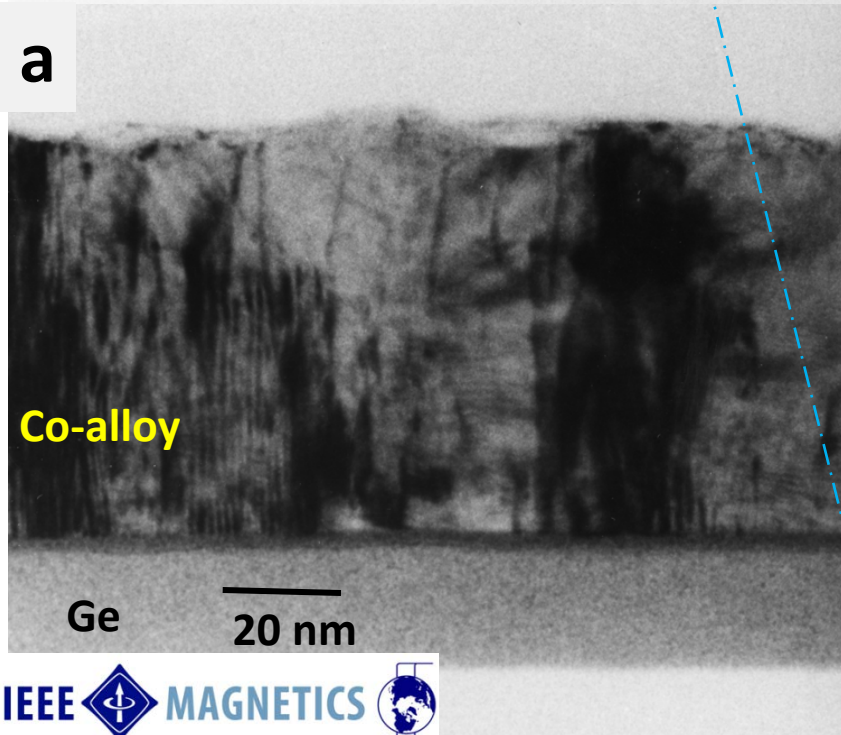
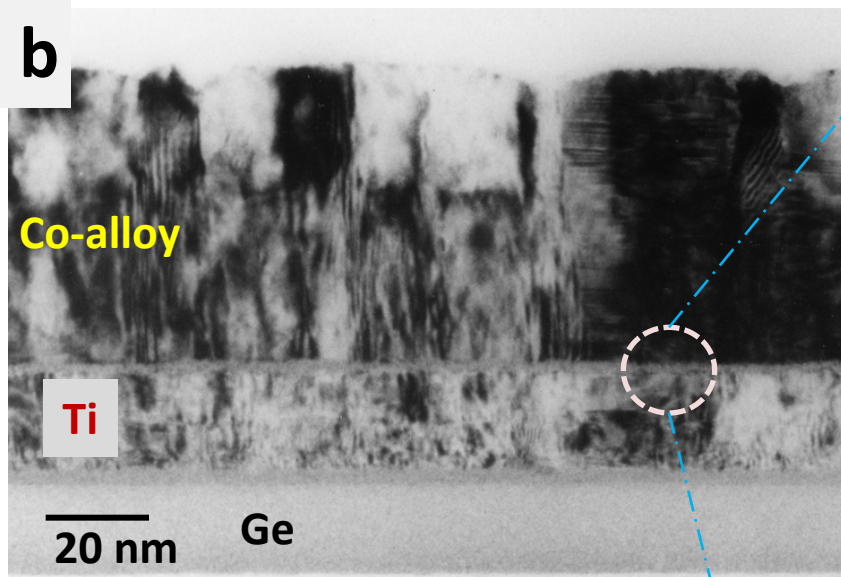
Recording layer :CoCrPt+Oxides
h=15 nm, d=7-9 nm
Hc=4.2 kOe

C-axis Alignment perpendicular to the surface

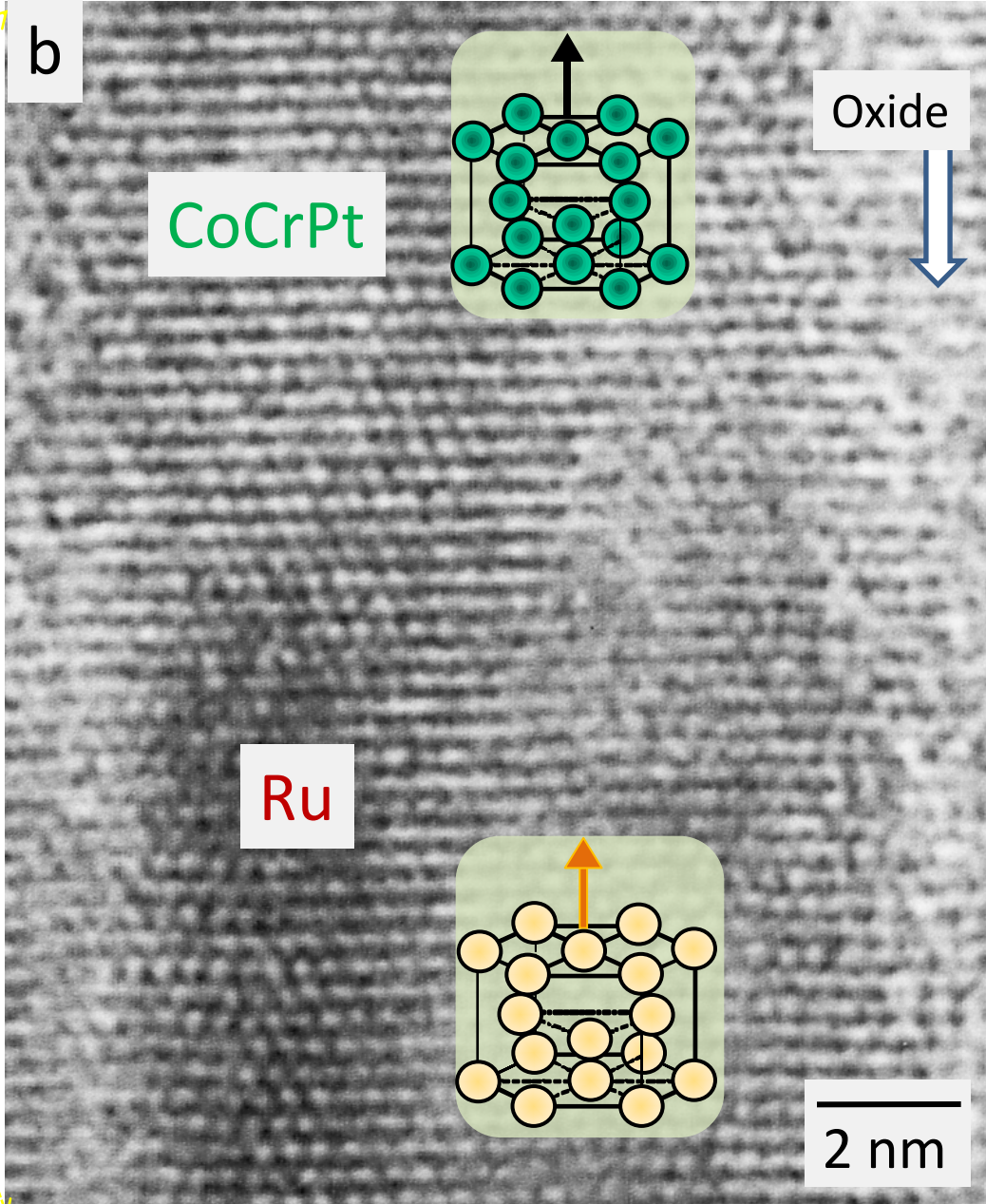
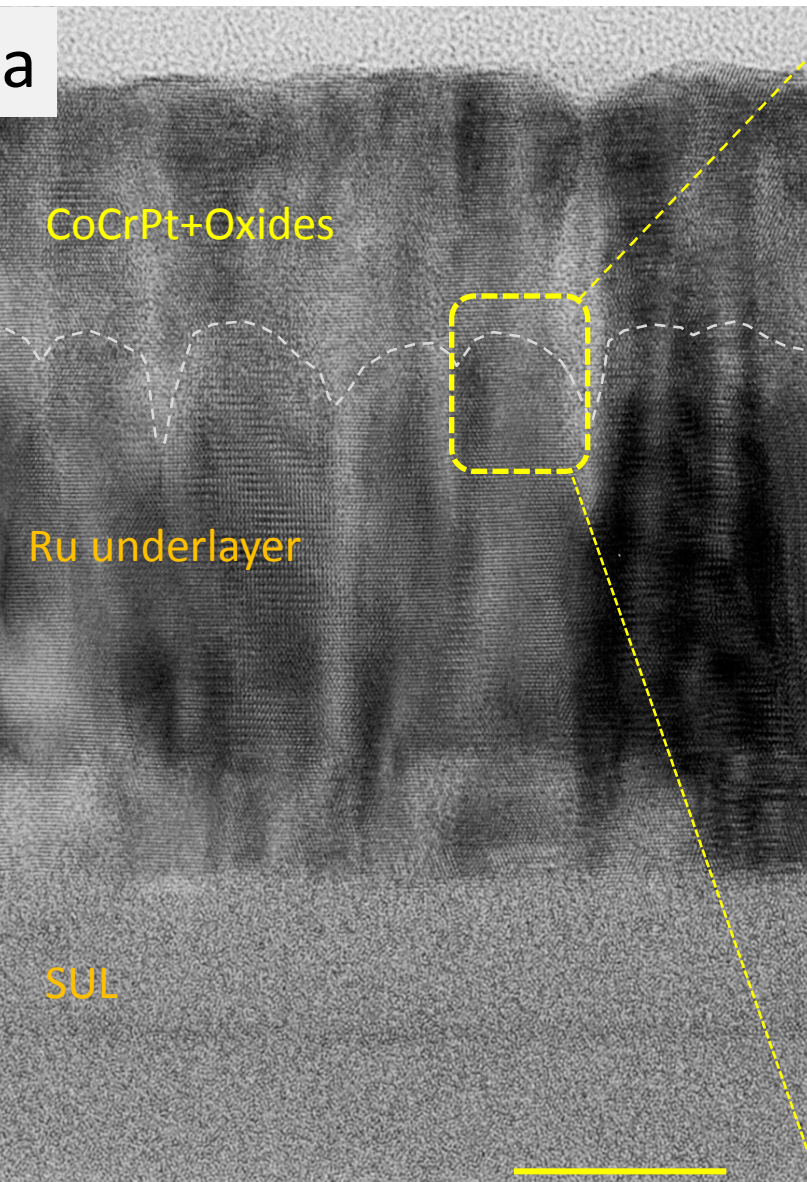


Materials		References
hcp	Ru	IEEE Trans. Magn. 30, 5115(1994).
	Ti	Dig. 6 th Conf. MSJ, p.42(1985).
	TiCr	IEEE Trans. Magn. 32, 3789(1996).
	Ta	IEEE Trans. Magn. MAG20, 776(1984).
	CoCr	IEEE Trans. Magn. 25, 4168(1989).
	CoCrRu	IEICE Trans. Electron. E84-C, 1132(2001).
	Ru/Ta	IEEE Trans. Magn. 42, 2382(2006).
	Ru/NiW	J. Appl. Phys. 105, 07B723(2009).
	Ru/Ru-oxide	IEEE Trans. Magn. 40, 3193(2005).
Ti/Ge	J. de Phys. Coll. C8, suppl.12, 1979(1988).	
fcc	Au, Al	IEEE Trans. Magn. 27, 4903(1991).
	Pt	IEEE Trans. Magn. 36, 2387(2000).
	Pt/Ti, Pd/Ti	J. Mag. Mag. Mater. 242, 311(2002).
Others	Ge, Si	IEEE Trans. Magn. MAG21, 1426(1985).
	C	IEICE Trans. Electron. E85-C, 1745(2002).
	Al ₂ O ₃ (0001)	IEICE Trans. Electron. E85-C, 1733(2002).
	MgO(111)	IEEE Trans. Magn. 45, 2519(2009).

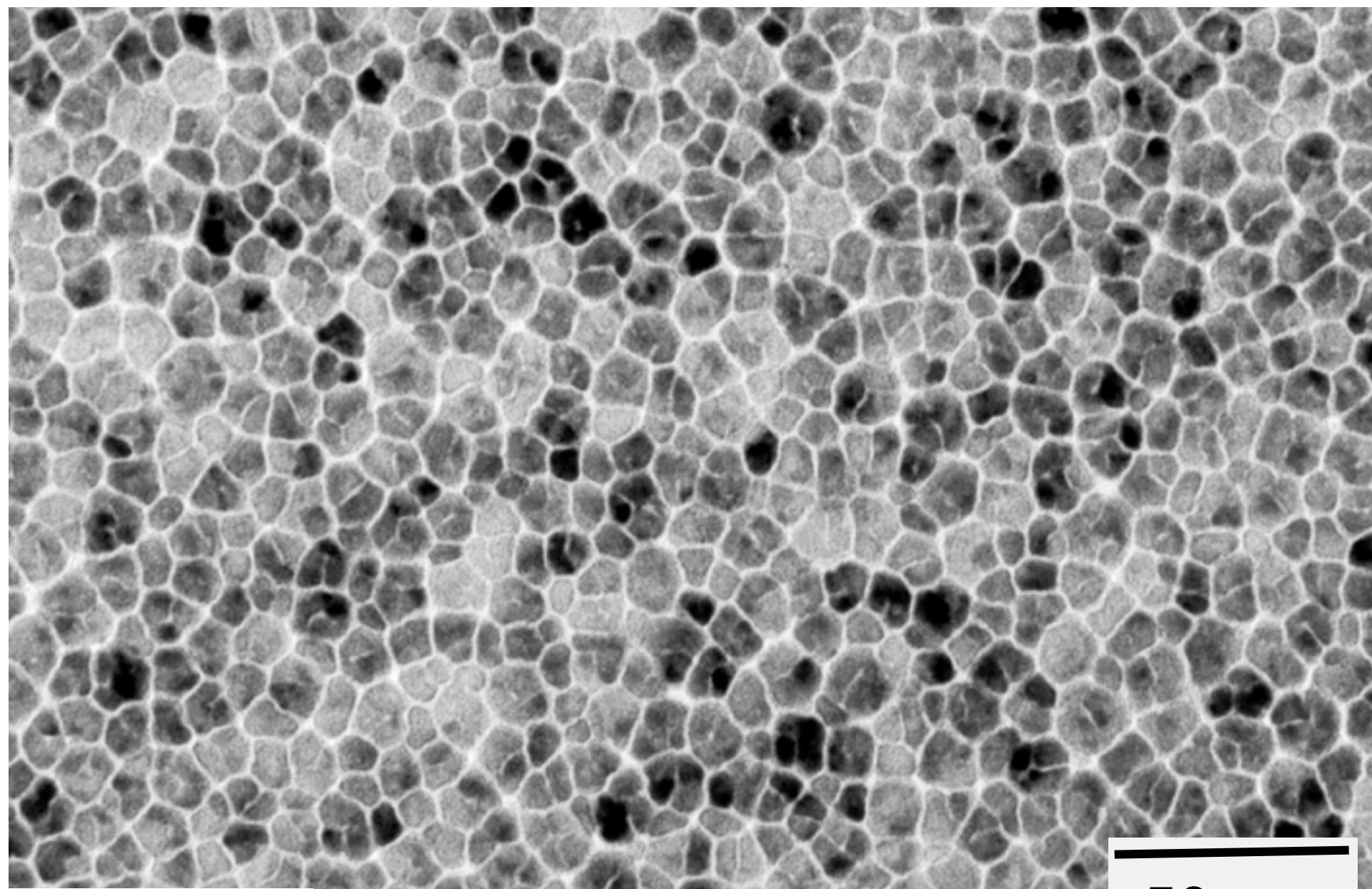
Interface Structure between Co-alloy/Underlayer



Interface Structure between Co-alloy/Ru-Underlayer

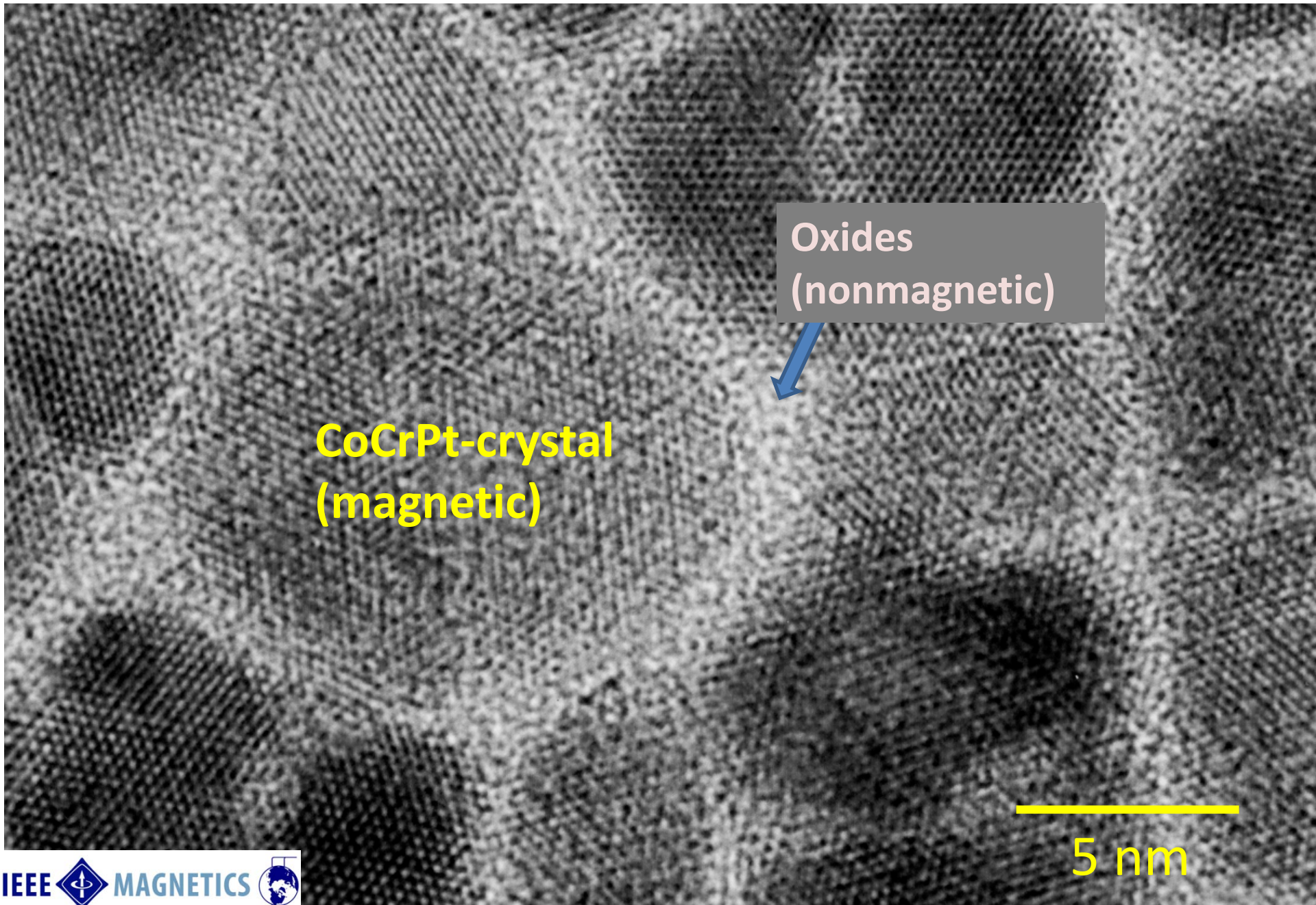


Plan-view TEM of CoCrPt+Oxide Layer

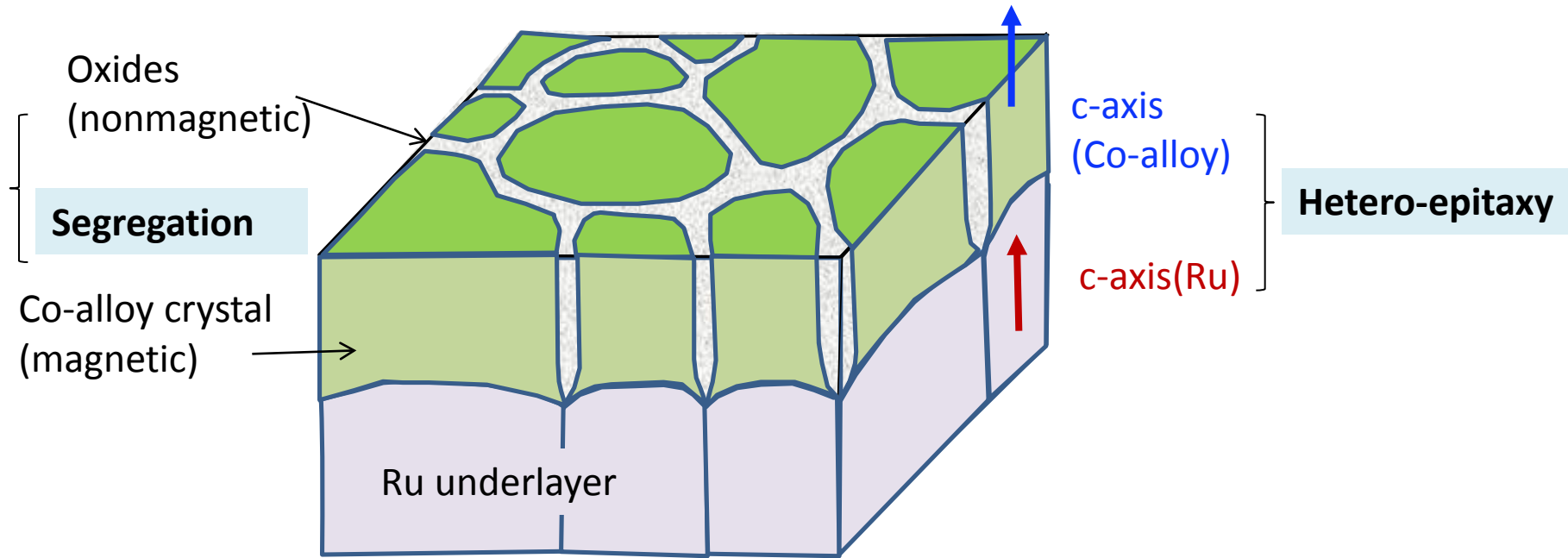


50 nm

Plan-view TEM of CoCrPt+Oxides Layer



Magnetic Crystal Isolation by Oxides Segregation



	Materials	References
Oxides	SiO₂ TiO ₂ MgO, Ta ₂ O ₅ Cr ₂ O ₃ Y ₂ O ₃	IEEE Trans. Magn. 38, 1976(2002). J. Mag. Mag. Mater. 28,167(2005). IEEE Trans. Magn. 41, 3142(2005). J. Appl. Phys., 95, 102507(2009). IEEE Trans. Magn. 46, 2260(2010).
Others	C Ag, Au, Cu, etc.	IEEE Trans. Magn. 34, 1132(1998). Many references

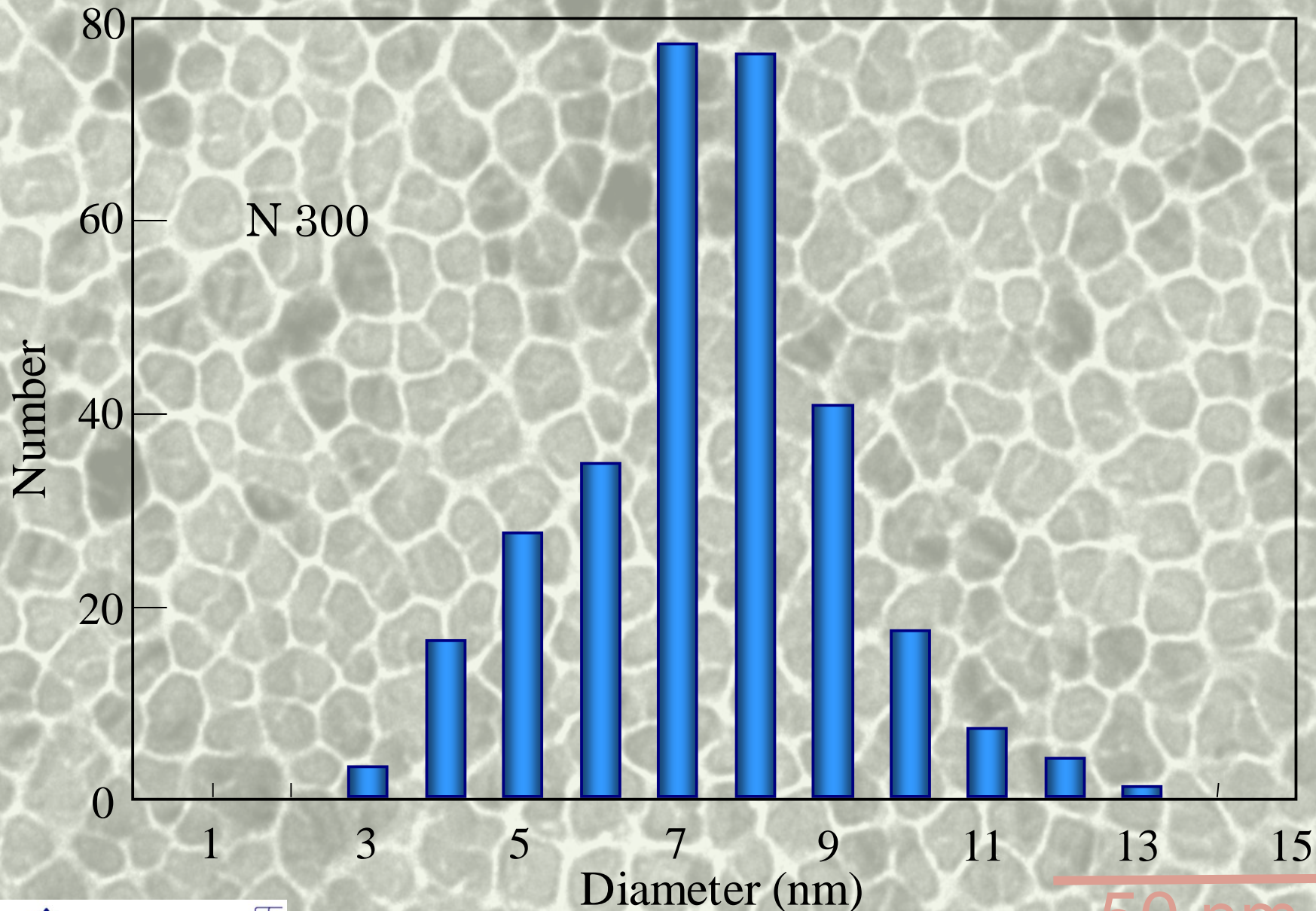
Local Composition Measurement by EDX-TEM

Focused electron beam
Diameter: 1.5 nm ϕ

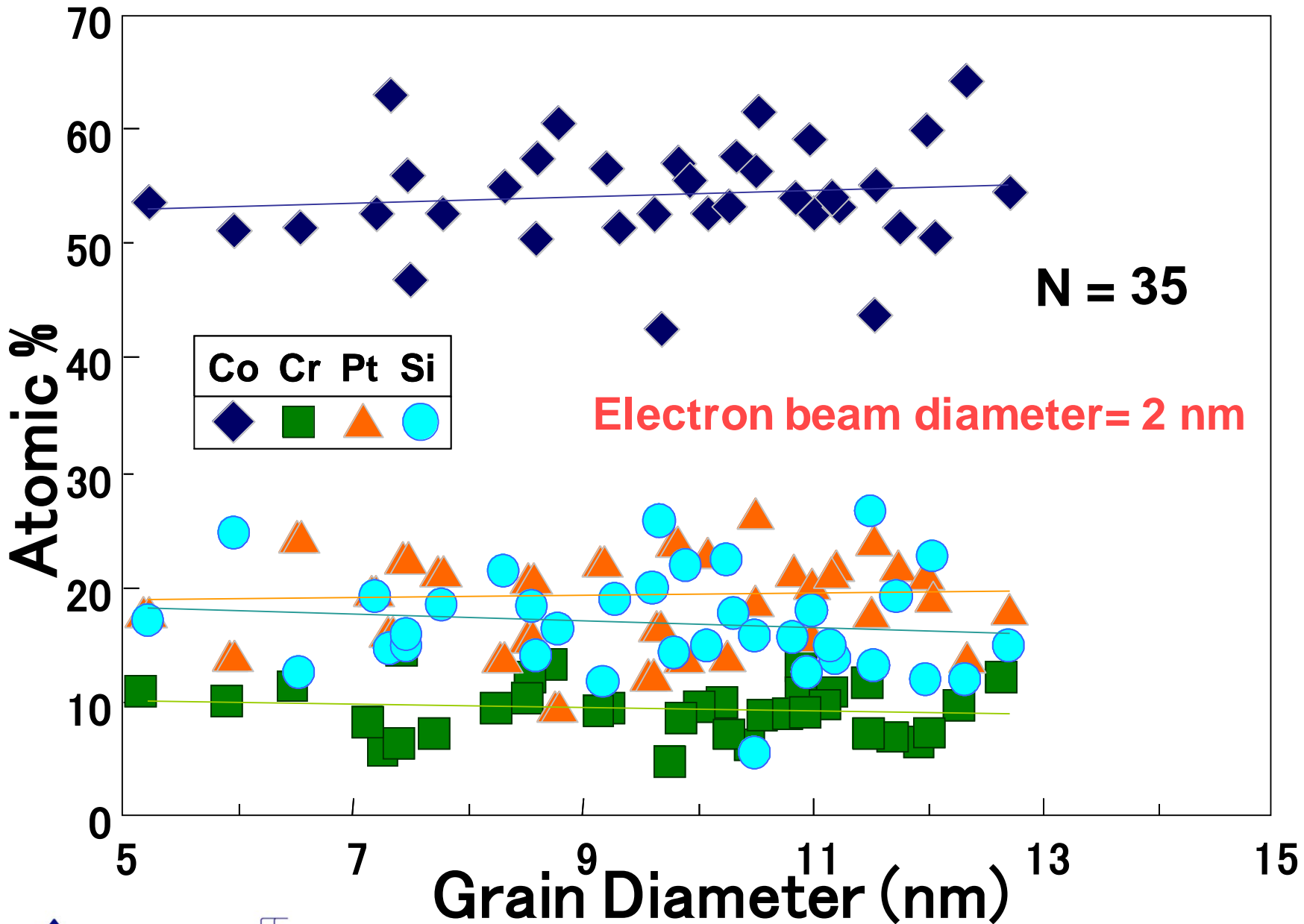


10 nm

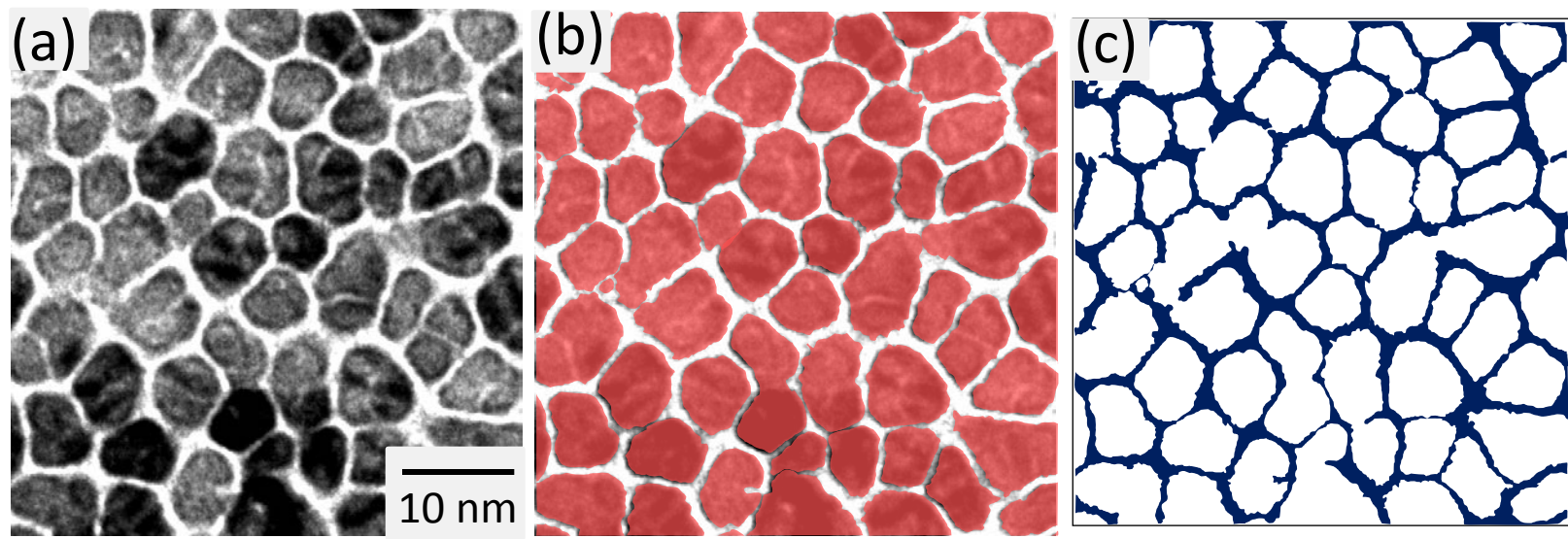
Crystal Grain Size Distribution



Composition Dependence on Crystal Grain Diameter



Estimation of Crystal Grain Boundary Composition



Plan-view TEM

Extraction of crystal grain profiles

Grain boundaries

Total volume
*
Average composition
(grain + boundaries)

Grain volume
*
Grain composition

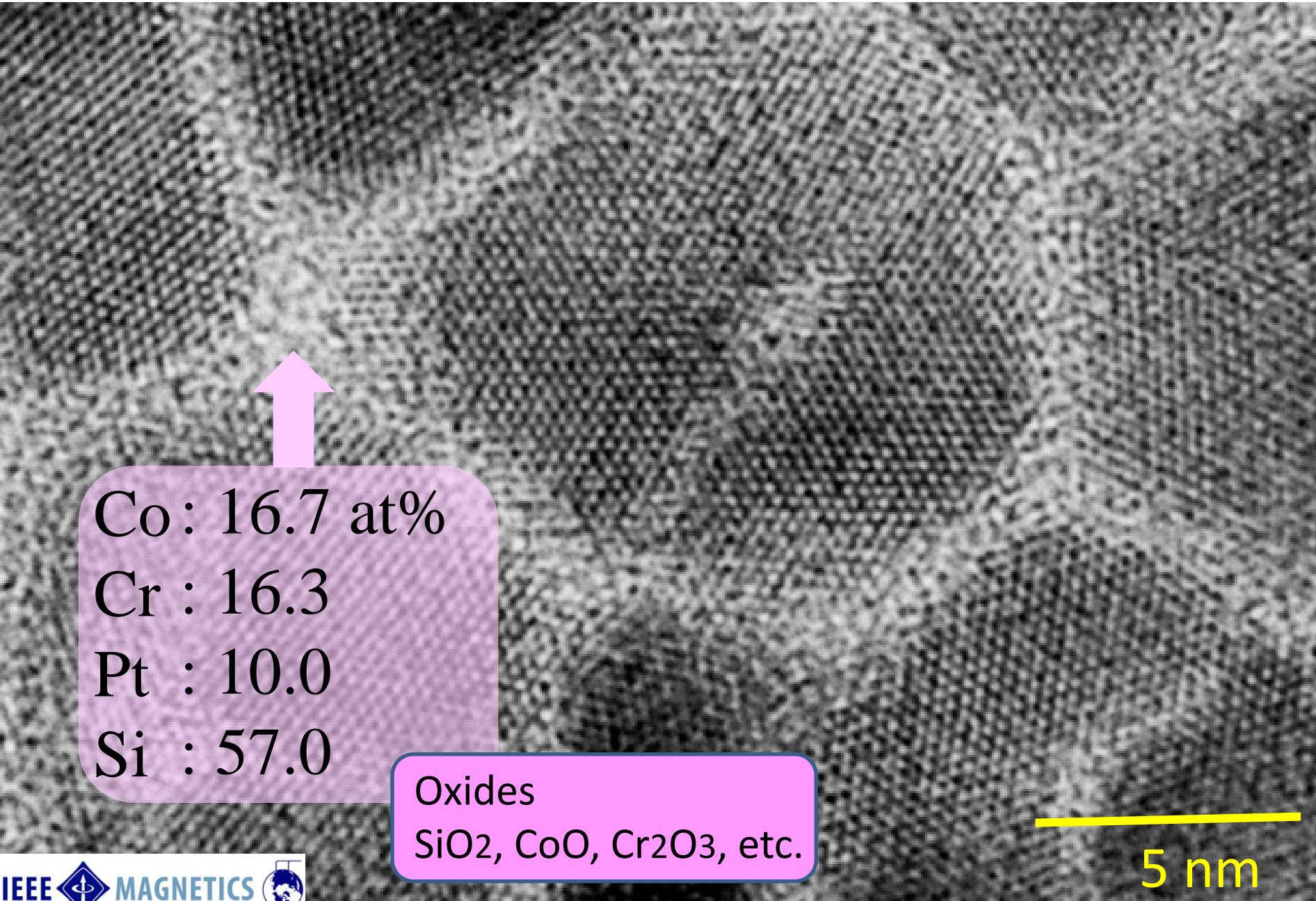
Boundary volume
*
Boundary composition

Co : 48.2 at%
Cr : 10.5
Pt : 17.9
Si : 23.4

Co : 54.2 at%
Cr : 9.4
Pt : 19.4
Si : 17.0

Co : 16.7 at%
Cr : 16.3
Pt : 10.0
Si : 57.0

Average Composition of Crystal Grain Boundaries



Co : 16.7 at%

Cr : 16.3

Pt : 10.0

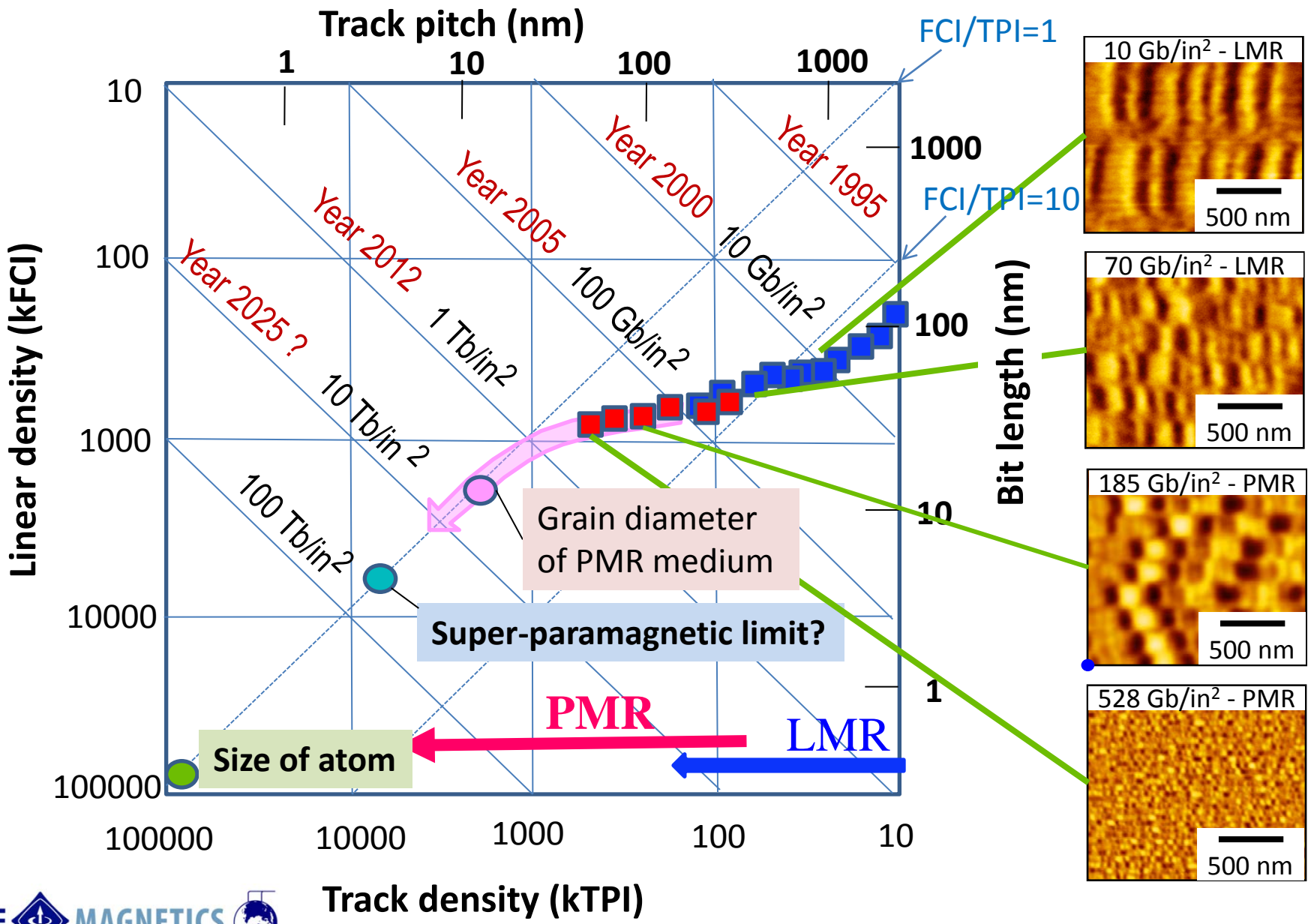
Si : 57.0

Oxides

SiO₂, CoO, Cr₂O₃, etc.

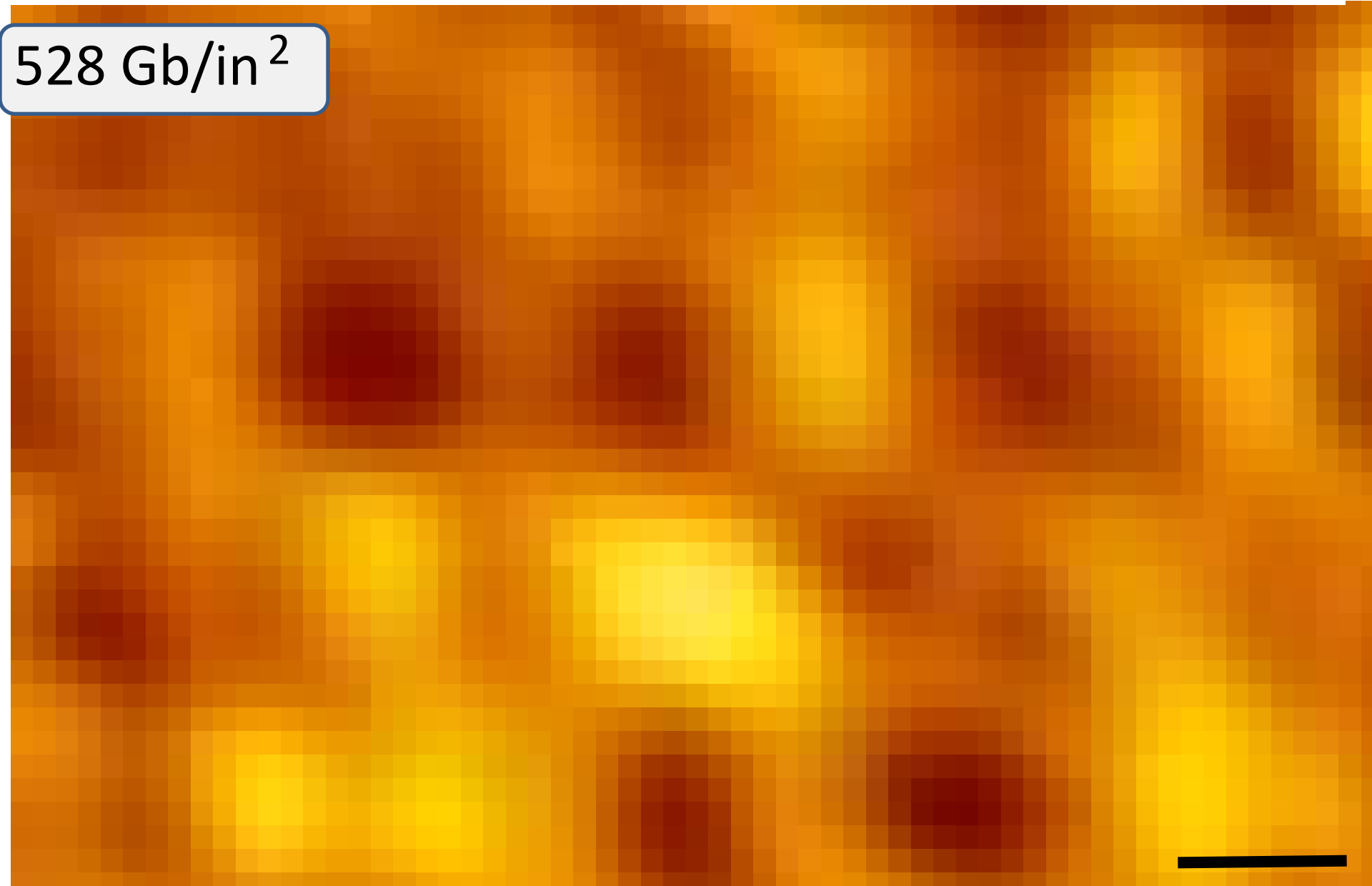
5 nm

Decreasing Trend of Recording Bit Size in HDDs



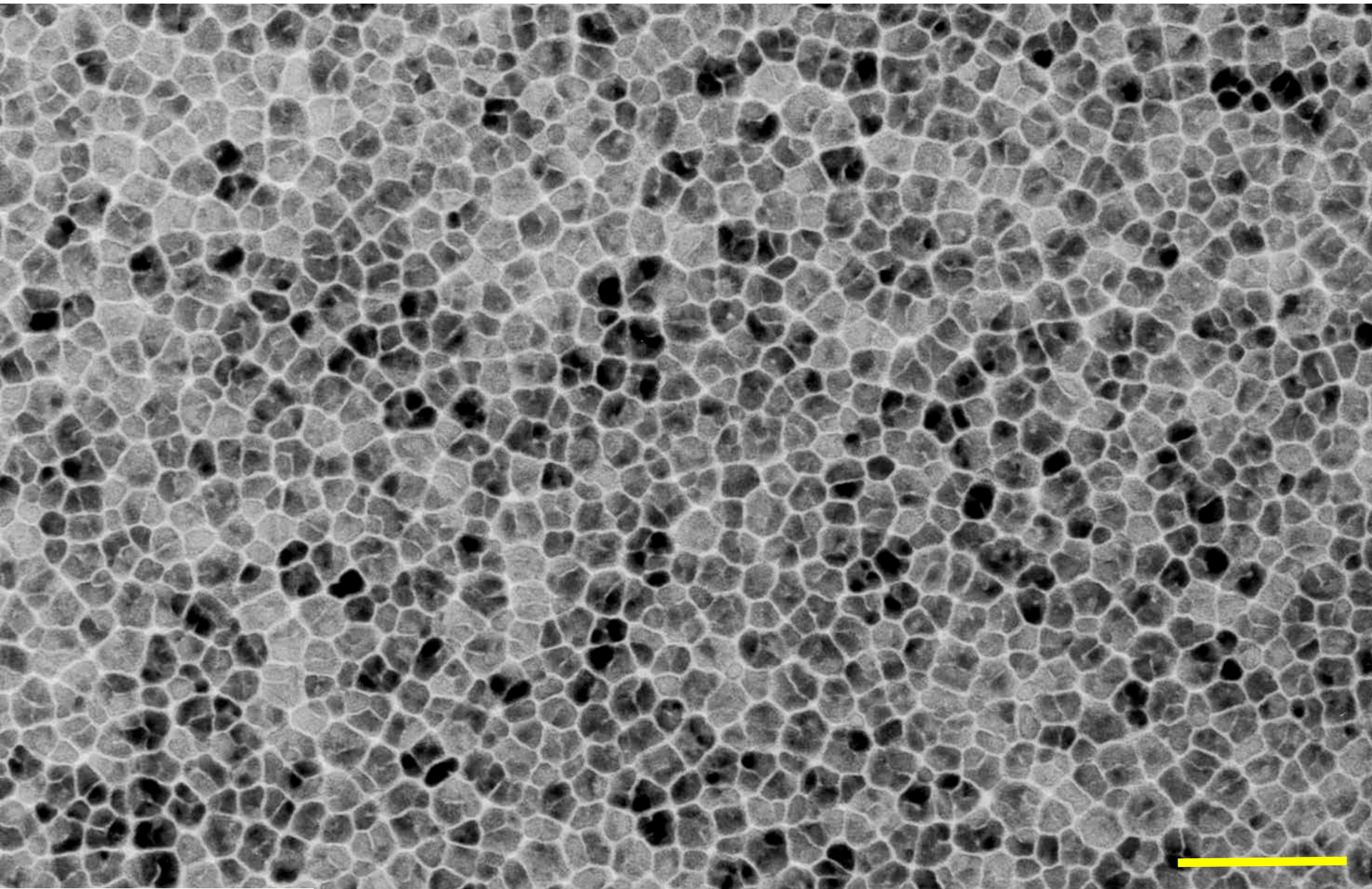
Relation between Bit Size and Crystal Grains

528 Gb/in²



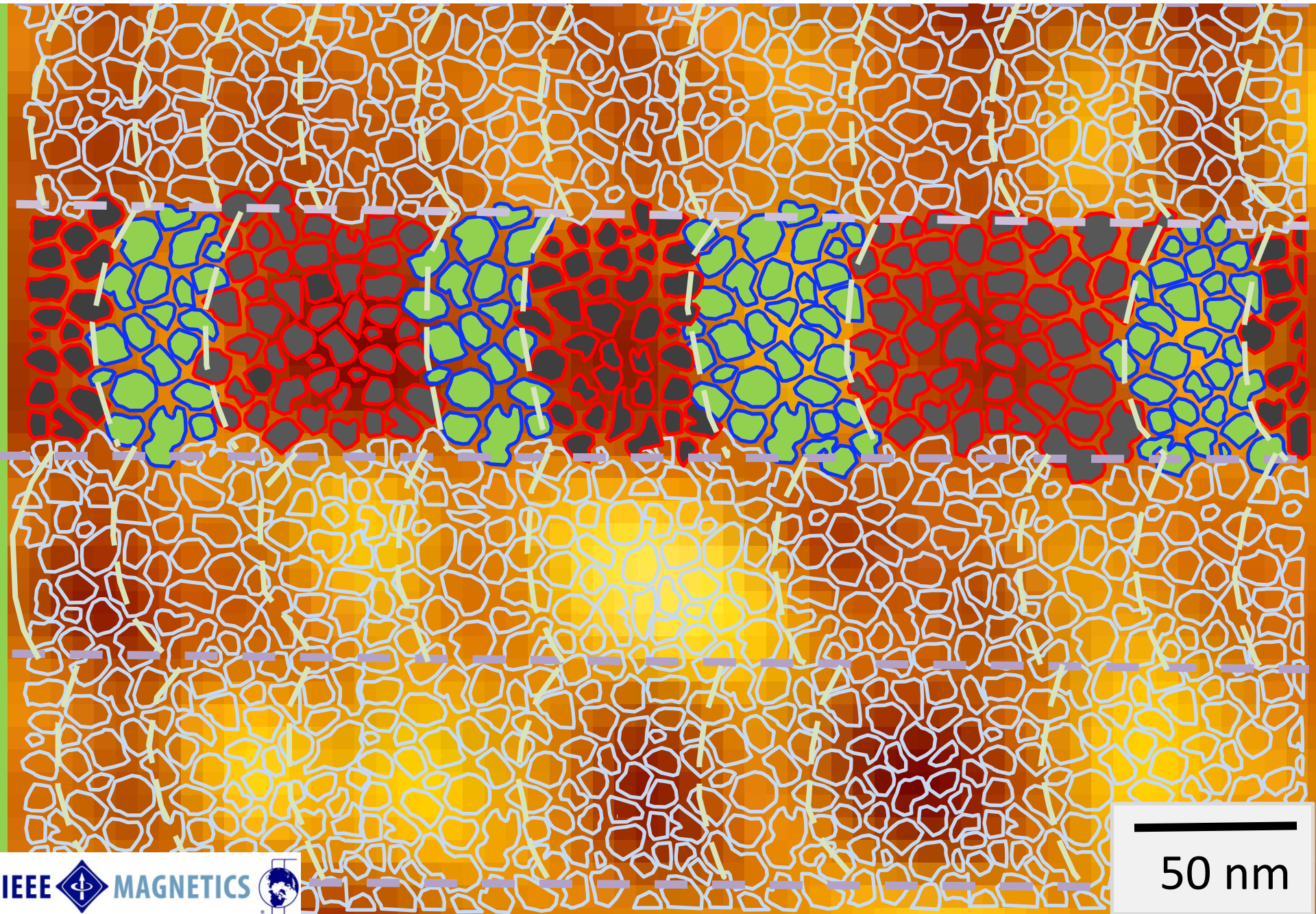
50 nm

Relation between Bit Size and Crystal Grains

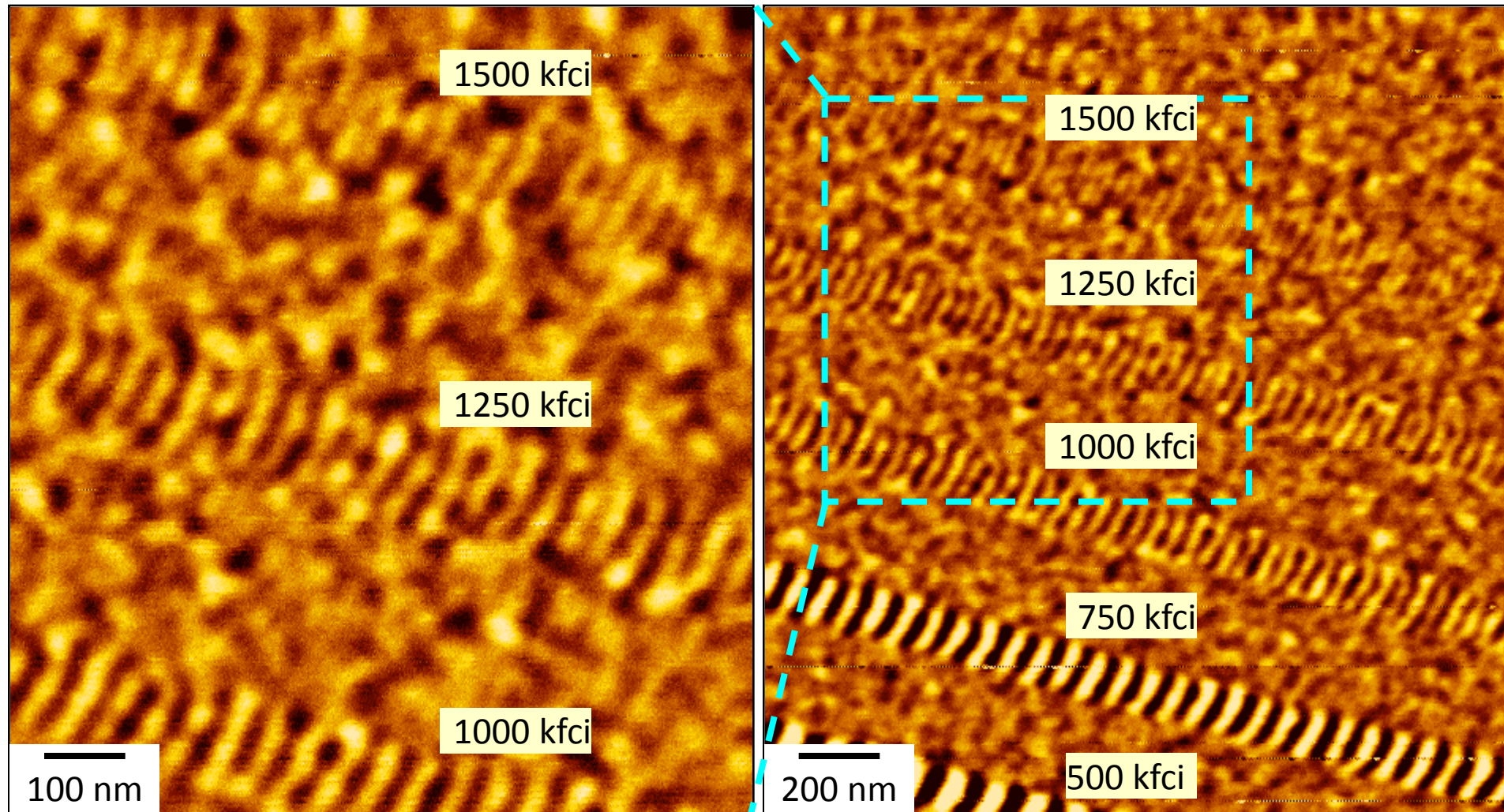


50 nm

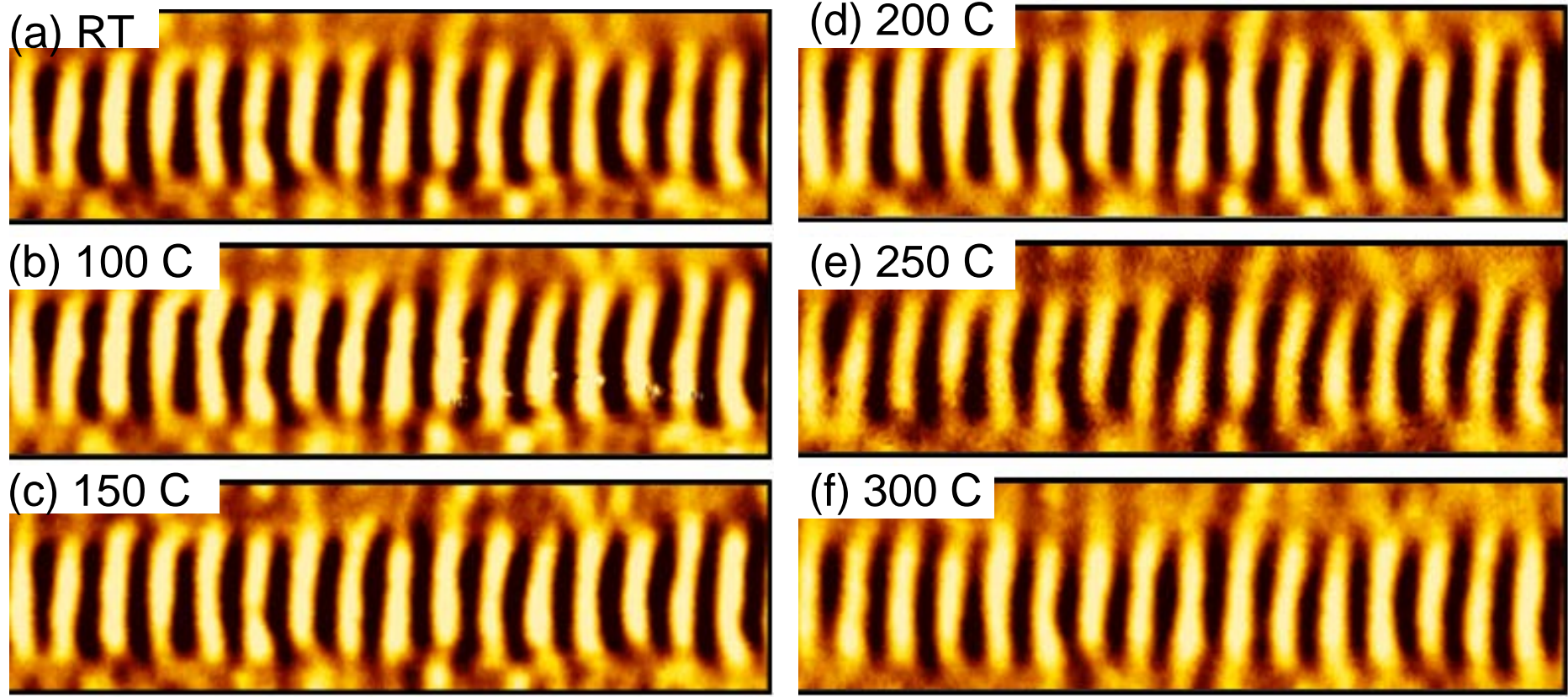
Relation between Bit Size and Crystal Grains



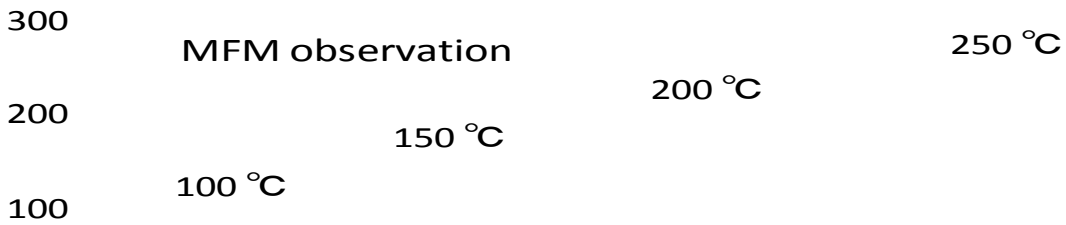
Recording Density Possibility of PMR Media



Stability of Recorded Bit Information (Thermal)



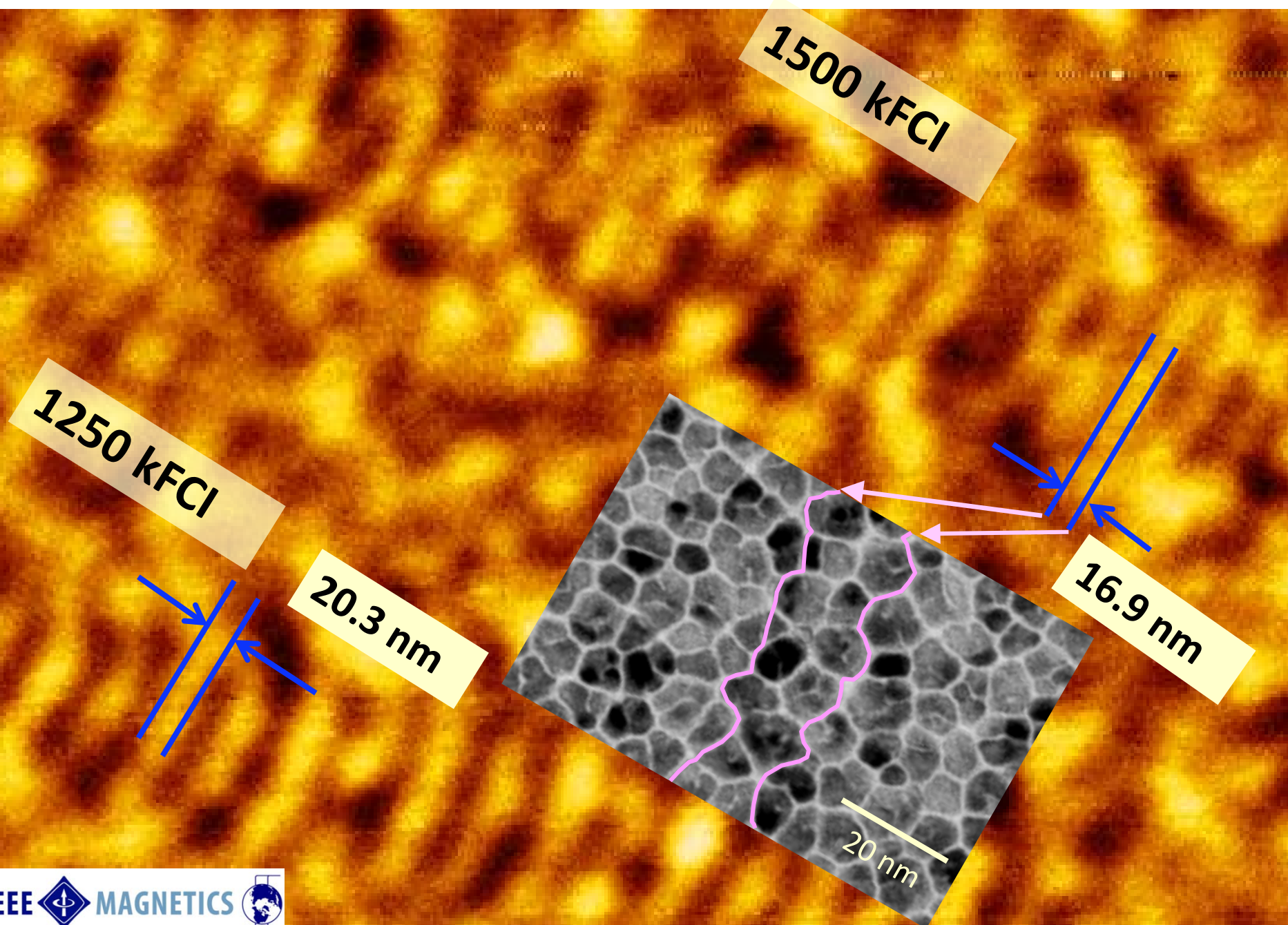
750 kFCI 200 nm



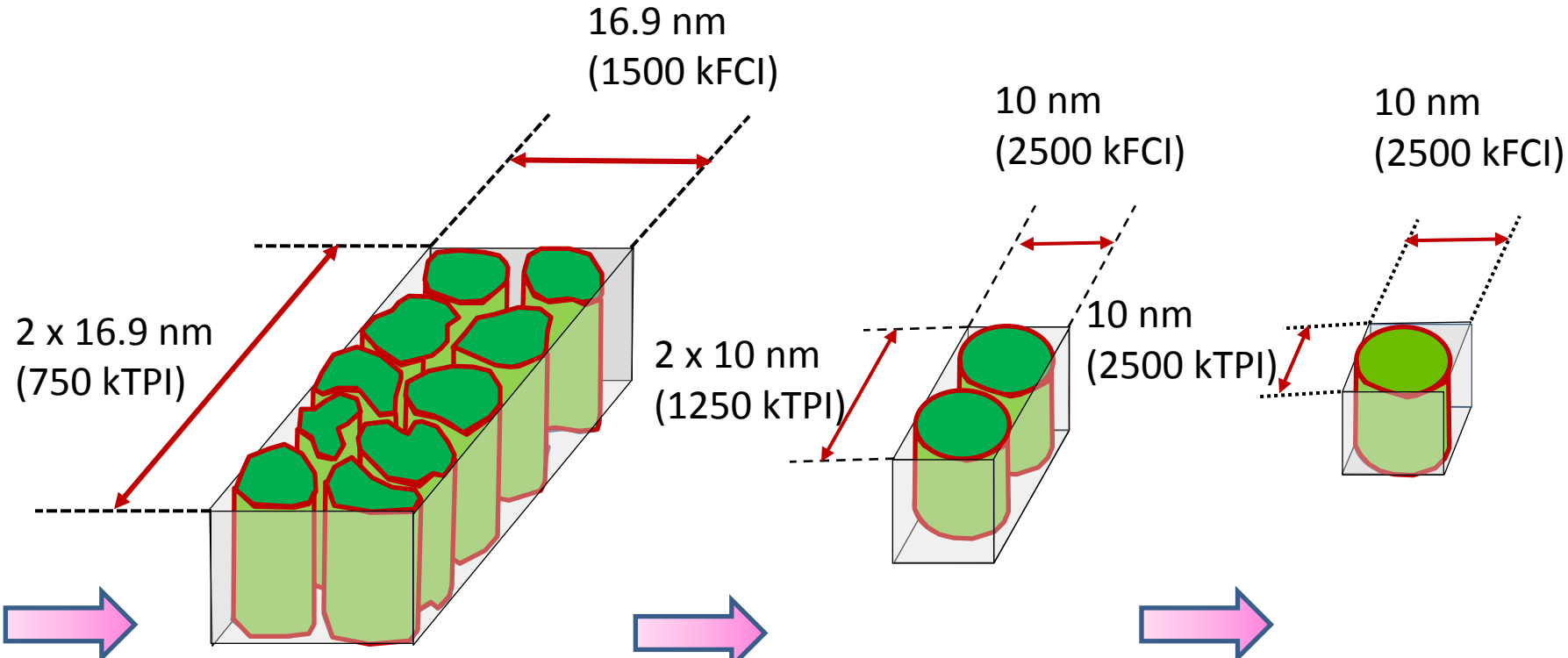
Heating time: 60 min at every temperature

Time

Recording Density Possibility of Current PMR Media



Recording Density Possibility of Future PMR Media



Area density
1.1 Tb/in²

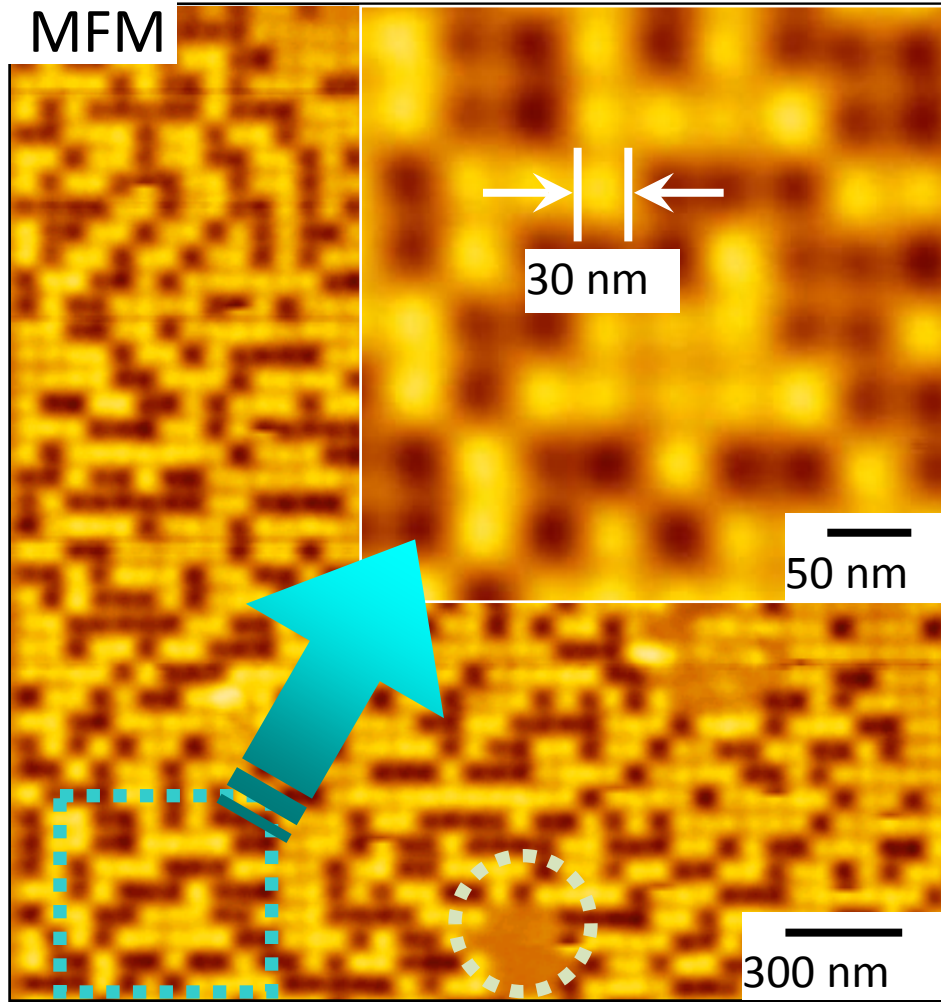
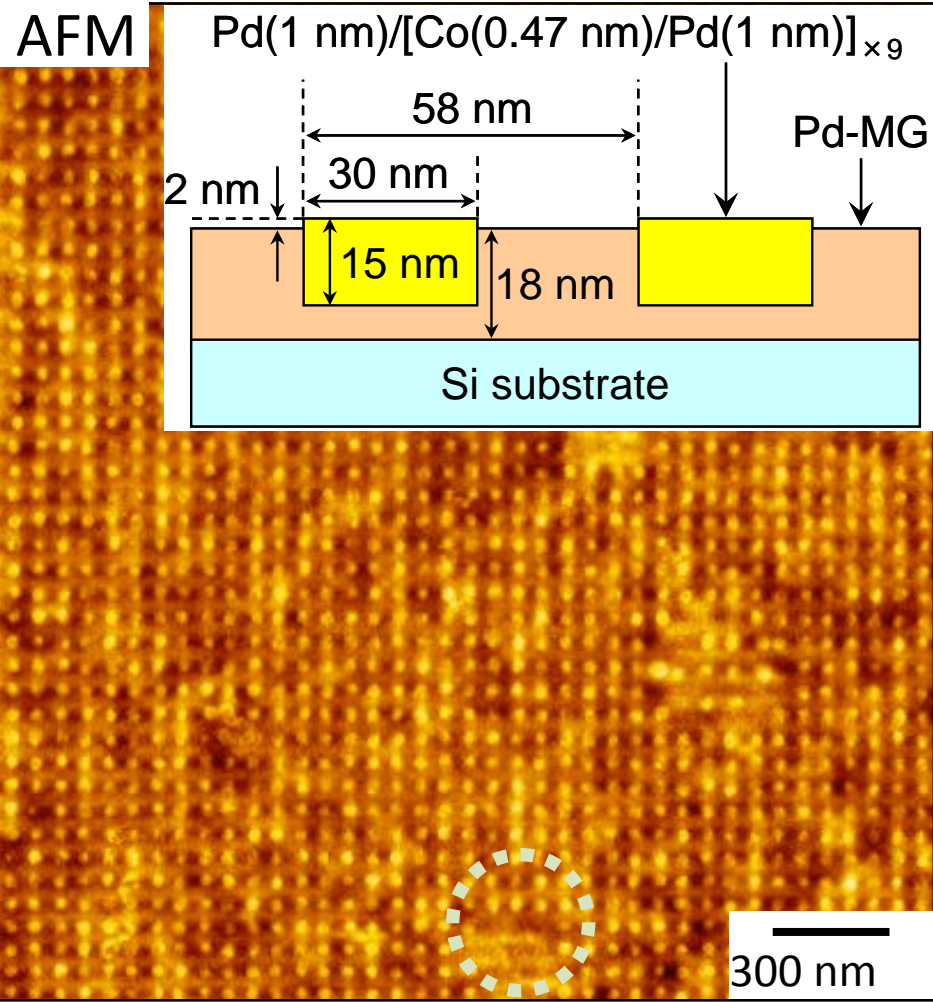
3.1 Tb/in²

6.3 Tb/in²

Recording Density Possibility of Future PMR Media

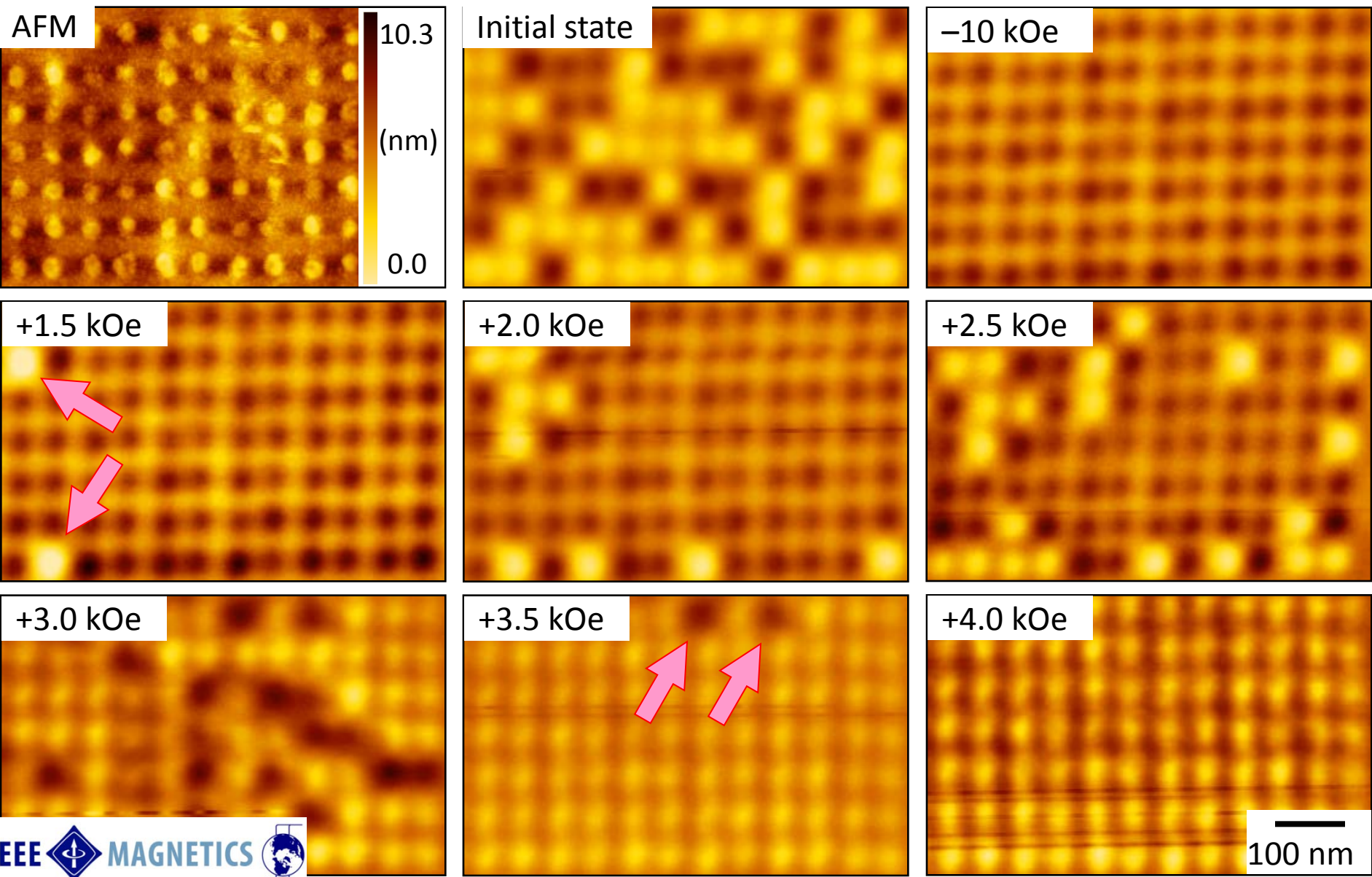
Diameter & Position Control : Bit Patterned Media

■ Diameter: 30 nm
 ■ Pitch: 58 nm



Recording Density Possibility of Future PMR Media

Diameter & Position Control : Bit Patterned Media



Summary for PMR Media

1. Brief history of PMR research & development

- * **Co-alloy media microstructure developments**

2. Current PMR Media

- * **Nano-crystallographic, nano-compositional, and nano-magnetization structures**

3. Future possibilities of PMR Media

- * **Up to several Tb/in² seems feasible**

→ **Various parameter control required**

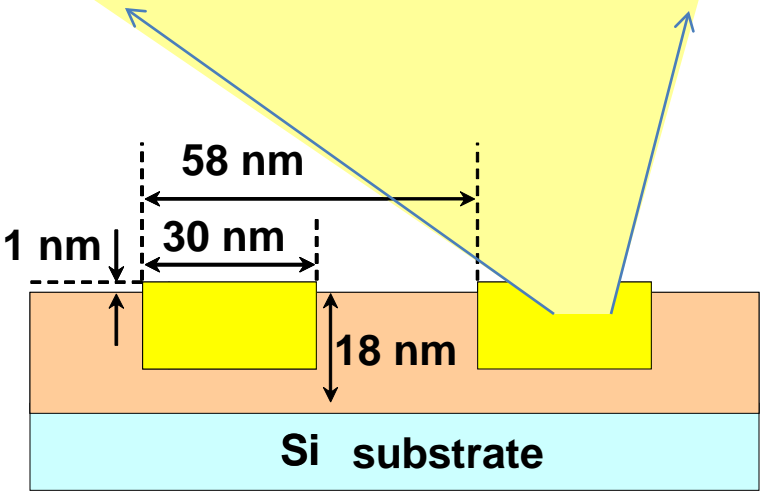
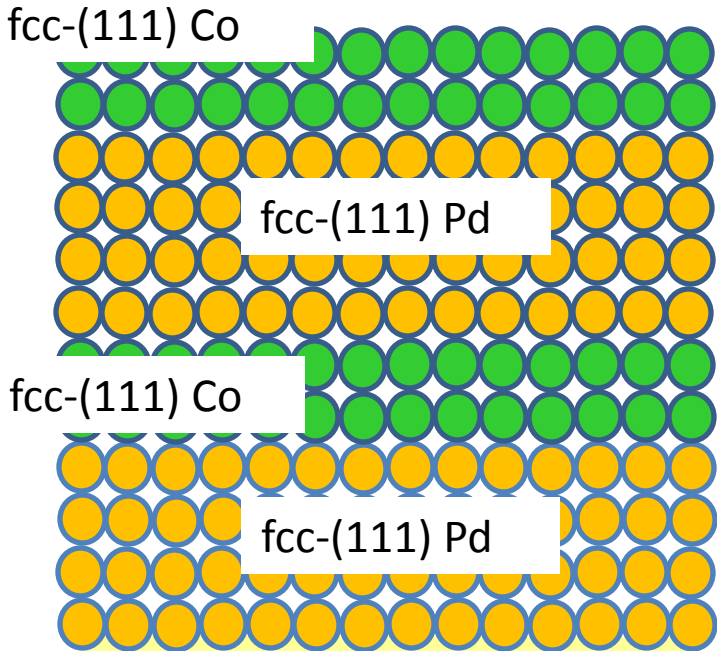
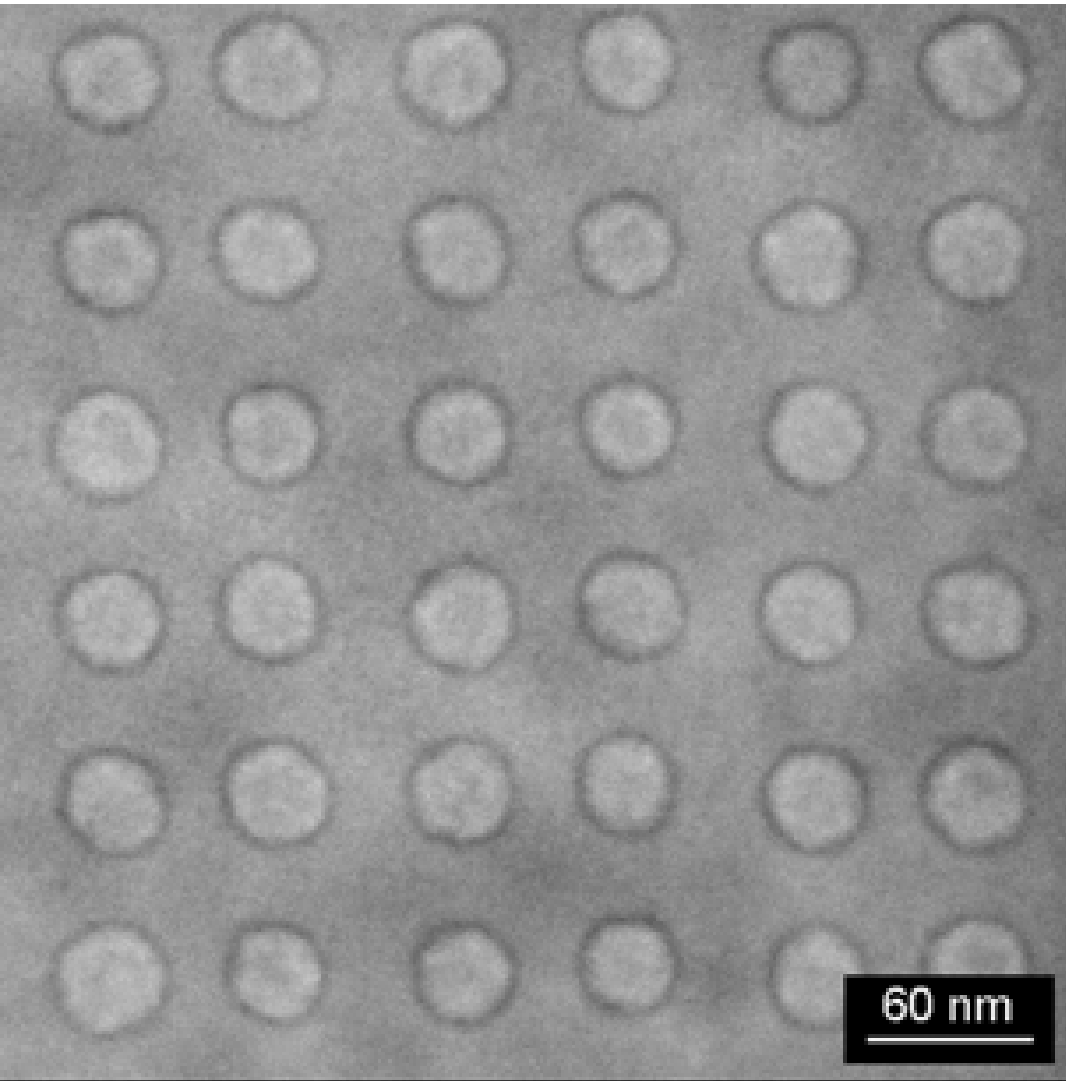
- * **Grain diameter**

- * **Two-dimensional grain distribution**

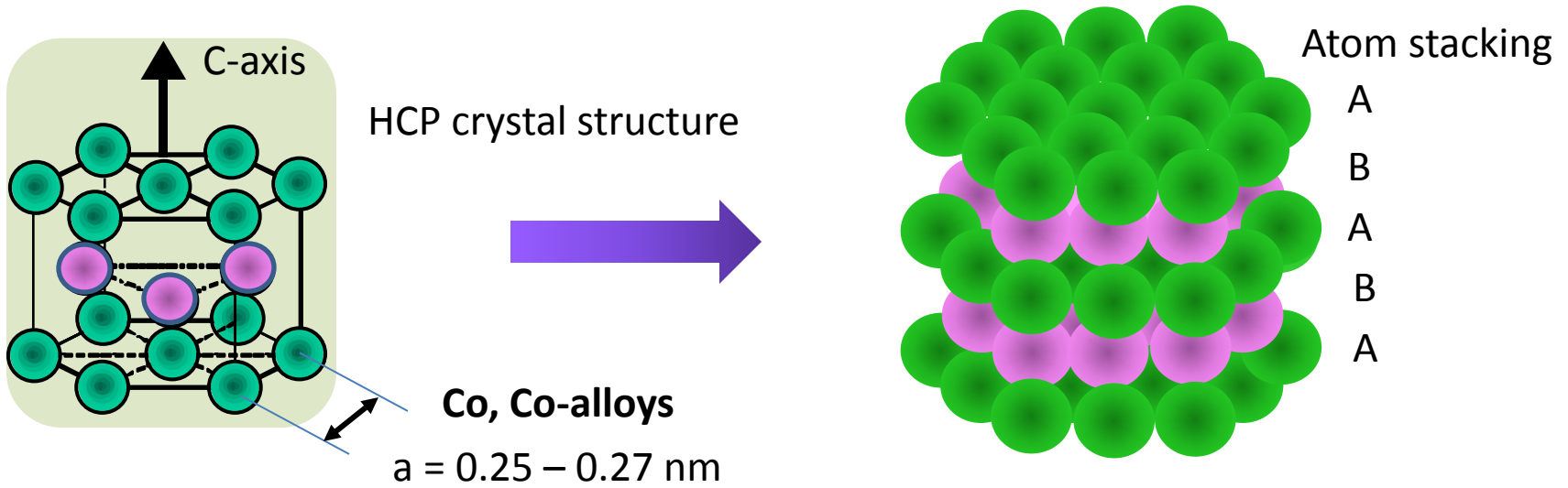
- * **Magnetization switching field distribution, etc.**

Structure of Co/Pd multilayer magnetic dots

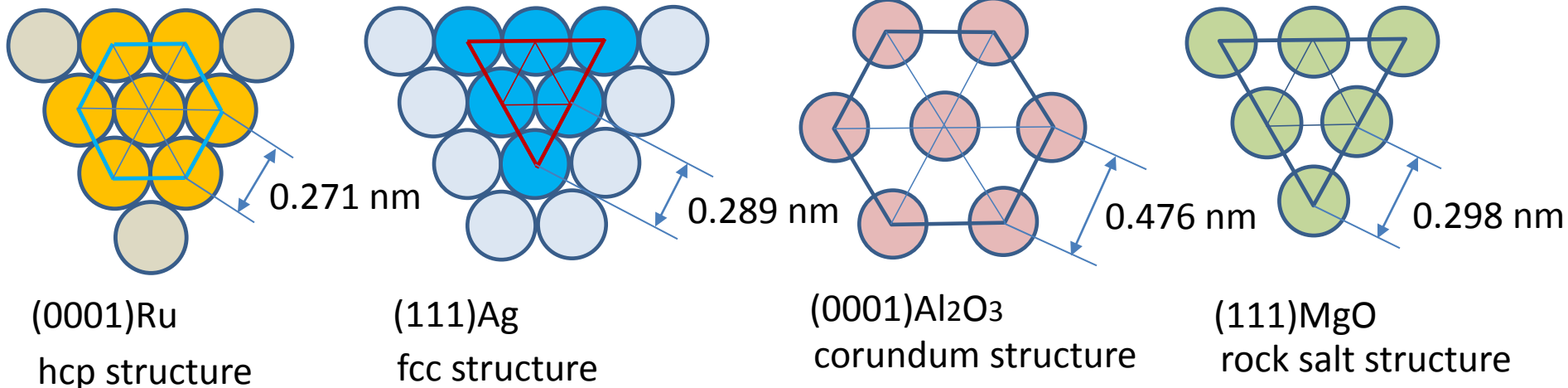
Pd(1 nm)/[Co(0.47 nm)/Pd(1 nm)]x9



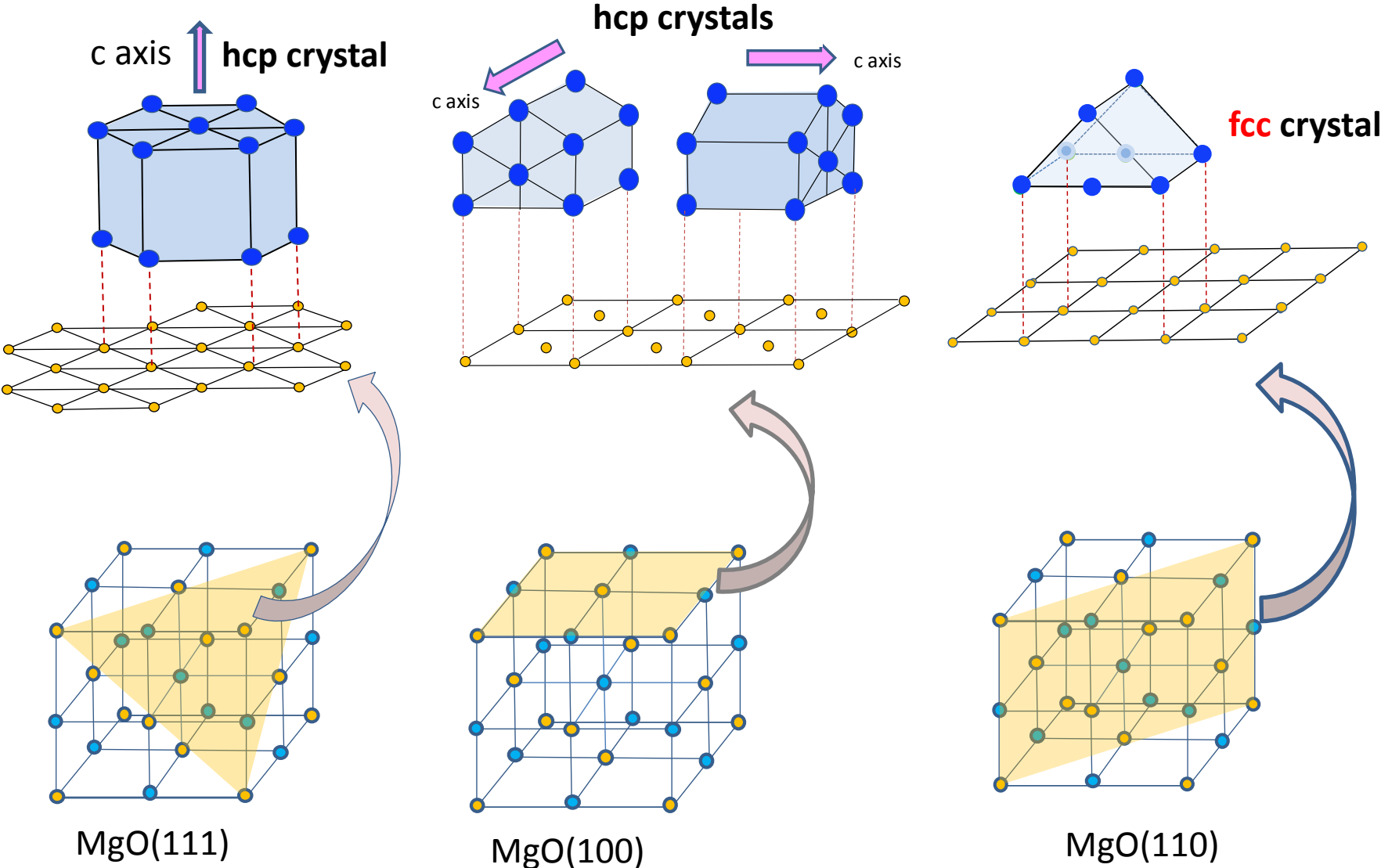
Epitaxial Growth of hcp-Co film on underlayers



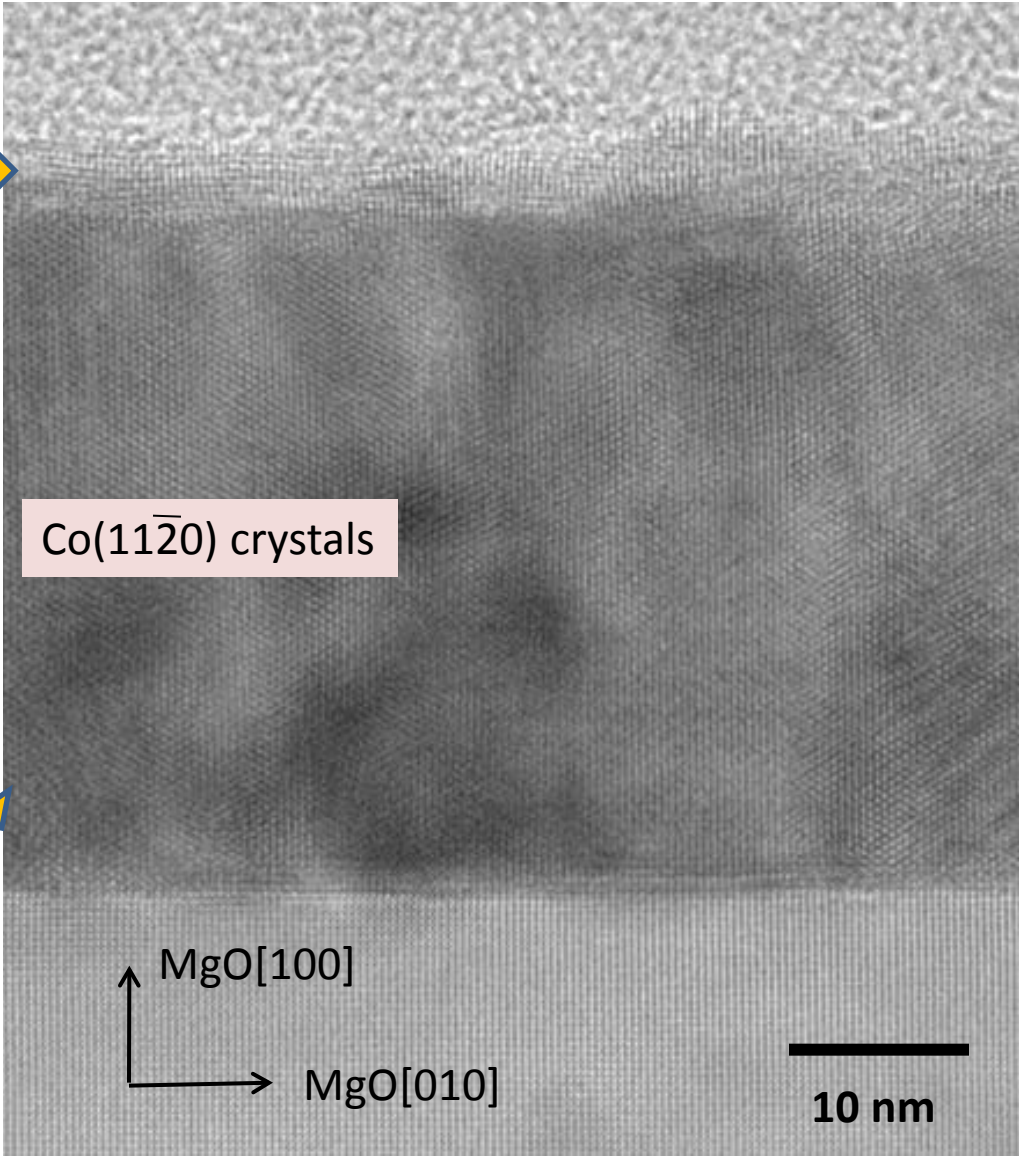
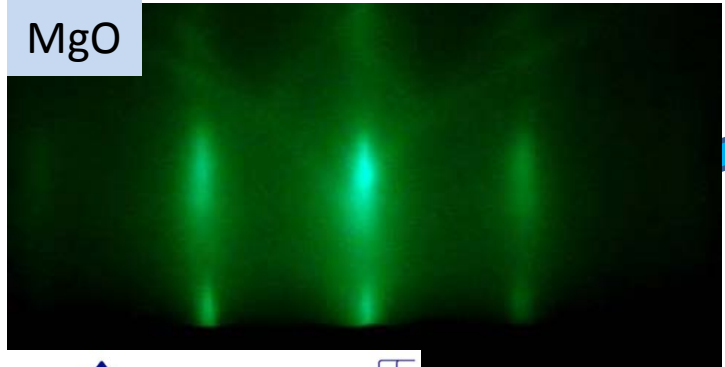
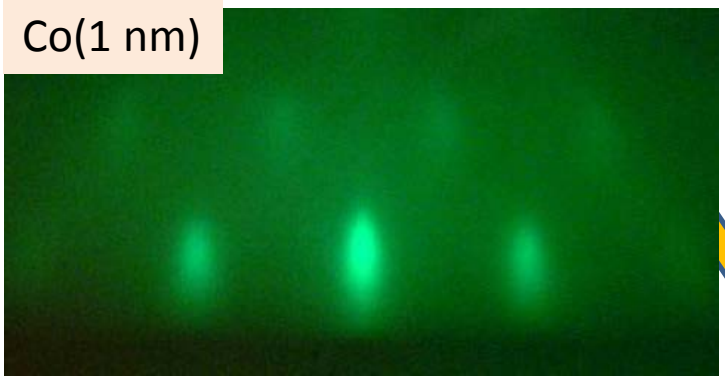
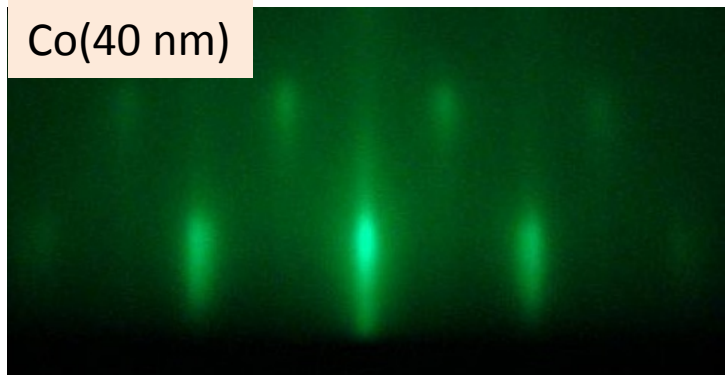
[Underlayers for hetero-epitaxial growth of Co, Co-alloy crystals]



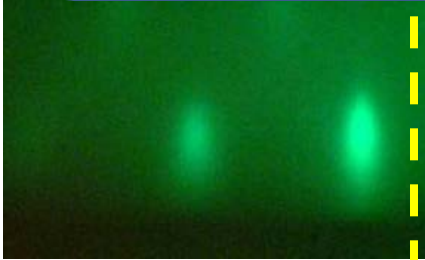
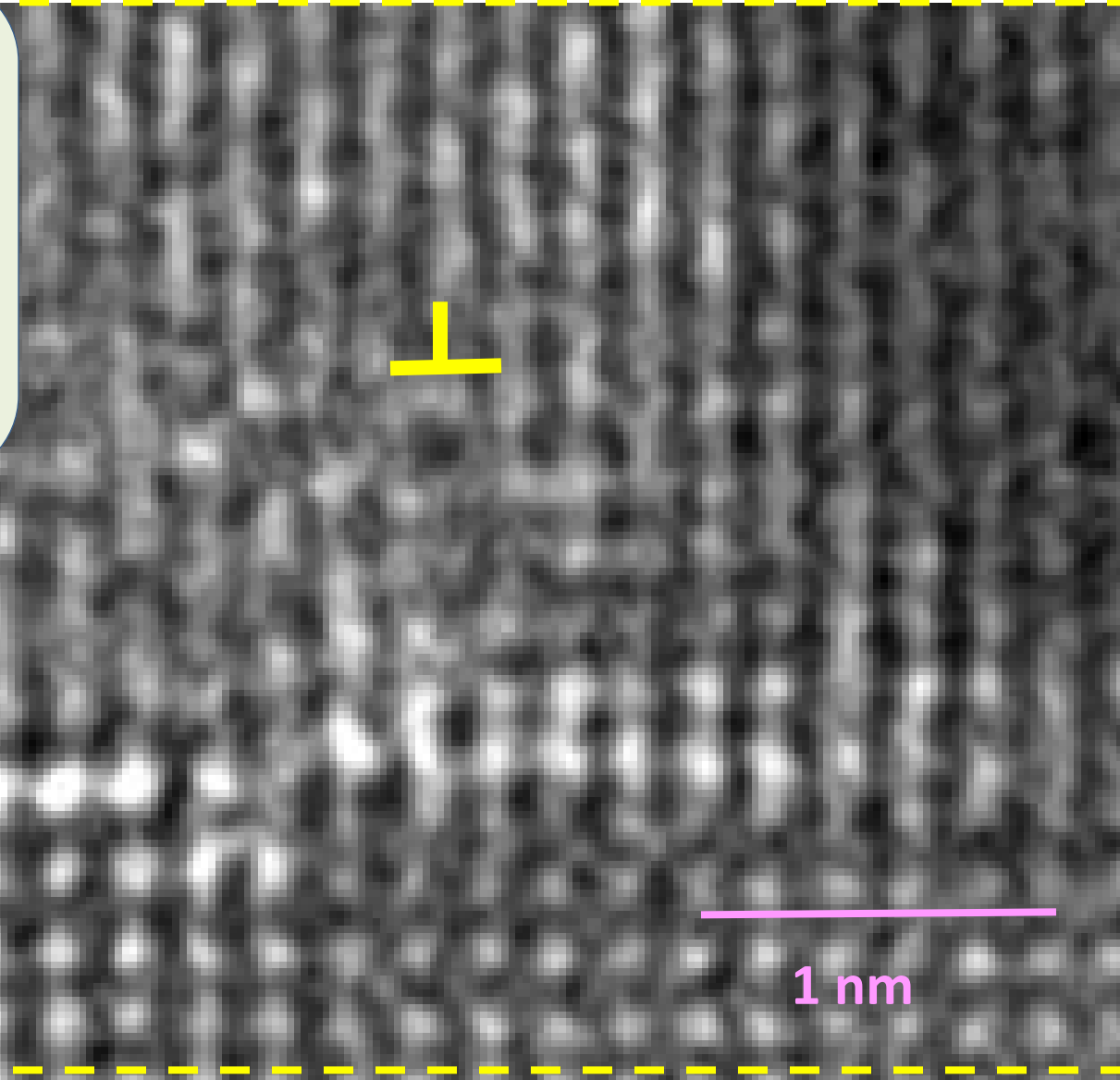
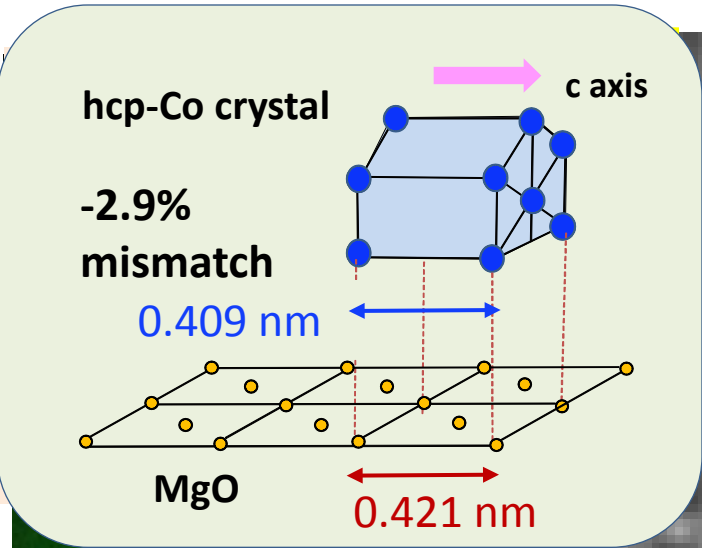
Epitaxial Growth of Co Film on MgO Crystals



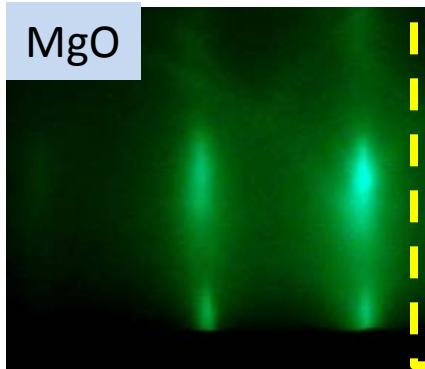
Growth of hcp-Co on MgO(100) Crystal Surface



Growth of hcp-Co on MgO(100) Crystal Surface



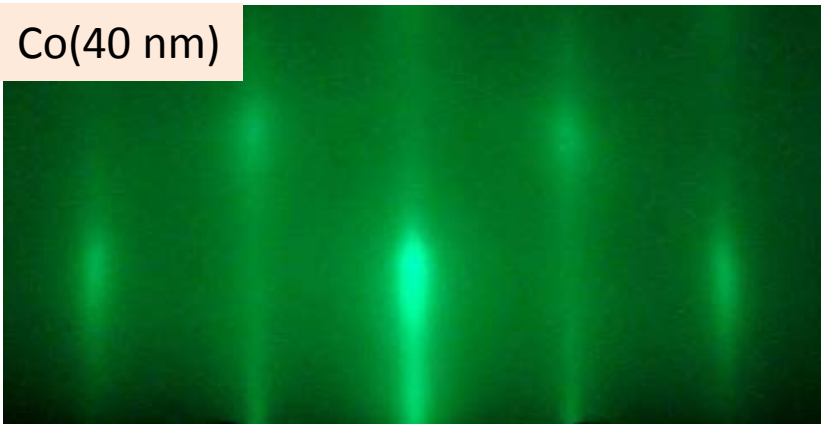
hcp-Co



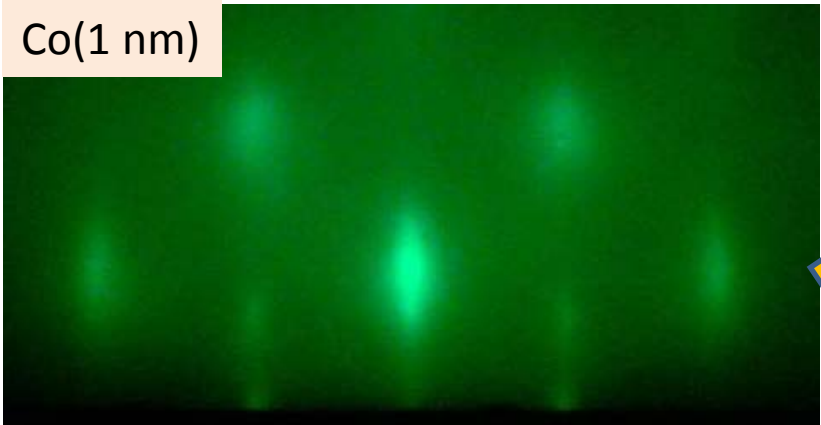
MgO

Growth of fcc-Co on MgO(110) Crystal Surface

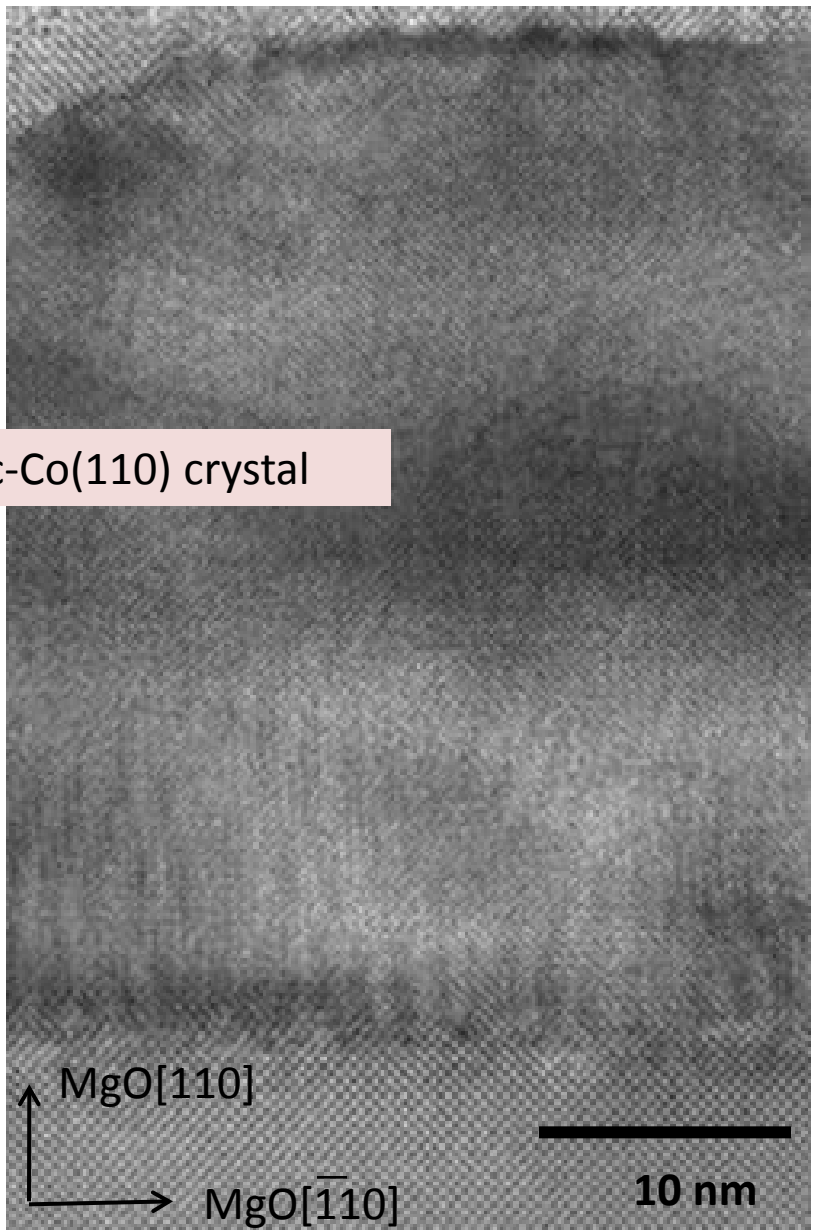
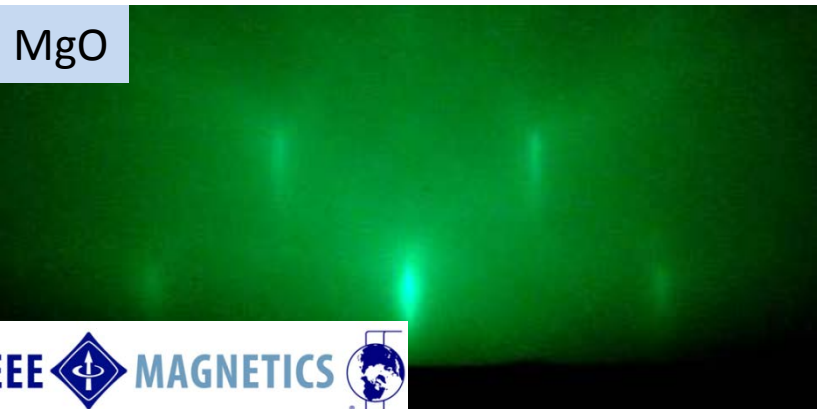
Co(40 nm)



Co(1 nm)



MgO



fcc-Co(110) crystal

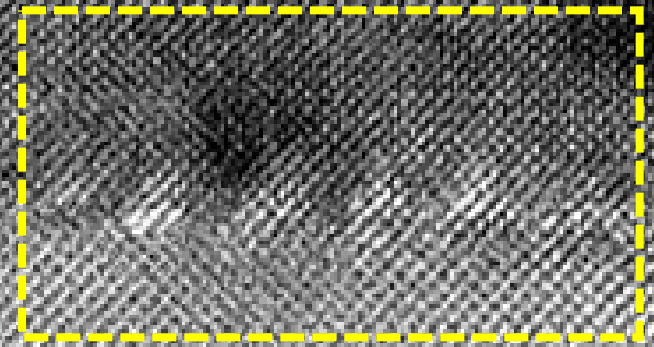
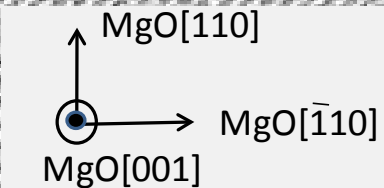
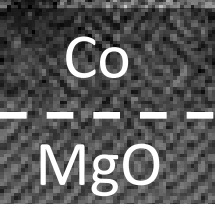
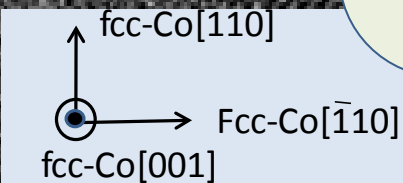
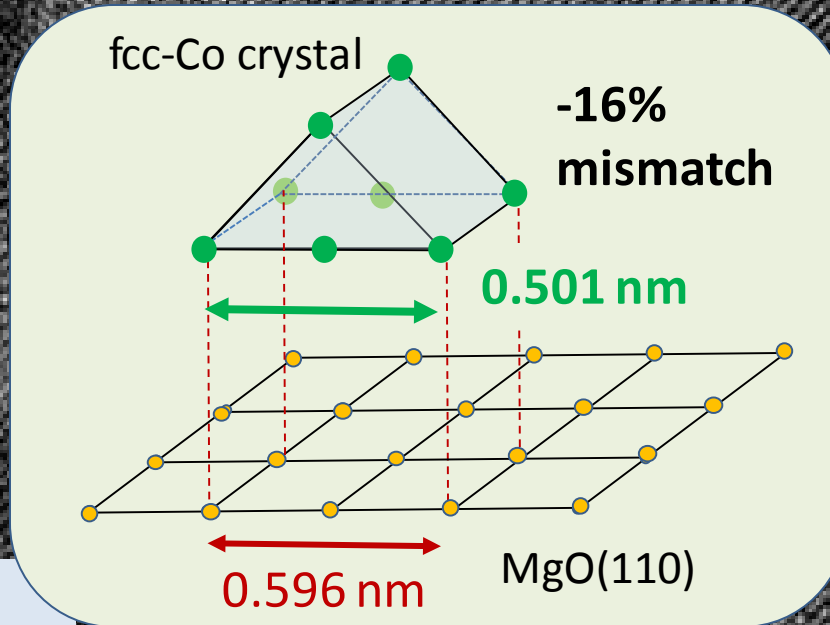
MgO[110]

MgO[110]

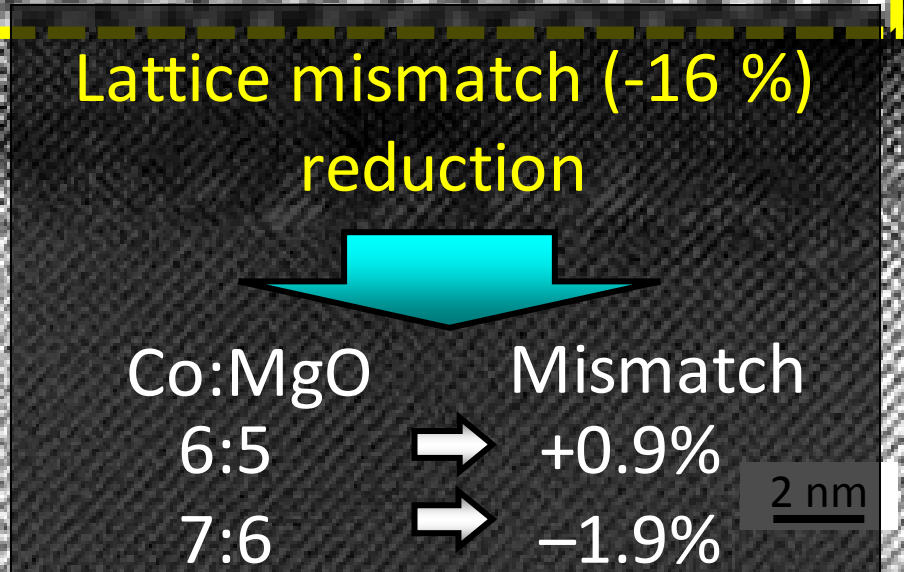
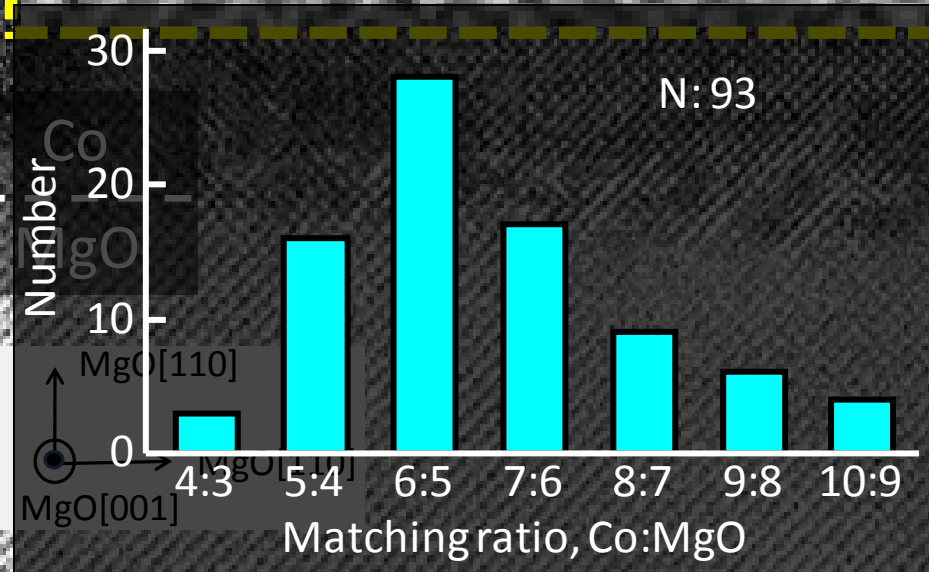
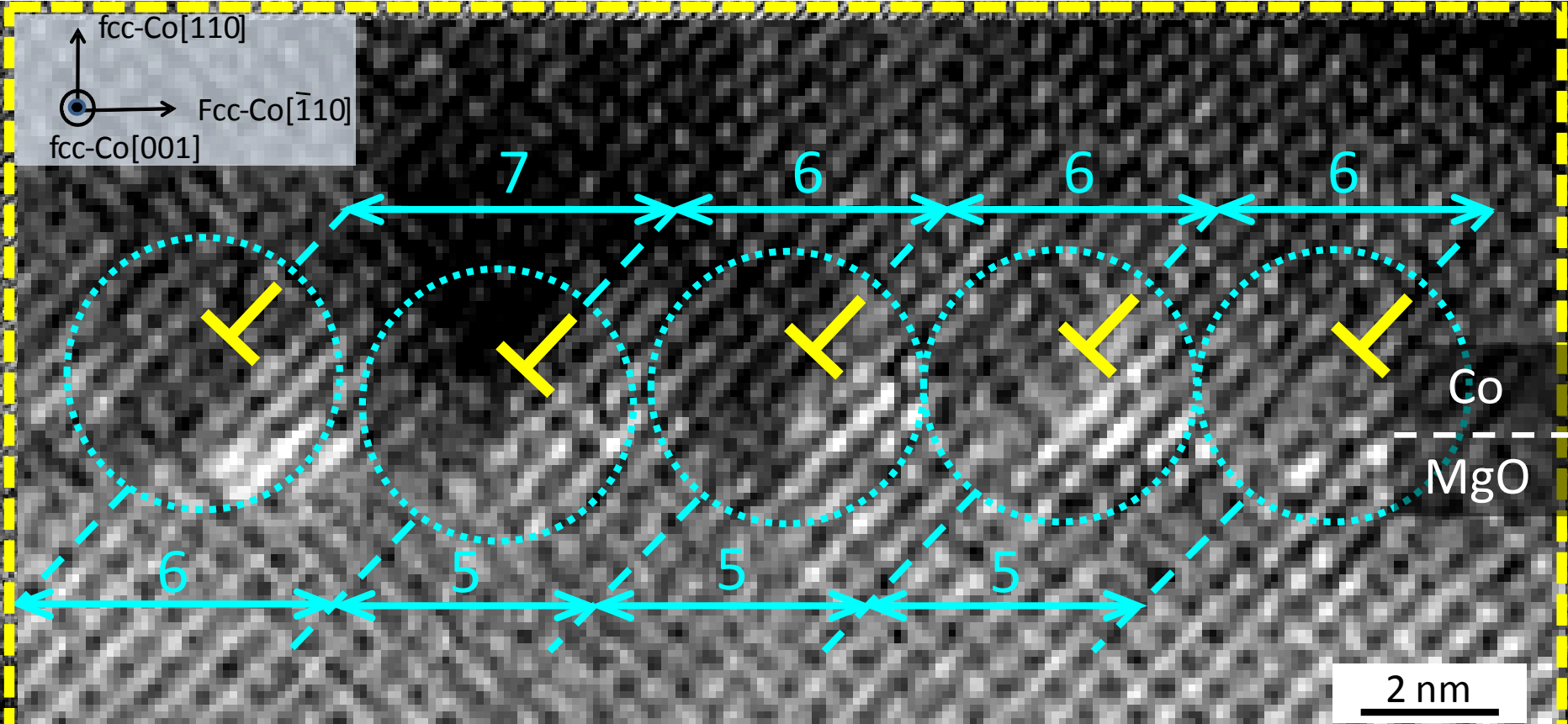


10 nm

Growth of fcc-Co on MgO(110) Crystal Surface



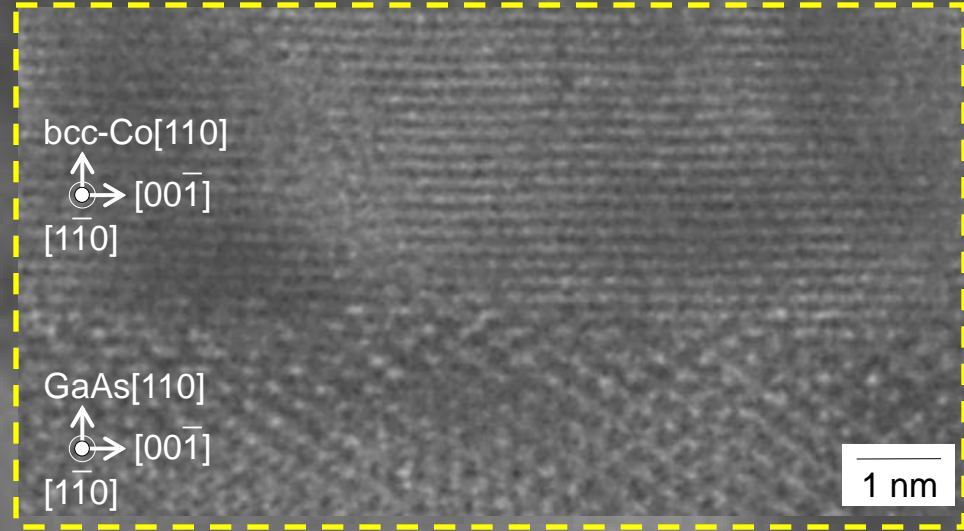
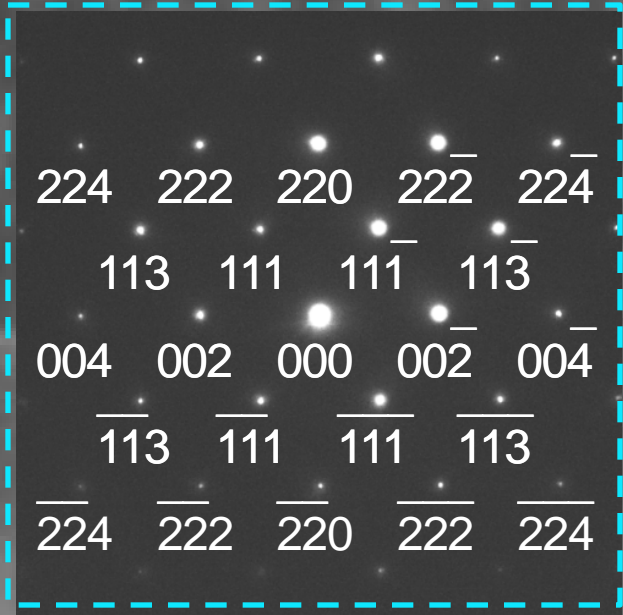
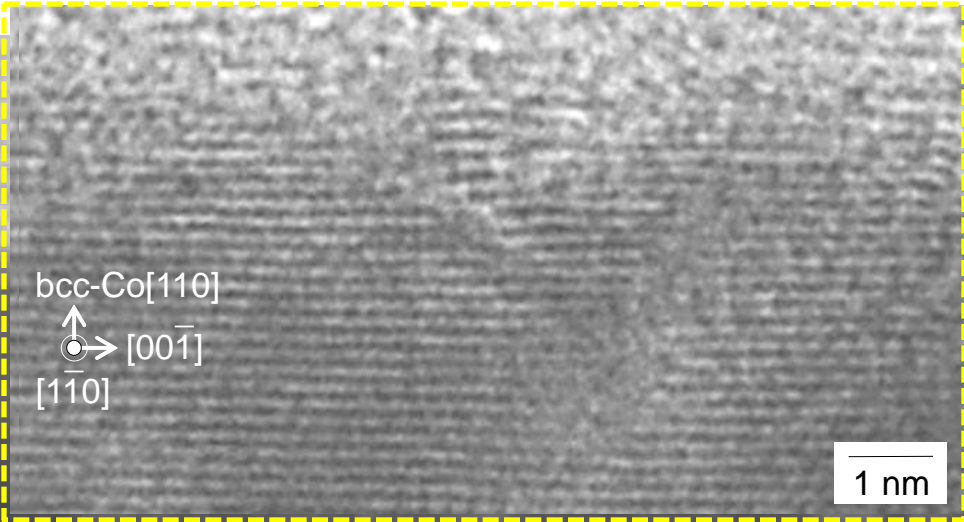
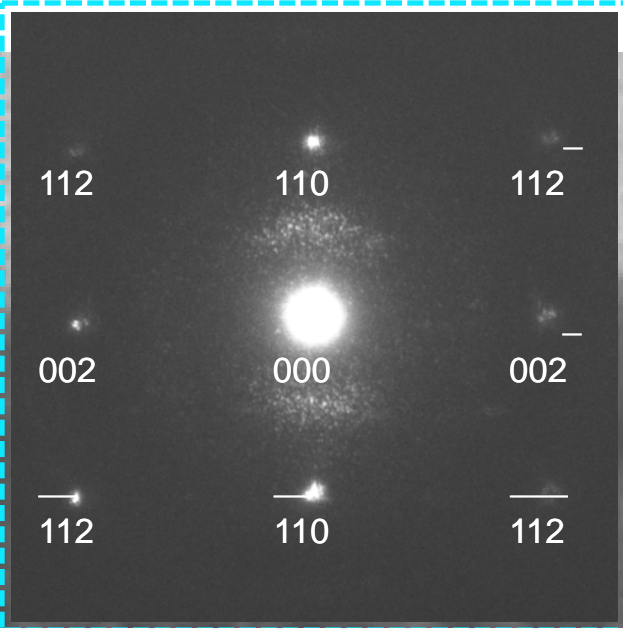
2 nm



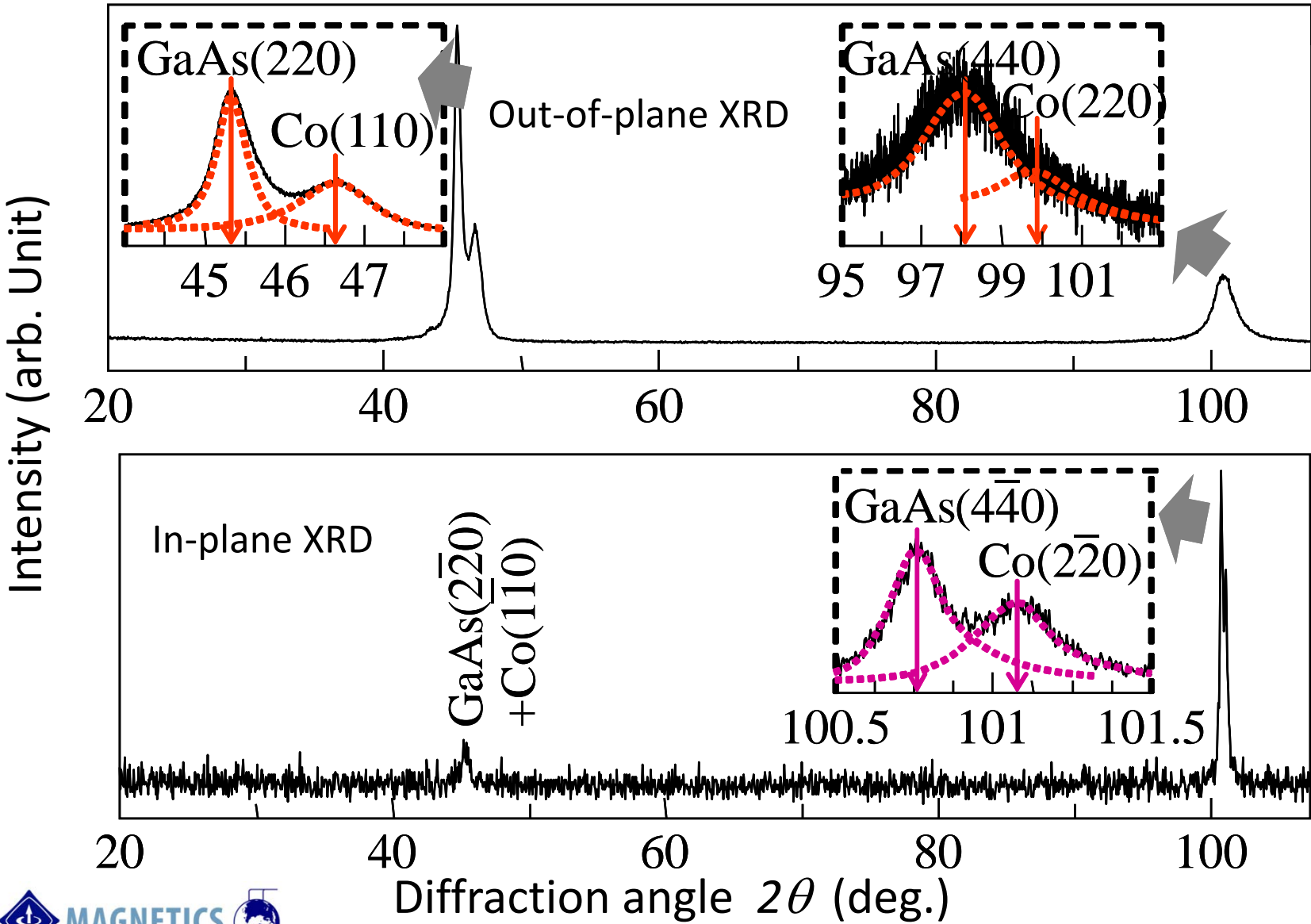
Co Film Growth on Different Planes of MgO Crystal

Plane Temp.	MgO(100)	MgO(110)	MgO(111)
100 °C	hcp-Co(11 $\bar{2}$ 0): -4% + fcc-Co(100):-16%		fcc-Co(111) -16%
300 °C	hcp-Co(11 $\bar{2}$ 0) -4%	fcc-Co(110) -16%	hcp-Co(0001) -16%
500 °C			

bcc-Co Film Growth by Heteroepitaxy on GaAs(110)



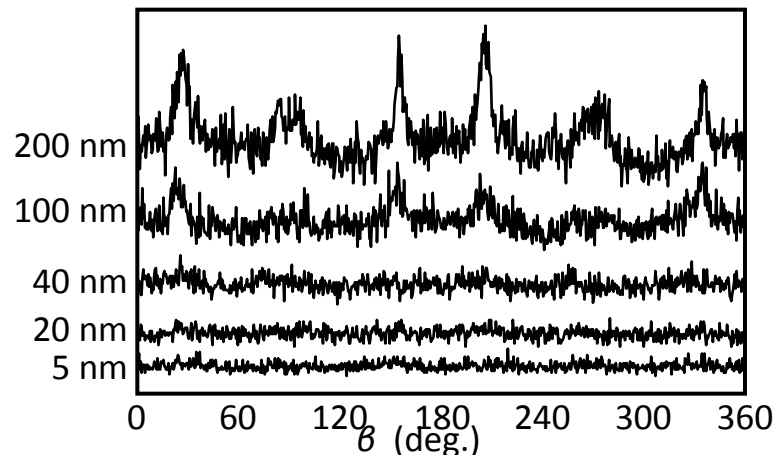
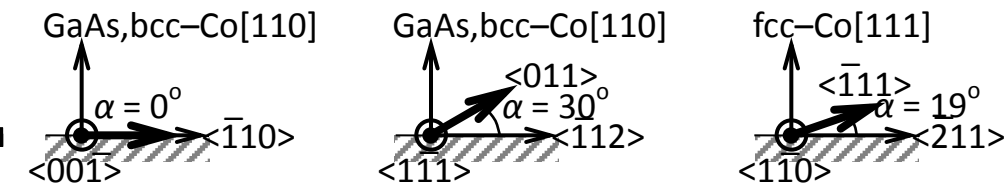
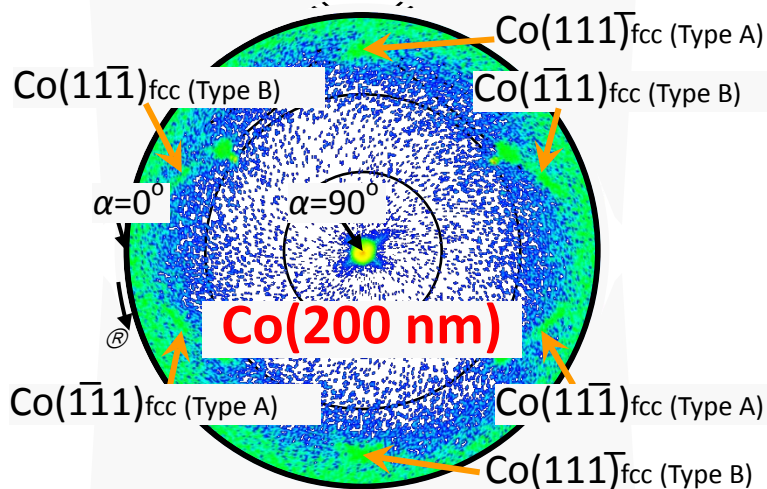
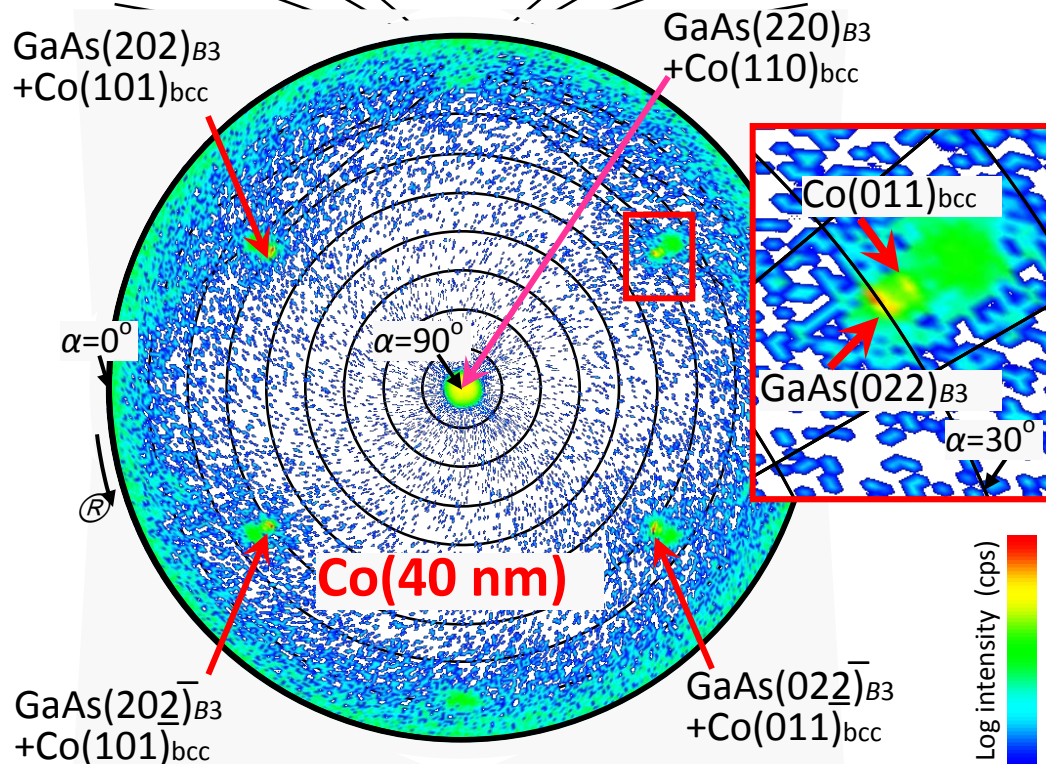
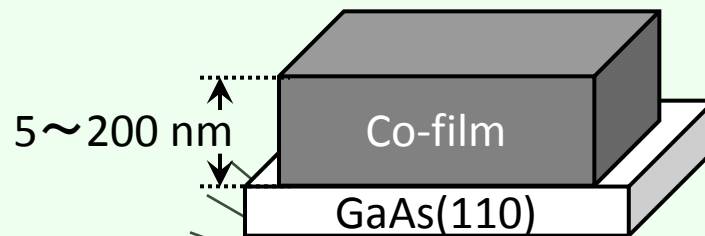
bcc-Co Film Growth by Heteroepitaxy on GaAs(110)



bcc-Co Film Growth by Heteroepitaxy on GaAs(110)

Experimental

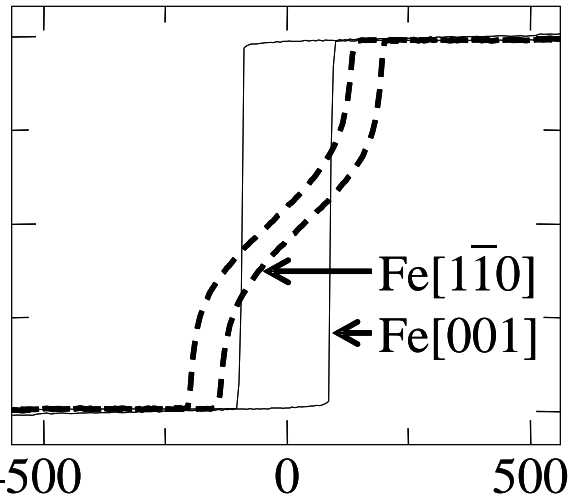
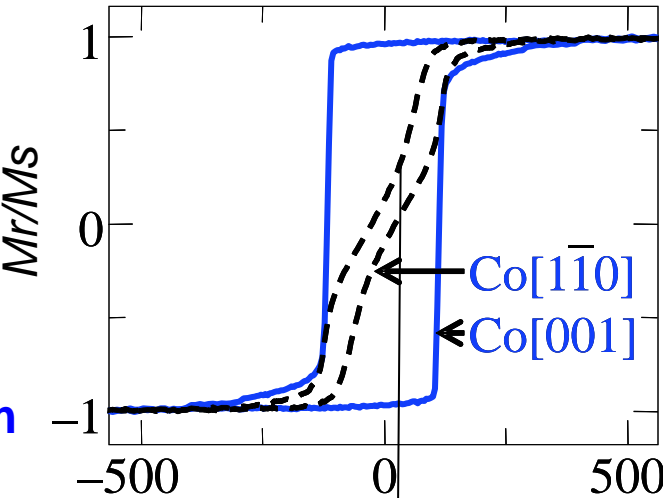
- ▶ RF-Magnetron Sputtering
- ▶ Substrate Temperature: Room Temperature



Magnetic Property of bcc-Co Single-Crystal Film

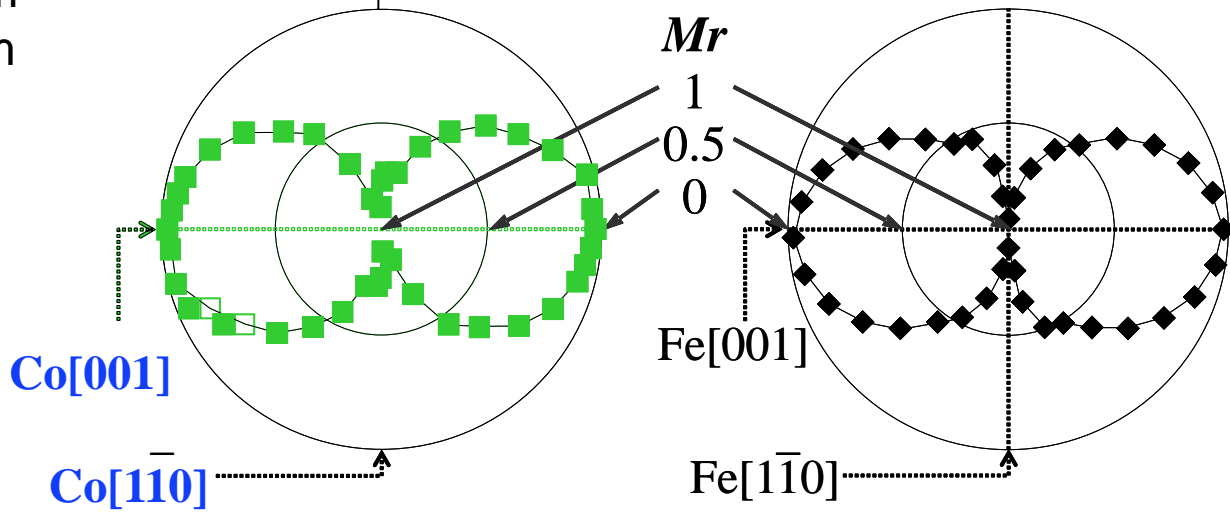
bcc-Co film

$a=0.2789$ nm
 $b=0.2789$ nm
 $c=0.2825$ nm
 $c/a=1.013$

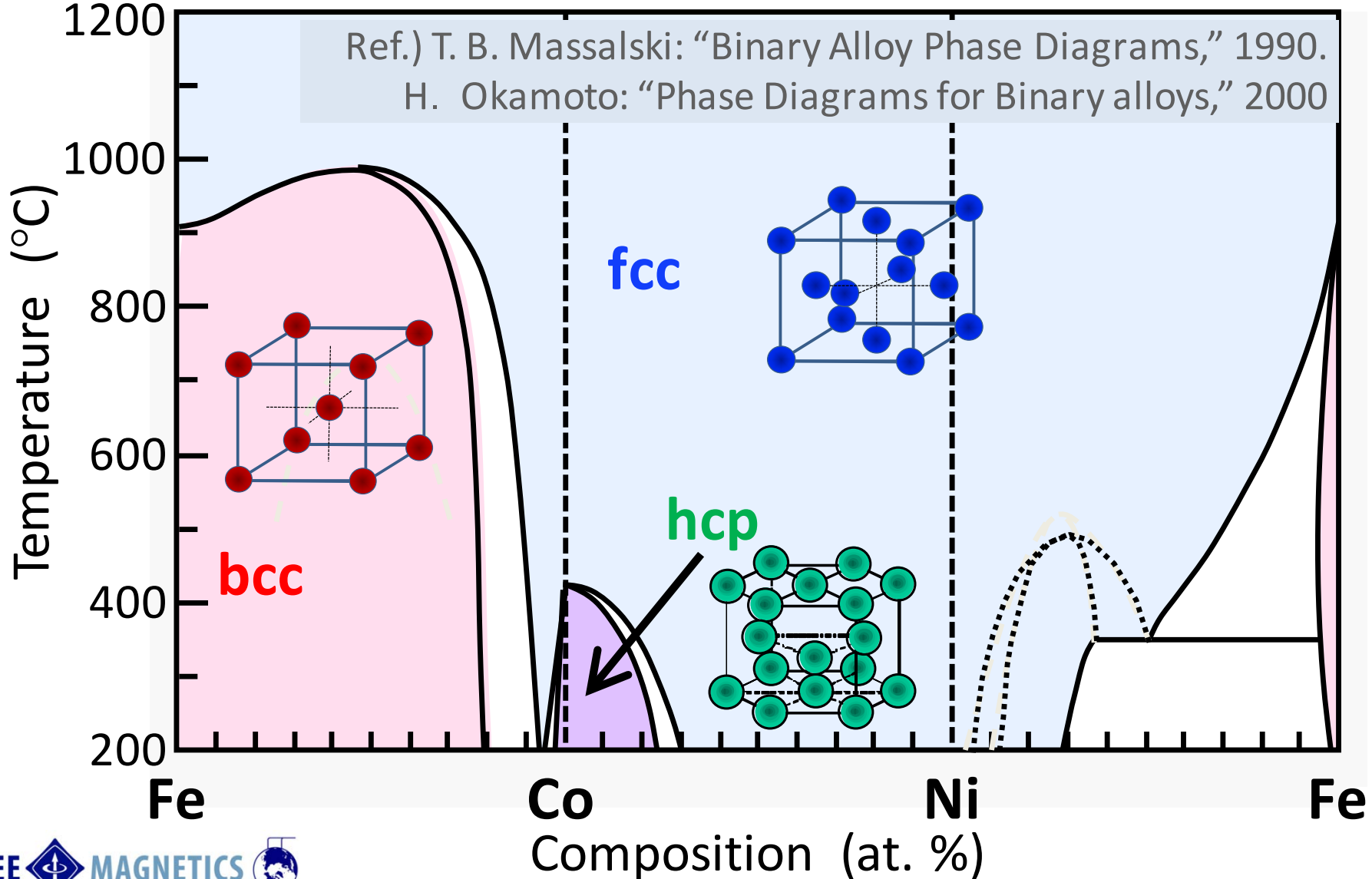


bcc-Fe

$a=b=c$
 $=0.28665$ nm
 $c/a=1.0$



Binary Alloy Phase Diagrams: Fe, Co, Ni Systems



Thin Film Growth of Co-Ni, Ni-Fe, Fe-Co on MgO

>> MgO(100)

Temp.	Co	Co ₈₀ Ni ₂₀	Co ₂₀ Ni ₈₀	Ni	Ni ₈₀ Fe ₂₀	Ni ₂₀ Fe ₈₀	Fe	Fe ₆₅ Co ₃₅	Fe ₅₀ Co ₅₀
100 °C									
300 °C	hcp(11 $\bar{2}$ 0) -4%	hcp(11 $\bar{2}$ 0) + fcc(100) -16%				bcc(100): -4%			
500 °C									

>> MgO(110)

Temp.	Co	Co ₈₀ Ni ₂₀	Co ₂₀ Ni ₈₀	Ni	Ni ₈₀ Fe ₂₀	Ni ₂₀ Fe ₈₀	Fe	Fe ₆₅ Co ₃₅	Fe ₅₀ Co ₅₀
100 °C									
300 °C		fcc(110): -16%				bcc(211): -17%			
500 °C									

>> MgO(111)

Temp.	Co	Co ₈₀ Ni ₂₀	Co ₂₀ Ni ₈₀	Ni	Ni ₈₀ Fe ₂₀	Ni ₂₀ Fe ₈₀	Fe	Fe ₆₅ Co ₃₅	Fe ₅₀ Co ₅₀
100 °C									
300 °C	hcp(0001) -16%	hcp(0001)	fcc(111): -16%				bcc(110): -22%		
500 °C		fcc(111)				fcc(111) bcc(110)			

Thin Film Growth of Co, Ni, Fe on fcc Noble Metals

>> Au, Ag, Cu(100)

	Co			Ni			Fe		
Temp.	Au	Ag	Cu	Au	Ag	Cu	Au	Ag	Cu
100 °C	hcp(112̄0)			hcp(112̄0)			bcc(100)		
300 °C	hcp(1120) fcc(100)	fcc(100)		hcp(1120) fcc(100)	fcc(100)				

>> Au, Ag, Cu(110)

	Co			Ni			Fe		
Temp.	Au	Ag	Cu	Au	Ag	Cu	Au	Ag	Cu
100 °C	hcp(11̄00)			fcc(110)			bcc(211)		
300 °C									

>> Au, Ag, Cu(111)

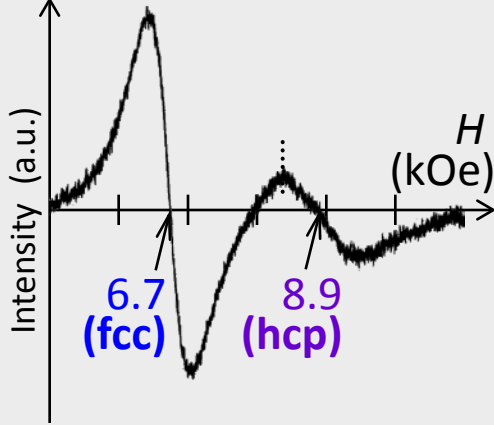
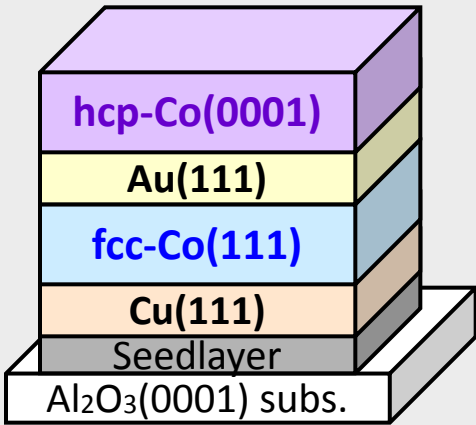
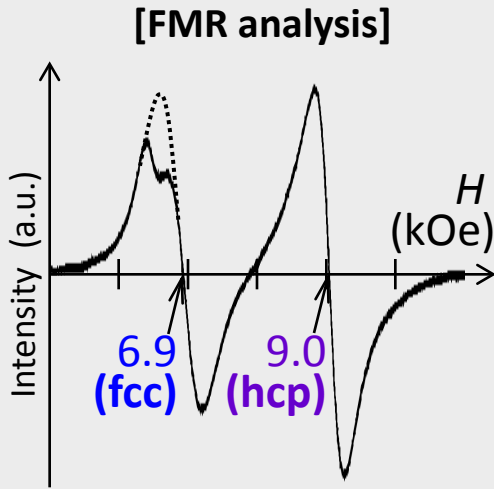
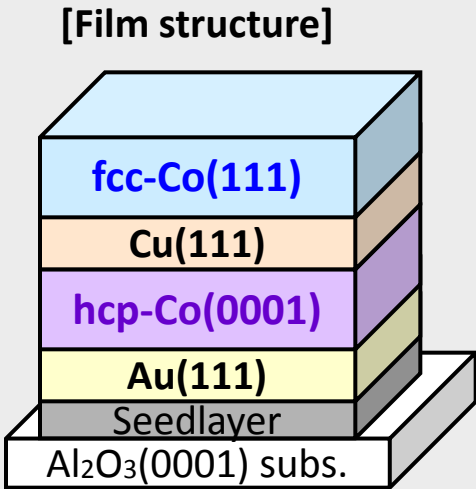
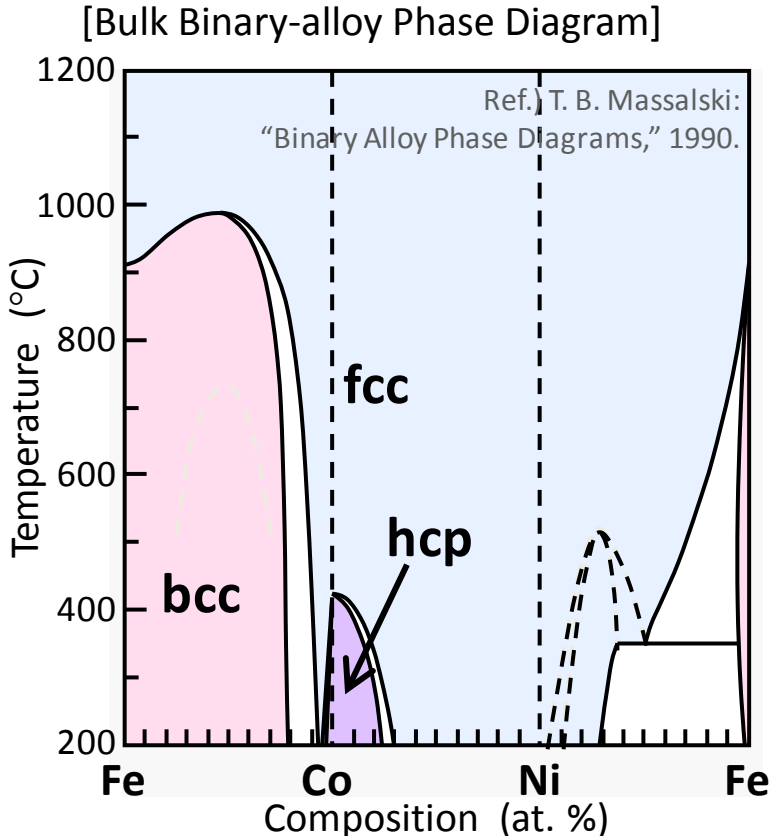
	Co			Ni			Fe		
Temp.	Au	Ag	Cu	Au	Ag	Cu	Au	Ag	Cu
100 °C	hcp(0001) fcc(111)		hcp(0001) fcc(111)	fcc(111)			bcc(110)		
300 °C	hcp(0001)								

Structure Control of Co Films by Heteroepitaxy (I)

Co			
Temp.	Au(111)	Ag(111)	Cu(111)
100 °C	hcp(0001) fcc(111)		hcp(0001) fcc(111)
300 °C	hcp(0001)		fcc(111)

fcc
($K_1: 6 \times 10^5 \text{ erg/cm}^3$)

hcp
($K_u: 5 \times 10^6 \text{ erg/cm}^3$)



Summary

- 1. Epitaxial film growth is a very important technology in controlling the film nanostructure**
- 2. Proper selection of underlayer material and deposition condition will make it possible to control the crystal structure, orientation, strain, stress, etc. in magnetic thin films.**
- 3. Magnetic thin films with meta-stable structures are one of the hopeful possibilities in the future development of magnetic devices**